RENESAS

RX140 Group **Renesas MCUs**

Datasheet

R01DS0379EJ0120 Rev.1.20 Nov 22, 2024

48-MHz, 32-bit RX MCUs, on-chip FPU, 204 Coremark, up to 256-KB flash memory, up to 36 pins capacitive touch sensing unit, up to 9 comms channels, 12-bit A/D, D/A, RTC, IEC60730 compliance, 1.8-V to 5.5-V single supply, Encryption functions (optional)

Features

32-bit RXv2 CPU core

- Maximum operating frequency: 48 MHz
- Maximum operating frequency: 48 MHz Capable of 204 Coremark in operation at 48 MHz
 Enhanced DSP instructions: 32-bit multiply-accumulate instructions, and 16-bit multiply-subtract instructions are supported.
 On-chip FPU: 32-bit single-precision floating point compliant with IEEE.754
- On-chip divider that operated at the fastest of two clock cycles
- Fast interrupt
 CISC Harvard architecture with 5-stage pipeline
- Variable-length instructions, ultra-compact code
- · On-chip debugging circuit

Low power design and architecture

- Operation from a single 1.8-V to 5.5-V supply
 Four low power consumption modes
- Low power timer (LPT) that operates during the software standby state Supply current
- High-speed operating mode: 58 µA/MHz Supply current in software standby mode: 0.25 μ A (typ.) (T_a = 25°C)
- Recovery time from software standby mode: 6.2 μ s (typ.) (Clock Source: HOCO 32 MHz, T_a = 25°C)

On-chip flash memory for code

- 64 K/128 K/256 Kbytes size capacities
- User code is programmable by on-board programming.
 Programmable at 1.8 V
- For instructions and operands

On-chip data flash memory

- 4K/8 Kbytes (1,000,000 program/erase cycles (typ.))
- BGO (Background Operation)
- On-chip SRAM, no wait states
 - 16 K/32 K/64 Kbytes size capacities

DTC

- · Five transfer modes
- ELC
 - · Module operation can be initiated by event signals without using
 - interrupts · Linked operation between modules is possible while the CPU is sleeping.

Reset and supply management

- Seven types of reset, including the power-on reset (POR)
 Low voltage detection (LVD) with voltage settings

Clock functions

- External clock input frequency: Up to 20 MHz
 Main clock oscillator frequency: 1 to 20 MHz
 Sub clock oscillator frequency: 32.768 kHz
 PLL circuit input: 4 MHz to 12 MHz
 Low-speed on-chip oscillator: 4 MHz
 High-speed on-chip oscillator: 24/32/48 MHz ± 1%
 IWDT-dedicated on-chip oscillator: 15 kHz
 Generate a 32.768 kHz clock for the real-time clock
 On-chip olock frequency acuracy measurement circ
- On-chip clock frequency accuracy measurement circuit (CAC)

Realtime clock

- Adjustment functions (30 seconds, leap year, and error)
- · Calendar count mode or binary count mode selectable

Independent watchdog timer

• 15-kHz on-chip oscillator produces a dedicated clock signal to drive IWDT operation.

Useful functions for IEC60730 compliance

 Self-diagnostic and disconnection-detection assistance functions for the A/D converter, clock frequency accuracy measurement circuit, independent watchdog timer, RAM test assistance functions using the DOĈ, etc.



MPC

Input/output functions selectable from multiple pins

Up to 9 communication functions

- One channel of CAN module compliant with ISO11898-1: Transfer at up to 1 Mbps
- SCI with many useful functions (up to 6 channels) Asynchronous mode (Fine adjustable baud rate: 0 to 255/255), clock synchronous mode, smart card interface mode
- I²C bus interface: Transfer at up to 400 kbps, capable of SMBus RSPI (one channel)
 RSPI (one channel): Transfer at up to 16 Mbps

Up to 12 extended-function timers

- 16-bit MTU: input capture, output compare, complementary PWM output, phase counting mode (six channels) • 8-bit TMR (four channels)
- - 16-bit compare-match timers (two channels)

12-bit A/D converter

- Capable of conversion within 0.67 μs
 17 (external pin input) +1 (internal input) channels
- Sampling time can be set for each channel
- Conversion results compare features Self-diagnostic function and analog input disconnection detection assistance function
- Double trigger (data duplication) function for motor control

D/A converter

· Two channels

Capacitive touch sensing unit

- Self-capacitance method: A single pin configures a single key, supporting up to 36 keys
- Mutual capacitance method: Matrix configuration with 8 × 8, supporting up to 64 keys
- Comparator B

Two channels

- General I/O ports
- 5-V tolerant, open drain, input pull-up

Encryption functions (optional)

- AES (key lengths: 128 and 256 bits)
 RNG (True random number generator)
- Temperature sensor
- Unique ID
- 32-byte ID code for the MCU
- Operating temperature range

-40 to +85°C -40 to +105°C

- Applications
- General industrial and consumer equipment



1. Overview

1.1 Outline of Specifications

 Table 1.1 lists the specifications, and Table 1.2 gives a comparison of the functions of the products in different packages.

Table 1.1 is for products with the greatest number of functions, so the number of peripheral modules and channels will differ in accordance with the package type. For details, see Table 1.2, Comparison of Functions for Different Packages in the RX140 Group.

Table 1.1	Outline of Specifications (1/4)
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Classification	Module/Function	Description						
CPU	CPU	 Maximum operating frequency: 48 MHz 32-bit RX CPU (RX v2) Minimum instruction execution time: One instruction per clock cycle Address space: 4-Gbyte linear Register set General purpose: Sixteen 32-bit registers Control: Ten 32-bit registers Accumulator: Two 72-bit registers Basic instructions: 75 (variable-length instruction format) Floating point instructions: 11 DSP instructions: 23 Addressing modes: 11 Data arrangement Instructions: Little endian Data: Selectable as little endian or big endian On-chip 32-bit multiplier: 32-bit × 32-bit → 64-bit On-chip divider: 32-bit + 32-bit → 32 bits 						
	FPU	Single precision (32-bit) floating pointData types and exceptions in conformance with the IEEE754 standard						
Memory	ROM	 Capacity: 64 K/128 K/256 Kbytes 32 MHz ≤: No-wait cycle access 32 MHz to 48 MHz: One-wait cycle access Programming/erasing method: Serial programming (asynchronous serial communication), self-programming 						
	RAM	Capacity: 16 K/32 K/64 Kbytes No-wait memory access						
	E2 DataFlash	 Capacity: 4 K/8 Kbytes Number of erase/write cycles: 1,000,000 (typ.) 						
MCU operating mo	ode	Single-chip mode						
Clock	Clock generation circuit	 Main clock oscillator, sub-clock oscillator, low-speed on-chip oscillator, high-speed on-chip oscillator, PLL frequency synthesizer, and IWDT-dedicated on-chip oscillator Oscillation stop detection: Available Clock frequency accuracy measurement circuit (CAC) Independent settings for the system clock (ICLK), peripheral module clock (PCLK), and FlashIF clock (FCLK) The CPU and system sections such as other bus masters run in synchronization with the system clock (ICLK): 48 MHz (at max.) Peripheral modules run in synchronization with the PCLKB: 32 MHz (at max.) The flash peripheral circuit runs in synchronization with the FCLK: 48 MHz (at max.) ADCLK in the S12AD runs in synchronization with PCLKD: Up to 48 MHz The ICLK frequency can only be set to FCLK, PCLKB, or PCLKD multiplied by n (n: 1, 2, 4, 8, 16, 32, 64) 						
Resets		RES# pin reset, power-on reset, voltage monitoring reset, independent watchdog timer reset, and software reset						
Voltage detection	Voltage detection circuit (LVDAb)	 When the voltage on VCC falls below the voltage detection level, an internal reset or internal interrupt is generated. Voltage detection circuit 0 is capable of selecting the detection voltage from 4 levels Voltage detection circuit 1 is capable of selecting the detection voltage from 14 levels Voltage detection circuit 2 is capable of selecting the detection voltage from 4 levels 						



Classification	Module/Function	Description						
Low power consumption	Low power consumption functions	 Module stop function Four low power consumption modes Sleep mode, deep sleep mode, software standby mode, and snooze mode 						
	Function for lower operating power consumption	Operating power control modes High-speed operating mode, middle-speed operating mode 2 and low- speed operating mode						
Interrupt	Interrupt controller (ICUb)	 Interrupt vectors: 256 External interrupts: 9 (NMI, IRQ0 to IRQ7 pins) Non-maskable interrupts: 5 (The NMI pin, oscillation stop detection interrupt, voltage monitoring 1 interrupt, voltage monitoring 2 interrupt, and IWDT interrupt) 16 levels specifiable for the order of priority 						
DMA	Data transfer controller (DTCb)	 Transfer modes: Normal transfer, repeat transfer, and block transfer Activation sources: Interrupts Sequence transfer 						
I/O ports	General I/O ports	80-pin/64-pin (ROM capacity: product with 128 Kbytes or more)/64-pins (ROM capacity: produc Kbytes)/48-pin/32-pin I/O: 69/53/53/39/23 Input: 3/3/1/1/1 Pull-up resistors: 69/53/53/39/23 Open-drain outputs: 47/35/35/27/20 5-V tolerance: 4/2/2/2/2						
Event link control	ler (ELC)	 Event signals of 48 types can be directly connected to the module Operations of timer modules are selectable at event input Capable of event link operation for port B 						
Multi-function pin	controller (MPC)	Capable of selecting the input/output function from multiple pins						
Timers	Multi-function timer pulse unit 2 (MTU2a)	 (16 bits × 6 channels) × 1 unit Up to 16 pulse-input/output lines and three pulse-input lines are available based on the six 16-bit timer channels Select from among eight or seven counter-input clock signals for each channel (PCLK/1, PCLK/4, PCLK/16, PCLK/64, PCLK/256, PCLK/1024, MTCLKA, MTCLKB, MTCLKC, MTCLKD) other than channel 5, for which only four signals are available. Input capture function 21 output compare/input capture registers Pulse output mode Complementary PWM output mode Reset synchronous PWM mode Phase-counting mode Capable of generating conversion start triggers for the A/D converter 						
	Port output enable 2 (POE2a)	Controls the high-impedance state of the MTU's waveform output pins						
	Compare match timer (CMT)	 (16 bits × 2 channels) × 1 unit Select from among four clock signals (PCLK/8, PCLK/32, PCLK/128, PCLK/512) 						
	Independent watchdog timer (IWDTa)	 14 bits × 1 channel Count clock: Dedicated low-speed clock for the IWDT Frequency divided by 1, 16, 32, 64, 128, or 256 						
	Realtime clock (RTCB)	 Clock source: Sub-clock Calendar count mode or binary count mode selectable Interrupts: Alarm interrupt, periodic interrupt, and carry interrupt 						
	Low power timer (LPTa)	 16 bits × 1 channel Clock source: Sub-clock, LOCO clock divided by 4, or dedicated low-speed clock for the IWDT selectable Clock division ratio: Frequency divided by 1, 2, 4, 8, 16, or 32 selectable PWM output mode 						
	8-bit timer (TMRa)	 (8 bits × 2 channels) × 2 units Seven internal clocks (PCLK/1, PCLK/2, PCLK/8, PCLK/32, PCLK/64, PCLK/1024, and PCLK/8192) and an external clock can be selected Pulse output and PWM output with any duty cycle are available Two channels can be cascaded and used as a 16-bit timer 						

Table 1.1Outline of Specifications (2/4)



Classification	Module/Function	Description						
Communication functions	Serial communications interfaces (SCIg, SCIh, SCIk)	 6 channels (channel 1, 5: SCIk, 6, 8, 9: SCIg, channel 12: SCIh) SCIg Serial communications modes: Asynchronous, clock synchronous, and smart-card interface On-chip baud rate generator allows selection of the desired bit rate Choice of LSB-first or MSB-first transfer Average transfer rate clock can be input from TMR timers for SCI5, SCI6, and SCI12 Start-bit detection: Level or edge detection is selectable. Simple I²C Simple SPI 7, 8, or 9-bit transfer mode Bit rate modulation Event linking by the ELC (only on SCI5) SCIk (the following functions are added) Data matching detection Adjustment function of the asynchronous RXD sampling SCIh (the following functions are added to SCIg) Supports the serial communications protocol, which contains the start frame and information frame Supports the LIN format 						
	I ² C bus interface (RIICa)	 1 channel Communications formats: I²C bus format/SMBus format Master mode or slave mode selectable Supports fast mode 						
Communication functions	Serial peripheral interface (RSPIc)	 1 channel Transfer facility Using the MOSI (master out, slave in), MISO (master in, slave out), SSL (slave select), and RSPCH (RSPI clock) signals enables serial transfer through SPI operation (four lines) or clock-synchronous operation (three lines) Capable of handling serial transfer as a master or slave Data formats Choice of LSB-first or MSB-first transfer The number of bits in each transfer can be changed to 8, 9, 10, 11, 12, 13, 14, 15, 16, 20, 24, or 32 bits. 128-bit buffers for transmission and reception Up to four frames can be transmitted or received in a single transfer operation (with each frame having up to 32 bits) Transit/receive data can be swapped in byte units Double buffers for both transmission and reception RSPCK can be stopped with the receive buffer full for master reception. 						
	CAN module (RSCAN)	 1 channel Compliance with the ISO11898-1 specification (standard frame and extended frame) 16 mailboxes 						
12-bit A/D convert	er (S12ADE)	 12 bits (18 channels × 1 unit*1) 12-bit resolution Minimum conversion time: 0.67 µs per channel when the ADCLK is operating at 48 MHz Operating modes Scan mode (single scan mode, continuous scan mode, and group scan mode) Group A priority control (only for group scan mode) Sampling variable Sampling time can be set up for each channel. Self-diagnostic function Double trigger mode (A/D conversion data duplicated) Detection of analog input disconnection Conversion results compare features A/D conversion start conditions A software trigger, a trigger from a timer (MTU), an external trigger signal, or ELC Event linking by the ELC 						
Temperature sens	or (TEMPSA)	 1 channel The voltage output from the temperature sensor is converted into a digital value by the 12-bit A/D converter. 						
D/A converter (DA)	 2 channels 8-bit resolution Output voltage: 0 V to AVCC0 						
CRC calculator (C	RC)	 CRC code generation for arbitrary amounts of data in 8-bit units Select any of three generating polynomials: X⁸ + X² + X + 1, X¹⁶ + X¹⁵ + X² + 1, or X¹⁶ + X¹² + X⁵ + 1 Generation of CRC codes for use with LSB-first or MSB-first communications is selectable. 						
Comparator B (CN	ЛРВа)	 2 channels Function to compare the reference voltage and the analog input voltage Window comparator operation or standard comparator operation is selectable 						

Table 1.1 Outline of Specifications (3/4)



Classification	Module/Function	Description					
Capacitive touch sensing unit (CTSU2SL, CTSU2L)		 CTSU2L Self-capacitance method: A single pin configures a single key, supporting up to 36 keys Mutual capacitance method: Matrix configuration with 8 × 8, supporting up to 64 keys CTSU2SL (The following functions are added to CTSU2L) Automatic correction Automatic judgment 					
Data operation ci	rcuit (DOC)	Comparison, addition, and subtraction of 16-bit data					
Unique ID		32-byte ID code for the MCU					
Encryption function	Advanced encryption standard hardware accelerator (AESA)	 Key lengths: 128 and 256 bits Support for ECB, CBC, and CTR operating modes Speed of calculations: 128-bit key length in 176 cycles 256-bit key length in 240 cycles Compliant with FIPS PUB 197 					
True random number generator (RNGA)		 Length of random numbers: 32 bits Generation of random-number-generated interrupts after a number is generated 					
Power supply volt	tages/Operating frequencies	VCC = 1.8 to 5.5 V: 48 MHz					
Operating temper	ature range	D version: -40 to +85°C, G version: -40 to +105°C					
Packages		80-pin LFQFP (PLQP0080KB-B) 12 × 12 mm, 0.5 mm pitch 64-pin LFQFP (PLQP0064KB-C) 10 × 10 mm, 0.5 mm pitch 64-pin LQFP (PLQP0064GA-A) 14 × 14 mm, 0.8 mm pitch 48-pin LFQFP (PLQP0048KB-B) 7 × 7 mm, 0.5 mm pitch 48-pin HWQFN (PWQN0048KC-A) 7 × 7 mm, 0.5 mm pitch 32-pin LQFP (PLQP0032GB-A) 7 × 7 mm, 0.8 mm pitch 32-pin HWQFN (PWQN0032KE-A) 5 × 5 mm, 0.5 mm pitch					
Debugging interfa	ices	FINE interface					

Table 1.1Outline of Specifications (4/4)

Note 1. The 12-bit A/D converter has 17 external input channels and a single internal input channel. For details, refer to section 35, 12-Bit A/D Converter (S12ADE) in the User's Manual: Hardware.



		Products with	n 128-Kbyte or la	arger ROM	Products with	64-Kbyte ROM		
Module/Functions		80 Pins	64 Pins	48 Pins	64 Pins	48 Pins	32 Pins	
Interrupts	External interrupts	NMI, IRQ0 to IRQ7	NMI, IRQ0 to IRQ2, IRQ4 to IRQ7	NMI, IRQ0 to IRQ2, IRQ4 to IRQ7	NMI, IRQ0 to IRQ2, IRQ4 to IRQ7	NMI, IRQ0 to IRQ2, IRQ4 to IRQ7	NMI, IRQ0 to IRQ2 IRQ5 to IRQ7	
DTC	Data transfer controller		Available			Available	•	
Timers	Multi-function timer pulse unit 2		6 channels			6 channels		
	Port output enable 2	POE	0# to POE3#, P0	DE8#	POE0# to PC	DE3#, POE8#	POE0#, POE8#	
	8-bit timer	2	channels × 2 un	its	2	channels × 2 un	its	
	Compare match timer	2	channels × 1 ur	nit	2	channels × 1 ur	nit	
	Low power timer		1 channel			1 channel		
	Realtime clock	Avai	ilable	Not supported	Available	Not su	pported	
	Independent watchdog timer		Available			Available		
Communicat ion functions	Serial communications interfaces (SCIk)		2 channels (SCI1, 5)			2 channels (SCI1, 5)		
	Serial communications interfaces (SCIg)	-	3 channels 2 channels (SCI6, 8, 9) (SCI6, 8)		Not supported			
	Serial communications interfaces (SCIh)		1 channel (SCI12)		1 channel (SCI12)			
Communicat	I ² C bus interface	1 channel			1 channel			
ion functions	Serial peripheral interface		1 channel			1 channel		
	CAN module		1 channel			Not supported		
Capacitive tou	ich sensing unit (CTSU2SL)	36 channels	36 channels 32 channels 24 channels		Not supported			
Capacitive tou	ich sensing unit (CTSU2L)		Not supported		12 channels	12 channels	12 channels	
12-bit A/D cor	verter	18 channels *1	15 channels *1	11 channels *1	15 channels *1	11 channels *1	8 channels *1	
Temperature s	sensor		Available			Available		
D/A converter		2 cha	annels	Not supported	2 channels	Not su	pported	
CRC calculate	Dr		Available			Available		
Event link con	troller		Available			Available		
Comparator B			2 channels			2 channels		
Encryption Advanced encryption standard function hardware accelerator (AESA)		Ava	ailable/Not suppo	rted		Not supported		
True random number generator (RNGA)		Ava	Available/Not supported			Not supported		
Packages		80-pin LFQFP (0.5 mm)	64-pin LQFP (0.8 mm) 64-pin LFQFP (0.5 mm)	48-pin LFQFP (0.5 mm) 48-pin HWQFN (0.5 mm)	64-pin LQFP (0.8 mm) 64-pin LFQFP (0.5 mm)	48-pin LFQFP (0.5 mm) 48-pin HWQFN (0.5 mm)	32-pin LQFP (0.8 mm) 32-pin HWQFN (0.5 mm)	

Table 1.2 Comparison of Functions for Different Packages in the RX140 Group

Note 1. This number includes a single internal input channel. For details, refer to section 35, 12-Bit A/D Converter (S12ADE) in the User's Manual: Hardware.



1.2 List of Products

Table 1.3 is a lists of products, and Figure 1.1 shows how to read the product part no., memory capacity, and package type.

Group	Part No.	Part No. (for Orders)	Package	ROM Capacity	RAM Capacity	E2 DataFlash	Operating Frequency (Max.)	Encryption Module	Operating Temperature
RX140	R5F51406ADFN	R5F51406ADFN#30	PLQP0080KB-B						
	R5F51406ADFM	R5F51406ADFM#30	PLQP0064KB-C						
	R5F51406ADFK	R5F51406ADFK#30	PLQP0064GA-A						–40 to +85°C
	R5F51406ADFL	R5F51406ADFL#30	PLQP0048KB-B						
	R5F51406ADNE	R5F51406ADNE#30	PWQN0048KC-A	256	64				
	R5F51406AGFN	R5F51406AGFN#30	PLQP0080KB-B	Kbytes	Kbytes				
	R5F51406AGFM	R5F51406AGFM#30	PLQP0064KB-C						
	R5F51406AGFK	R5F51406AGFK#30	PLQP0064GA-A						–40 to +105°C
	R5F51406AGFL	R5F51406AGFL#30	PLQP0048KB-B						
	R5F51406AGNE	R5F51406AGNE#30	PWQN0048KC-A			9 Khutoo			
	R5F51405ADFN	R5F51405ADFN#30	PLQP0080KB-B			8 Kbytes			
	R5F51405ADFM	R5F51405ADFM#30	PLQP0064KB-C	128 32				Not supported	
	R5F51405ADFK	R5F51405ADFK#30	PLQP0064GA-A						–40 to +85°C
	R5F51405ADFL	R5F51405ADFL#30	PLQP0048KB-B				48 MHz		
	R5F51405ADNE	R5F51405ADNE#30	PWQN0048KC-A		32				
	R5F51405AGFN	R5F51405AGFN#30	PLQP0080KB-B	Kbytes	Kbytes				
	R5F51405AGFM	R5F51405AGFM#30	PLQP0064KB-C						
	R5F51405AGFK	R5F51405AGFK#30	PLQP0064GA-A						–40 to +105°C
	R5F51405AGFL	R5F51405AGFL#30	PLQP0048KB-B						
	R5F51405AGNE	R5F51405AGNE#30	PWQN0048KC-A						
	R5F51403ADFM	R5F51403ADFM#30	PLQP0064KB-C						
	R5F51403ADFK	R5F51403ADFK#30	PLQP0064GA-A						
	R5F51403ADFL	R5F51403ADFL#30	PLQP0048KB-B						–40 to +85°C
	R5F51403ADNE	R5F51403ADNE#30	PWQN0048KC-A						-40 10 +65 C
	R5F51403ADFJ	R5F51403ADFJ#30	PLQP0032GB-A	Kbytes					
	R5F51403ADNH	R5F51403ADNH#30	PWQN0032KE-A		16	4.166.455			
	R5F51403AGFM	R5F51403AGFM#30	PLQP0064KB-C		Kbytes	4 Kbytes			
	R5F51403AGFK	R5F51403AGFK#30	PLQP0064GA-A						
	R5F51403AGFL	R5F51403AGFL#30	PLQP0048KB-B						40 to 1405°C
	R5F51403AGNE	R5F51403AGNE#30	PWQN0048KC-A						–40 to +105°C
	R5F51403AGFJ	R5F51403AGFJ#30	PLQP0032GB-A	1					
	R5F51403AGNH	R5F51403AGNH#30	PWQN0032KE-A	1					

Table 1.3List of Products (1/2)

R5F51406BDFL R5F51406BDFL#30 PLQP0048KB-B R5F51406BDNE R5F51406BDNE#30 PWQN0048KC-A R5F51406BGFN R5F51406BGFN#30 PLQP0080KB-B R5F51406BGFM R5F51406BGFM#30 PLQP0080KB-B R5F51406BGFK R5F51406BGFK#30 PLQP0084KB-C R5F51406BGFL R5F51406BGFL#30 PLQP0048KB-B R5F51406BGFL R5F51406BGFL#30 PLQP0048KB-B R5F51406BGFL R5F51406BGFL#30 PLQP0080KB-B R5F51405BDFN R5F51405BDFN#30 PLQP0080KB-B R5F51405BDFN R5F51405BDFN#30 PLQP0064KB-C R5F51405BDFK R5F51405BDFM#30 PLQP0064KB-C R5F51405BDFK R5F51405BDFK#30 PLQP0064KB-C R5F51405BDFL R5F51405BDFL#30 PLQP0064KB-C R5F51405BDFL R5F51405BDFL#30 PLQP0084KB-B R5F51405BDFL R5F51405BDFL#30 PLQP0084KB-B R5F51405BDFL R5F51405BDFL#30 PLQP0084KB-B R5F51405BDFL R5F51405BDFL#30 PLQP0084KB-B R5F51405BDFL R5F51405BDFL#30 PLQP0086KB-B R5F5140	Group	Part No.	Part No. (for Orders)	Package	ROM Capacity	RAM Capacity	E2 DataFlash	Operating Frequency (Max.)	Encryption Module	Operating Temperature
RSF51406BDFK RSF51406BDFK#30 PLQP0064GA-A RSF51406BDFL RSF51406BDFL#30 PLQP0048KB-B PLQP0048KB-B RSF51406BGFN RSF51406BDFL#30 PLQP0048KB-B RSF51406BGFN 64 Kbytes <	RX140	R5F51406BDFN	R5F51406BDFN#30	PLQP0080KB-B						
RSF51406BDFL RSF51406BDFL#30 PLQP0048KB-B RSF51406BDNE RSF51406BDNE#30 PWQN0048KC-A RSF51406BGFM RSF51406BGFN#30 PLQP0080KB-B RSF51406BGFK RSF51406BGFK RSF51406BGFK RSF51406BGFL RSF51406BGFL#30 PLQP0064KB-C RSF51406BGFL RSF51406BGFL#30 PLQP0048KB-B RSF51406BGFL RSF51406BGFL#30 PLQP0080KB-B RSF51405BDFN RSF51405BDFN#30 PLQP0080KB-B RSF51405BDFM RSF51405BDFH#30 PLQP0080KB-B RSF51405BDFK RSF51405BDFL#30 PLQP0084KB-C RSF51405BDFK RSF51405BDFL#30 PLQP0044KB-C RSF51405BDFL RSF51405BDFL#30 PLQP0044KB-C RSF51405BDFL RSF51405BDFL#30 PLQP0044KB-C RSF51405BDFL RSF51405BDFL#30 PLQP0044KB-C RSF51405BDFL RSF51405BGFN#30 PLQP0044KB-C RSF51405BDFL RSF51405BGFN#30 PLQP0044KB-C RSF51405BDFL RSF51405BGFN#30 PLQP0044KB-C RSF51405BGFN RSF51405BGFN#30 PLQP00044KB-C RSF51405B		R5F51406BDFM	R5F51406BDFM#30	PLQP0064KB-C						
R5F51406BDNE R5F51406BDNE#30 PWQN0048KC-A 256 64 Kbytes 64 <		R5F51406BDFK	R5F51406BDFK#30	PLQP0064GA-A						–40 to +85°C
Construct Construct <t< td=""><td></td><td>R5F51406BDFL</td><td>R5F51406BDFL#30</td><td>PLQP0048KB-B</td><td></td><td></td><td></td><td></td><td></td><td></td></t<>		R5F51406BDFL	R5F51406BDFL#30	PLQP0048KB-B						
Rol 01400BCH W Rol 01400BCH W00 FLCH 0000RD-D FLCH 0000RD-D R5F51406BGFM R5F51406BGFM#30 PLQP0064KB-C -40 to +105° R5F51406BGFL R5F51406BGFL#30 PLQP0048KB-B -40 to +105° R5F51406BGRE R5F51406BGFL#30 PLQP0080KB-B -40 to +105° R5F51406BGFL R5F51405BDFN R5F51405BDFM#30 PLQP0064KB-C R5F51405BDFK R5F51405BDFK#30 PLQP0064KB-C R5F51405BDFL R5F51405BDFL#30 PLQP0064KB-B R5F51405BDFL R5F51405BDFL#30 PLQP0080KB-B R5F51405BDFL R5F51405BDFL#30 PLQP0080KB-B R5F51405BDFL R5F51405BDFL#30 PLQP0080KB-B R5F51405BGFN R5F51405BGFN#30 PLQP0084KB-C R5F51405BGFN R5F51405BGFN#30 PLQP0084KB-C R5F51405BGFK R5F51405BGFM#30 PLQP0064GA-A R5F51405BGFK R5F51405BGFL#30 PLQP0064GA-A R5F51405BGFL R5F51405BGFL#30 PLQP0084KB-C R5F51405BGFL R5F51405BGFL#30 PLQP0084KB-B R5F51405BGFL R5F51405BGFL#30 PLQP0084KB-B		R5F51406BDNE	R5F51406BDNE#30	PWQN0048KC-A	256	64				
R5F51406BGFK R5F51406BGFK#30 PLQP0064GA-A R5F51406BGFL R5F51406BGFL#30 PLQP0048KB-B R5F51406BGNE R5F51406BGNE#30 PWQN0048KC-A R5F51405BDFN R5F51405BDFN#30 PLQP0080KB-B R5F51405BDFN R5F51405BDFM#30 PLQP0064KB-C R5F51405BDFK R5F51405BDFK#30 PLQP0064KB-C R5F51405BDFL R5F51405BDFL#30 PLQP0064KB-C R5F51405BDFL R5F51405BDFL#30 PLQP0048KB-B R5F51405BDFL R5F51405BDFL#30 PLQP0080KB-B R5F51405BDFL R5F51405BDFL#30 PLQP0080KB-B R5F51405BGFN R5F51405BGFN#30 PLQP0080KB-B R5F51405BGFN R5F51405BGFN#30 PLQP0080KB-B R5F51405BGFN R5F51405BGFN#30 PLQP0064GA-A R5F51405BGFN R5F51405BGFN#30 PLQP0064KB-C R5F51405BGFK R5F51405BGFK#30 PLQP0064KB-C R5F51405BGFK R5F51405BGFK#30 PLQP0064KB-C R5F51405BGFK R5F51405BGFL#30 PLQP0064KB-C R5F51405BGFK R5F51405BGFL#30 PLQP0064KB-C R5F51405BGFK R5F51405BGFL#30 PLQP0064KB-C R		R5F51406BGFN	R5F51406BGFN#30	PLQP0080KB-B	Kbytes	Kbytes			Available	
R5F51406BGFL R5F51406BGFL#30 PLQP0048KB-B R5F51406BGNE R5F51406BGNE#30 PWQN0048KC-A R5F51405BDFN R5F51405BDFN#30 PLQP0080KB-B R5F51405BDFM R5F51405BDFM#30 PLQP0064KB-C R5F51405BDFK R5F51405BDFK#30 PLQP0064KB-C R5F51405BDFL R5F51405BDFK#30 PLQP0064KB-B R5F51405BDFL R5F51405BDFL#30 PLQP0048KC-A R5F51405BDFL R5F51405BDFL#30 PLQP0080KB-B R5F51405BDFL R5F51405BDNE#30 PLQP0080KB-B R5F51405BGFN R5F51405BDNE#30 PLQP0080KB-B R5F51405BGFN R5F51405BGFM30 PLQP0064KB-C R5F51405BGFN R5F51405BGFM#30 PLQP0064KB-C R5F51405BGFN R5F51405BGFM30 PLQP0064KB-C R5F51405BGFM R5F51405BGFK#30 PLQP0064KB-C R5F51405BGFK R5F51405BGFK#30 PLQP0064KB-C R5F51405BGFK R5F51405BGFK#30 PLQP0064KB-C R5F51405BGFK R5F51405BGFK#30 PLQP0064KB-C R5F51405BGFL R5F51405BGFK#30 PLQP0064KB-C R5F51405BGFL R5F51405BGFK#30 PLQP00044KB-B		R5F51406BGFM	R5F51406BGFM#30	PLQP0064KB-C	-		— 8 Kbytes	48 MHz		–40 to +105°C
RSF51406BGNE RSF51406BGNE#30 PWQN0048KC-A 8 Kbytes 48 MHz Available RSF51405BDFN RSF51405BDFN#30 PLQP0080KB-B 48 MHz Available -40 to +85°C RSF51405BDFM RSF51405BDFK#30 PLQP0064KB-C 8 Kbytes 48 MHz Available RSF51405BDFK RSF51405BDFK#30 PLQP0064GA-A 128 48 MHz -40 to +85°C RSF51405BDFL RSF51405BDFL#30 PLQP0048KB-B 128 Kbytes -40 to +85°C RSF51405BGFN RSF51405BGFN#30 PLQP0064GA-A 128 Kbytes -40 to +105°C RSF51405BGFN RSF51405BGFN#30 PLQP0064KB-C 128 Kbytes -40 to +105°C RSF51405BGFK RSF51405BGFK#30 PLQP0064KB-C -40 to +105°C -40 to +105°C RSF51405BGFL RSF51405BGFL#30 PLQP0064KB-B -40 to +105°C -40 to +105°C		R5F51406BGFK	R5F51406BGFK#30	PLQP0064GA-A						
R5F51405BDFN R5F51405BDFN#30 PLQP0080KB-B 8 Kbytes 48 MHz Available R5F51405BDFM R5F51405BDFM#30 PLQP0064KB-C		R5F51406BGFL	R5F51406BGFL#30	PLQP0048KB-B						
R5F51405BDFN R5F51405BDFN#30 PLQP0080KB-B R5F51405BDFM R5F51405BDFM#30 PLQP0064KB-C R5F51405BDFK R5F51405BDFK#30 PLQP0064GA-A R5F51405BDFL R5F51405BDFL#30 PLQP0048KB-B R5F51405BDFL R5F51405BDFL#30 PLQP0048KB-B R5F51405BDFL R5F51405BDFL#30 PLQP0080KB-B R5F51405BGFN R5F51405BGFN#30 PLQP0080KB-B R5F51405BGFM R5F51405BGFM#30 PLQP0064KB-C R5F51405BGFK R5F51405BGFK#30 PLQP0064GA-A R5F51405BGFK R5F51405BGFK#30 PLQP0064KB-C R5F51405BGFK R5F51405BGFK#30 PLQP0048KB-B R5F51405BGFL R5F51405BGFL#30 PLQP0048KB-B		R5F51406BGNE	R5F51406BGNE#30	PWQN0048KC-A						
R5F51405BDFK R5F51405BDFL#30 PLQP0064GA-A R5F51405BDFL R5F51405BDFL#30 PLQP0048KB-B R5F51405BDFL R5F51405BDFL#30 PWQN0048KC-A R5F51405BGFN R5F51405BGFN#30 PLQP0080KB-B R5F51405BGFN R5F51405BGFN#30 PLQP0080KB-B R5F51405BGFM R5F51405BGFM#30 PLQP0064KB-C R5F51405BGFK R5F51405BGFK#30 PLQP0064KB-C R5F51405BGFL R5F51405BGFL#30 PLQP0064GA-A R5F51405BGFL R5F51405BGFL#30 PLQP0048KB-B		R5F51405BDFN	R5F51405BDFN#30	PLQP0080KB-B						
R5F51405BDFL R5F51405BDFL#30 PLQP0048KB-B R5F51405BDNE R5F51405BDNE#30 PWQN0048KC-A R5F51405BGFN R5F51405BGFN#30 PLQP0080KB-B R5F51405BGFM R5F51405BGFM#30 PLQP0064KB-C R5F51405BGFK R5F51405BGFK#30 PLQP0064KB-C R5F51405BGFK R5F51405BGFK#30 PLQP0064KB-C R5F51405BGFL R5F51405BGFL#30 PLQP0048KB-B		R5F51405BDFM	R5F51405BDFM#30	PLQP0064KB-C	_					
R5F51405BDNE R5F51405BDNE#30 PWQN0048KC-A 128 32 R5F51405BGFN R5F51405BGFN#30 PLQP0080KB-B Kbytes 4 <td></td> <td>R5F51405BDFK</td> <td>R5F51405BDFK#30</td> <td>PLQP0064GA-A</td> <td></td> <td></td> <td rowspan="2">–40 to +85°C</td>		R5F51405BDFK	R5F51405BDFK#30	PLQP0064GA-A						–40 to +85°C
R5F51405BGFN R5F51405BGFN#30 PLQP0080KB-B Kbytes 32 R5F51405BGFM R5F51405BGFM#30 PLQP0064KB-C Kbytes -40 to +105° R5F51405BGFL R5F51405BGFL#30 PLQP0064GA-A -40 to +105°		R5F51405BDFL	R5F51405BDFL#30	PLQP0048KB-B						
RSF51405BGFN RSF51405BGFN#30 PLQP0064KB-C R5F51405BGFK R5F51405BGFK#30 PLQP0064GA-A R5F51405BGFL R5F51405BGFL#30 PLQP0048KB-B		R5F51405BDNE	R5F51405BDNE#30	PWQN0048KC-A	120	32				
R5F51405BGFK R5F51405BGFK#30 PLQP0064GA-A R5F51405BGFL R5F51405BGFL#30 PLQP0048KB-B		R5F51405BGFN	R5F51405BGFN#30	PLQP0080KB-B		Kbytes				
R5F51405BGFL R5F51405BGFL#30 PLQP0048KB-B		R5F51405BGFM	R5F51405BGFM#30	PLQP0064KB-C						
		R5F51405BGFK	R5F51405BGFK#30	PLQP0064GA-A						–40 to +105°C
R5F51405BGNE R5F51405BGNE#30 PWQN0048KC-A		R5F51405BGFL	R5F51405BGFL#30	PLQP0048KB-B						
		R5F51405BGNE	R5F51405BGNE#30	PWQN0048KC-A	1					

Table 1.3List of Products (2/2)

Note: The part numbers for orders above are used for products in mass production or under development when this manual is issued. Refer to the Renesas Electronics Corporation website for the latest part numbers.





Figure 1.1 How to Read the Product Part Number



1.3 Block Diagram

Figure 1.2 shows a block diagram.





1.4 Pin Functions

 Table 1.4 lists the pin functions.

Table 1.4Pin Functions (1/3)

Classifications	Pin Name	I/O	Description			
Power supply	VCC	Input	Power supply pin. Connect it to the system power supply.			
	VCL	—	Connect this pin to the VSS pin via the 4.7 μF smoothing capacitor used to stabilize the internal power supply. Place the capacitor close to the pin.			
	VSS	Input	Ground pin. Connect it to the system power supply (0 V).			
Clock	XTAL	Output	Pins for connecting a crystal. An external clock can be input through the			
	EXTAL	Input	EXTAL pin.			
	XCIN	Input	Input/output pins for the sub-clock oscillator. Connect a crystal between			
	XCOUT	Output	CIN and XCOUT.			
	CLKOUT	Output	Clock output pin.			
Operating mode control	MD	Input	Pin for setting the operating mode. For usage, refer to section 3.1, Operating Mode Types and Selection in the User's Manual: Hardware.			
System control	RES#	Input	Reset pin. This MCU enters the reset state when this signal goes low.			
Voltage detection circuit	CMPA2	Input	Detection target voltage pin for voltage detection 2.			
Clock frequency accuracy measurement circuit	CACREF	Input	Input pin for the clock frequency accuracy measurement circuit.			
On-chip emulator	FINED	I/O	FINE interface pin.			
Interrupts	NMI	Input	Non-maskable interrupt request pin.			
-	IRQ0 to IRQ7	Input	Interrupt request pins.			
Multi-function timer pulse unit 2	MTIOC0A, MTIOC0B, MTIOC0C, MTIOC0D	I/O	The TGRA0 to TGRD0 input capture input/output compare output/PWM output pins.			
	MTIOC1A, MTIOC1B	I/O	The TGRA1 and TGRB1 input capture input/output compare output/PWM output pins.			
	MTIOC2A, MTIOC2B	I/O	The TGRA2 and TGRB2 input capture input/output compare output/PWM output pins.			
	MTIOC3A, MTIOC3B, MTIOC3C, MTIOC3D	I/O	The TGRA3 to TGRD3 input capture input/output compare output/PWM output pins.			
	MTIOC4A, MTIOC4B, MTIOC4C, MTIOC4D	I/O	The TGRA4 to TGRD4 input capture input/output compare output/PWM output pins.			
	MTIC5U, MTIC5V, MTIC5W	Input	The TGRU5, TGRV5, and TGRW5 input capture input/external pulse input pins.			
	MTCLKA, MTCLKB, MTCLKC, MTCLKD	Input	Input pins for the external clock.			
Port output enable 2	POE0# to POE3#, POE8#	Input	Input pins for request signals to place the MTU pins in the high impedance state.			
Realtime clock	RTCOUT	Output	Output pin for the 1-Hz/64-Hz clock.			
8-bit timer	TMO0 to TMO3	Output	Compare match output pins.			
	TMCI0 to TMCI3	Input	Input pins for the external clock to be input to the counter.			
	TMRI0 to TMRI3	Input	Counter reset input pins.			
Low power timer	LPTO	Output	PWM output pin			



Table 1.4	Pin Functions (2/3)
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Classifications	Pin Name	I/O	Description
Serial	Asynchronous mode/clock s	synchrono	us mode
communications interface (SCIg, SCIk)	SCK1, SCK5, SCK6, SCK8, SCK9	I/O	Input/output pins for the clock.
,	RXD1, RXD5, RXD6, RXD8, RXD9	Input	Input pins for received data.
	TXD1, TXD5, TXD6, TXD8, TXD9	Output	Output pins for transmitted data.
	CTS1#, CTS5#, CTS6#, CTS8#, CTS9#	Input	Input pins for controlling the start of transmission and reception.
	RTS1#, RTS5#, RTS6#, RTS8#, RTS9#	Output	Output pins for controlling the start of transmission and reception.
	Simple I ² C mode		
	SSCL1, SSCL5, SSCL6, SSCL8, SSCL9	I/O	Input/output pins for the I ² C clock.
	SSDA1, SSDA5, SSDA6, SSDA8, SSDA9	I/O	Input/output pins for the I ² C data.
	Simple SPI mode		
	SCK1, SCK5, SCK6, SCK8, SCK9	I/O	Input/output pins for the clock.
	SMISO1, SMISO5, SMISO6, SMISO8, SMISO9	I/O	Input/output pins for slave transmit data.
	SMOSI1, SMOSI5, SMOSI6, SMOSI8, SMOSI9	I/O	Input/output pins for master transmit data.
	SS1#, SS5#, SS6#, SS8#, SS9#	Input	Slave-select input pins.
Serial	Asynchronous mode/clock s	synchrono	us mode
communications nterface (SCIh)	SCK12	I/O	Input/output pin for the clock.
	RXD12	Input	Input pin for receiving data.
	TXD12	Output	Output pin for transmitting data.
	CTS12#	Input	Input pin for controlling the start of transmission and reception.
	RTS12#	Output	Output pin for controlling the start of transmission and reception.
	Simple I ² C mode		
	SSCL12	I/O	Input/output pin for the I ² C clock.
	SSDA12	I/O	Input/output pin for the I ² C data.
	Simple SPI mode		
	SCK12	I/O	Input/output pin for the clock.
	SMISO12	I/O	Input/output pin for slave transmit data.
	SMOSI12	I/O	Input/output pin for master transmit data.
	SS12#	Input	Slave-select input pin.
	 Extended serial mode 		
	RXDX12	Input	Input pin for data reception by SCIf.
	TXDX12	Output	Output pin for data transmission by SCIf.
	SIOX12	I/O	Input/output pin for data reception or transmission by SCIf.
I ² C bus interface	SCL0	I/O	Input/output pin for I ² C bus interface clocks. Bus can be directly driven by the N-channel open drain output.
	SDA0	I/O	Input/output pin for I ² C bus interface data. Bus can be directly driven by the N-channel open drain output.



Classifications	Pin Name	I/O	Description
Serial peripheral	RSPCKA	I/O	Input/output pin for the RSPI clock.
interface	MOSIA	I/O	Input/output pin for transmitting data from the RSPI master.
	MISOA	I/O	Input/output pin for transmitting data from the RSPI slave.
	SSLA0	I/O	Input/output pin to select the slave for the RSPI.
	SSLA1 to SSLA3	Output	Output pins to select the slave for the RSPI.
CAN module	CRXD0	Input	Input pin
	CTXD0	Output	Output pin
12-bit A/D converter	AN000 to AN007, AN016 to AN021, AN024 to AN026	Input	Input pins for the analog signals to be processed by the A/D converter.
	ADTRG0#	Input	Input pin for the external trigger signal that start the A/D conversion.
D/A converter	DA0, DA1	Output	Analog output pins of the D/A converter.
Comparator B	CMPB0, CMPB1	Input	Input pin for the analog signal to be processed by comparator B.
	CVREFB0, CVREFB1	Input	Analog reference voltage supply pin for comparator B.
	CMPOB0, CMPOB1	Output	Output pin for comparator B.
Capacitive touch	TS0 to TS35	I/O	Electrostatic capacitance measurement pins (touch pins).
sensing unit	TSCAP	—	Connect to the VSS via a decoupling capacitor (10 nF) for stabilizing the internal voltage
Analog power supply	AVCC0	Input	Analog voltage supply pin for the 12-bit A/D converter and D/A converter. Connect this pin to VCC when not using the 12-bit A/D converter and D/A converter.
	AVSS0	Input	Analog ground pin for the 12-bit A/D converter and D/A converter. Connect this pin to VSS when not using the 12-bit A/D converter and D/A converter
	VREFH0	Input	Analog reference voltage supply pin for the 12-bit A/D converter.
	VREFL0	Input	Analog reference ground pin for the 12-bit A/D converter.
I/O ports	P03 to P07	I/O	5-bit input/output pins.
	P12 to P17	I/O	6-bit input/output pins.
	P20, P21, P26, P27	I/O	4-bit input/output pins.
	P30 to P32, P34 to P37	I/O	7-bit input/output pins (P35 input pin).
	P40 to P47	I/O	8-bit input/output pins.
	P54, P55	I/O	2-bit input/output pins.
	PA0 to PA6	I/O	7-bit input/output pins.
	PB0 to PB7	I/O	8-bit input/output pins.
	PC2 to PC7	I/O	6-bit input/output pins.
	PD0 to PD2	I/O	3-bit input/output pins.
	PE0 to PE5	I/O	6-bit input/output pins.
	PG7	I/O	1-bit input/output pin.
	PH0 to PH3, PH6*1, PH7*1	I/O	6-bit input/output pins (PH6, PH7: input pins).
	PJ1, PJ6, PJ7	I/O	3-bit input/output pins.

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Table 1.4Pin Functions (3/3)

Note 1. This is not supported by products with 64 Kbytes of ROM.

1.5 Pin Assignments

1.5.1 80-pin LFQFP







1.5.2 64-pin LFQFP, 64-pin LQFP



Figure 1.4 Pin Assignments of the 64-Pin LFQFP, 64-Pin LQFP



1.5.3 48-pin LFQFP



1.5.4 48-pin HWQFN



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1.5.5 32-pin LQFP



1.5.6 32-pin HWQFN





1.6 List of Pins and Pin Functions

1.6.1 80-pin LFQFP

Table 1.5 List of Pins and Pin Functions (80-Pin LFQFP) (1/2)

Pin No.	Power Supply, Clock, System Control	I/O Port	Timers (MTU, TMR, POE, LPT)	Communications (SClg, SClh, SClk, RSPI, RIIC, RSCAN)	Touch sensing	Others
		P06*1				
2		P03*1				DA0
		P04*1				
	VCL					
		PJ1	MTIOC3A			
	MD	PG7				FINED
•	XCIN	PH7				
	XCOUT	PH6				
	RES#					
0	XTAL	P37				IRQ4
1	VSS					
2	EXTAL	P36				IRQ2
3	VCC					
4		P35				NMI
5		P34	MTIOC0A/TMCI3/POE2#	SCK6		IRQ4
6		P32	MTIOC0C/TMO3	TXD6/SMOSI6/SSDA6	TS0	IRQ2/RTCOUT
7		P31	MTIOC4D/TMCI2	CTS1#/RTS1#/SS1#	TS1	IRQ1
8		P30	MTIOC4B/TMRI3/POE8#	RXD1/SMISO1/SSCL1	TS2	IRQ0
9		P27	MTIOC2B/TMCI3	SCK1	TS3	
0		P26	MTIOC2A/TMO1/LPTO	TXD1/SMOSI1/SSDA1	TS4	
1		P21	MTIOC1B/TMCI0			
2		P20	MTIOC1A/TMRI0			
3	(5V tolerant)	P17	MTIOC3A/MTIOC3B/TMO1/ POE8#	SCK1/MISOA/SDA0		IRQ7
24	(5V tolerant)	P16	MTIOC3C/MTIOC3D/TMO2	TXD1/SMOSI1/SSDA1/MOSIA/SCL0		IRQ6/RTCOUT/ ADTRG0#
25		P15	MTIOC0B/MTCLKB/TMCI2	RXD1/SMISO1/SSCL1/CRXD0	TS5	IRQ5
6		P14	MTIOC3A/MTCLKA/TMRI2	CTS1#/RTS1#/SS1#/CTXD0	TS6	IRQ4
7	(5V tolerant)	P13	MTIOC0B/TMO3	SDA0		IRQ3
8	(5V tolerant)	P12	TMCI1	SCL0		IRQ2
9		PH3	MTIOC4D/TMCI0		TS7	
0		PH2	MTIOC4C/TMRI0		TS8	IRQ1
1		PH1	MTIOC3D/TMO0		TS9	IRQ0
2		PH0	MTIOC3B		TS10	CACREF
3		P55	MTIOC4A/MTIOC4D/TMO3	CRXD0	TS11	
4		P54	MTIOC4B/TMCI1	CTXD0	TS12	
5		PC7	MTCLKB/MTIOC3A/TMO2/ LPTO	MISOA/TXD8/SMOSI8/SSDA8	TS13	CACREF
6		PC6	MTIOC3C/MTCLKA/TMCI2	MOSIA/RXD8/SMISO8/SSCL8	TS14	
7		PC5	MTIOC0C/MTIOC3B/ MTCLKD/TMRI2	RSPCKA/SCK8	TS15	
8		PC4	MTIOC0A/MTIOC3D/ MTCLKC/TMCI1/POE0#	SCK5/CTS8#/RTS8#/SS8#/SSLA0	TSCAP	
9		PC3	MTIOC4D	TXD5/SMOSI5/SSDA5	TS16	
0		PC2	MTIOC4B	RXD5/SMISO5/SSCL5/SSLA3	TS17	
1		PB7/ PC1* ²	МТІОСЗВ	TXD9/SMOSI9/SSDA9	TS18	
2		PB6/ PC0* ²	MTIOC3D	RXD9/SMISO9/SSCL9	TS19	
13		PB5	MTIOC2A/MTIOC1B/TMRI1/ POE1#	SCK9	TS20	
44		PB4		CTS9#/RTS9#/SS9#	TS21	



Pin No.	Power Supply, Clock, System Control	I/O Port	Timers (MTU, TMR, POE, LPT)	Communications (SCIg, SCIh, SCIk, RSPI, RIIC, RSCAN)	Touch sensing	Others
45		PB3	MTIOC0A/MTIOC4A/TMO0/ POE3#/LPTO	SCK6	TS22	
46		PB2		CTS6#/RTS6#/SS6#	TS23	
47		PB1	MTIOC0C/MTIOC4C/TMCI0	TXD6/SMOSI6/SSDA6	TS24	IRQ4/CMPOB1
48	VCC					
49		PB0	MTIOC3D/MTIC5W	RXD6/SMISO6/SSCL6/RSPCKA	TS25	
50	VSS					
51		PA6	MTIOC3D/MTIC5V/ MTCLKB/TMCI3/POE2#	CTS5#/RTS5#/SS5#/MOSIA	TS26	
52		PA5		RSPCKA	TS27	
53		PA4	MTIOC4C/MTIC5U/ MTCLKA/TMRI0	TXD5/SMOSI5/SSDA5/SSLA0	TS28	IRQ5/CVREFB1
54		PA3	MTIOC0D/MTIOC4D/ MTIC5V/MTCLKD	RXD5/SMISO5/SSCL5	TS29	IRQ6/CMPB1
55		PA2		RXD5/SMISO5/SSCL5/SSLA3	TS30	
56		PA1	MTIOC0B/MTIOC3B/ MTCLKC	SCK5/SSLA2	TS31	
57		PA0	MTIOC4A	SSLA1	TS32	CACREF
58		PE5	MTIOC4C/MTIOC2B			IRQ5/AN021/CMPOB0
59		PE4	MTIOC4D/MTIOC1A/ MTIOC4A		TS33	AN020/CMPA2/ CLKOUT
60		PE3	MTIOC1B/MTIOC4B/POE8#	CTS12#/RTS12#/SS12#	TS34	AN019/CLKOUT
61		PE2	MTIOC4A	RXD12/RXDX12/SMISO12/SSCL12	TS35	IRQ7/AN018/CVREFB0
62		PE1	MTIOC4C	TXD12/TXDX12/SIOX12/SMOSI12/ SSDA12		AN017/CMPB0
63		PE0		SCK12		AN016
64		PD2	MTIOC4D	SCK6		IRQ2/AN026
65		PD1	MTIOC4B	RXD6/SMISO6/SSCL6		IRQ1/AN025
66		PD0		TXD6/SMOSI6/SSDA6		IRQ0/AN024
67		P47*1				AN007
68		P46*1				AN006
69		P45*1				AN005
70		P44*1				AN004
71		P43*1				AN003
72		P42*1				AN002
73		P41*1				AN001
74	VREFL0	PJ7*1				
75		P40*1				AN000
76	VREFH0	PJ6*1				
77	AVCC0					
78		P07*1				ADTRG0#
79	AVSS0					
80		P05*1				DA1

Table 1.5 List of Pins and Pin Functions (80-Pin LFQFP) (2/2)

Note 1. The power source of the I/O buffer for these pins is AVCC0.

Note 2. PC0 and PC1 are valid only when the port switching function is selected.



1.6.2 64-pin LFQFP, 64-pin LQFP

Table 1.6 List of Pins and Pin Functions (64-Pin LFQFP, 64-Pin LQFP) (1/2)

Pin No.	Power Supply, Clock, System Control	I/O Port	Timers (MTU, TMR, POE, LPT)	Communications (SCIg, SCIh, SCIk, RSPI, RIIC, RSCAN)	Touch sensing	Others
		P03*1				DA0
	VCL					
	MD	PG7				FINED
	XCIN	PH7* ³				
	XCOUT	PH6*3				
	RES#					
	XTAL	P37				IRQ4
	VSS					
	EXTAL	P36				IRQ2
0	VCC					
1		P35				NMI
2		P32	MTIOC0C/TMO3	TXD6*3/SMOSI6*3/SSDA6*3	TS0*3	IRQ2/RTCOUT
3		P31	MTIOC4D/TMCI2	CTS1#/RTS1#/SS1#	TS1*3	IRQ1
4		P30	MTIOC4B/TMRI3/POE8#	RXD1/SMISO1/SSCL1	TS2*3	IRQ0
5		P27	MTIOC2B/TMCI3	SCK1	TS3	
6		P26	MTIOC2A/TMO1/LPTO	TXD1/SMOSI1/SSDA1	TS4	
7	(5V tolerant)	P17	MTIOC3A/MTIOC3B/TMO1/ POE8#	SCK1/MISOA/SDA0		IRQ7
8	(5V tolerant)	P16	MTIOC3C/MTIOC3D/TMO2	TXD1/SMOSI1/SSDA1/MOSIA/SCL0		IRQ6/RTCOUT/ ADTRG0#
9		P15	MTIOC0B/MTCLKB/TMCl2	RXD1/SMISO1/SSCL1/CRXD0	TS5*3	IRQ5
0		P14	MTIOC3A/MTCLKA/TMRI2	CTS1#/RTS1#/SS1#/CTXD0	TS6*3	IRQ4
1		PH3	MTIOC4D/TMCI0		TS7*3	
2		PH2	MTIOC4C/TMRI0		TS8*3	IRQ1
3		PH1	MTIOC3D/TMO0		TS9*3	IRQ0
4		PH0	MTIOC3B		TS10*3	CACREF
5		P55	MTIOC4A/MTIOC4D/TMO3	CRXD0*3	TS11*3	
6		P54	MTIOC4B/TMCI1	CTXD0*3	TS12*3	
7		PC7	MTIOC3A/MTCLKB/TMO2/ LPTO	TXD8*3/SMOSI8*3/SSDA8*3/MISOA	TS13	CACREF
8		PC6	MTIOC3C/MTCLKA/TMCI2	RXD8* ³ /SMISO8* ³ /SSCL8* ³ /MOSIA	TS14	
9		PC5	MTIOC0C/MTIOC3B/ MTCLKD/TMRI2	SCK8 ^{*3} /RSPCKA	TS15	
80		PC4	MTIOC0A/MTIOC3D/ MTCLKC/TMCI1/POE0#	SCK5/CTS8#* ³ /RTS8#* ³ /SS8#* ³ / SSLA0	TSCAP	
1		PC3	MTIOC4D	TXD5/SMOSI5/SSDA5	TS16* ³	
2		PC2	MTIOC4B	RXD5/SMISO5/SSCL5/SSLA3	TS17* ³	
3		PB7/ PC1* ²	МТІОСЗВ	TXD9*3/SMOSI9*3/SSDA9*3	TS18* ³	
4		PB6/ PC0* ²	MTIOC3D	RXD9*3/SMISO9*3/SSCL9*3	TS19* ³	
85		PB5	MTIOC2A/MTIOC1B/TMRI1/ POE1#	SCK9*3	TS20* ³	
6		PB3	MTIOC0A/MTIOC4A/TMO0/ POE3#/LPTO	SCK6*3	TS22* ³	
7		PB1	MTIOC0C/MTIOC4C/TMCI0	TXD6*3/SMOSI6*3/SSDA6*3	TS24* ³	IRQ4/CMPOB1
8	VCC					
9		PB0	MTIOC3D/MTIC5W	RXD6*3/SMISO6*3/SSCL6*3/RSPCKA	TS25	
0	VSS					
1		PA6	MTIOC3D/MTIC5V/ MTCLKB/TMCI3/POE2#	CTS5#/RTS5#/SS5#/MOSIA	TS26* ³	
12		PA4	MTIOC4C/MTIC5U/ MTCLKA/TMRI0	TXD5/SMOSI5/SSDA5/SSLA0	TS28	IRQ5/CVREFB1
13		PA3	MTIOC0D/MTIOC4D/ MTIC5V/MTCLKD	RXD5/SMISO5/SSCL5	TS29	IRQ6/CMPB1



Pin No.	Power Supply, Clock, System Control	I/O Port	Timers (MTU, TMR, POE, LPT)	Communications (SCIg, SCIh, SCIk, RSPI, RIIC, RSCAN)	Touch sensing	Others
44		PA1	MTIOC0B/MTIOC3B/ MTCLKC	SCK5/SSLA2	TS31	
45		PA0	MTIOC4A	SSLA1	TS32* ³	CACREF
46		PE5	MTIOC4C/MTIOC2B			IRQ5/AN021/CMPOB0
47		PE4	MTIOC4D/MTIOC1A/ MTIOC4A		TS33	AN020/CMPA2/ CLKOUT
48		PE3	MTIOC1B/MTIOC4B/POE8#	CTS12#/RTS12#/SS12#	TS34	AN019/CLKOUT
49		PE2	MTIOC4A	RXD12/RXDX12/SMISO12/SSCL12	TS35	IRQ7/AN018/CVREFB0
50		PE1	MTIOC4C	TXD12/TXDX12/SIOX12/SMOSI12/ SSDA12		AN017/CMPB0
51		PE0		SCK12		AN016
52		P47*1				AN007
53		P46*1				AN006
54		P45* ¹				AN005
55		P44* ¹				AN004
56		P43*1				AN003
57		P42*1				AN002
58		P41* ¹				AN001
59	VREFL0	PJ7*1				
60		P40*1				AN000
61	VREFH0	PJ6*1				
62	AVCC0					
63		P05*1				DA1
64	AVSS0					

Table 1.6List of Pins and Pin Functions (64-Pin LFQFP, 64-Pin LQFP) (2/2)

Note 1. The power source of the I/O buffer for these pins is AVCCO.

Note 2. PC0 and PC1 are valid only when the port switching function is selected.

Note 3. This is not supported by products with 64 Kbytes of ROM.



1.6.3 48-pin LFQFP, 48-pin HWQFN

Table 1.7 List of Pins and Pin Functions (48-Pin LFQFP, 48-Pin HWQFN) (1/2)

Pin No.	Power Supply, Clock, System Control	I/O Port	Timers (MTU, TMR, POE, LPT)	Communications (SCIg, SCIh, SCIk, RSPI, RIIC, RSCAN)	Touch sensing	Others
1	VCL					
2	MD	PG7				FINED
3	RES#					
4	XTAL	P37				IRQ4
5	VSS					
6	EXTAL	P36				IRQ2
7	VCC					
8		P35				NMI
9		P31	MTIOC4D/TMCI2	CTS1#/RTS1#/SS1#	TS1* ³	IRQ1
10		P30	MTIOC4B/TMRI3/POE8#	RXD1/SMISO1/SSCL1	TS2* ³	IRQ0
11		P27	MTIOC2B/TMCI3	SCK1	TS3	
12		P26	MTIOC2A/TMO1/LPTO	TXD1/SMOSI1/SSDA1	TS4	
13	(5V tolerant)	P17	MTIOC3A/MTIOC3B/TMO1/POE8#	SCK1/MISOA/SDA0		IRQ7
14	(5V tolerant)	P16	MTIOC3C/MTIOC3D/TMO2	TXD1/SMOSI1/SSDA1/MOSIA/SCL0		IRQ6/ ADTRG0#/ RTCOUT
15		P15	MTIOC0B/MTCLKB/TMCI2	RXD1/SMISO1/SSCL1/CRXD0*3	TS5* ³	IRQ5
16		P14	MTIOC3A/MTCLKA/TMRI2	CTS1#/RTS1#/SS1#/CTXD0*3	TS6* ³	IRQ4
17		PH3	MTIOC4D/TMCI0		TS7*3	
18		PH2	MTIOC4C/TMRI0		TS8*3	IRQ1
19		PH1	MTIOC3D/TMO0		TS9* ³	IRQ0
20		PH0	MTIOC3B		TS10* ³	CACREF
21		PC7	MTIOC3A/TMO2/MTCLKB/LPTO	TXD8*3/SMOSI8*3/SSDA8*3/MISOA	TS13	CACREF
22		PC6	MTIOC3C/MTCLKA/TMCI2	RXD8*3/SMISO8*3/SSCL8*3/MOSIA	TS14	
23		PC5	MTIOC0C/MTIOC3B/MTCLKD/ TMRI2	SCK8 ^{*3} /RSPCKA	TS15	
24		PC4	MTIOC0A/MTIOC3D/MTCLKC/ TMCI1/POE0#	SCK5/CTS8#* ³ /RTS8#* ³ /SS8#* ³ / SSLA0	TSCAP	
25		PB5/PC3*1	MTIOC2A/MTIOC1B/TMRI1/POE1#		TS20*3	
26		PB3/PC2*1	MTIOC0A/MTIOC4A/TMO0/POE3#/ LPTO	SCK6*3	TS22*3	
27		PB1/PC1*1	MTIOC0C/MTIOC4C/TMCI0	TXD6*3/SMOSI6*3/SSDA6*3	TS24*3	IRQ4/CMPOB
28	VCC					
29		PB0/PC0*1	MTIOC3D/MTIC5W	RXD6*3/SMISO6*3/SSCL6*3/ RSPCKA	TS25	
30	VSS					
31		PA6	MTIOC3D/MTIC5V/MTCLKB/TMCI3/ POE2#	CTS5#/RTS5#/SS5#/MOSIA	TS26*3	
32		PA4	MTIOC4C/MTIC5U/MTCLKA/TMRI0	TXD5/SMOSI5/SSDA5/SSLA0	TS28	IRQ5/ CVREFB1
33		PA3	MTIOC0D/MTIOC4D/MTIC5V/ MTCLKD	RXD5/SMISO5/SSCL5	TS29	IRQ6/CMPB1
34		PA1	MTIOC0B/MTIOC3B/MTCLKC	SCK5/SSLA2	TS31	
35		PE4	MTIOC4D/MTIOC1A/MTIOC4A		TS33	AN020/ CMPA2/ CLKOUT
36		PE3	MTIOC1B/MTIOC4B/POE8#	CTS12#/RTS12#	TS34	AN019/ CLKOUT
37		PE2	MTIOC4A	RXD12/RXDX12/SSCL12	TS35	IRQ7/AN018/ CVREFB0
38		PE1	MTIOC4C	TXD12/TXDX12/SIOX12/SSDA12	1	AN017/CMPB0
39		P47* ²			1	AN007
40		P46* ²			1	AN006
41		P45* ²			1	AN005
42		P42* ²			1	AN002
43		P41* ²	1		1	AN001



Pin No.	Power Supply, Clock, System Control	I/O Port	Timers (MTU, TMR, POE, LPT)	Communications (SClg, SClh, SClk, RSPI, RIIC, RSCAN)	Touch sensing	Others
44	VREFL0	PJ7*2				
45		P40* ²				AN000
46	VREFH0	PJ6* ²				
47	AVCC0					
48	AVSS0					

Table 1.7 List of Pins and Pin Functions (48-Pin LFQFP, 48-Pin HWQFN) (2/2)

Note 1. PC0 to PC3 are valid only when the port switching function is selected.

Note 2. The power source of the I/O buffer for these pins is AVCCO.

Note 3. This is not supported by products with 64 Kbytes of ROM.



1.6.4 32-pin LQFP, 32-pin HWQFN

Table 1.8	List of Pins and Pin Functions (32-Pin LQFP, 32-Pin HWQFN)

Pin No.	Power Supply, Clock, System Control	I/O Port	Timers (MTU, TMR, POE, LPT)	Communications (SCIg, SCIh, SCIk, RSPI, RIIC)	Touch sensing	Others
1	MD	PG7				FINED
2	RES#					
3	VSS					
4	EXTAL	P36				IRQ2
5	VCC					
6		P35				NMI
7		P31	MTIOC4D/TMCI2	CTS1#/RTS1#/SS1#		IRQ1
8		P30	MTIOC4B/TMRI3/POE8#	RXD1/SMISO1/SSCL1		IRQ0
9		P27	MTIOC2B/TMCI3	SCK1	TS3	
10		P26	MTIOC2A/TMO1/LPTO	TXD1/SMOSI1/SSDA1	TS4	
11	(5V tolerant)	P17	MTIOC3A/MTIOC3B/TMO1/ POE8#	SCK1/MISOA/SDA0		IRQ7
12	(5V tolerant)	P16	MTIOC3C/MTIOC3D/TMO2	TXD1/SMOSI1/SSDA1/MOSIA/ SCL0		IRQ6/ADTRG0#/ RTCOUT
13		PC7	MTIOC3A/MTCLKB/TMO2/ LPTO	MISOA	TS13	CACREF
14		PC6	MTIOC3C/MTCLKA/TMCI2	MOSIA	TS14	
15		PC5	MTIOC0C/MTIOC3B/ MTCLKD/TMRI2	RSPCKA	TS15	
16		PC4	MTIOC0A/MTIOC3D/ MTCLKC/TMCI1/POE0#	SCK5/SSLA0	TSCAP	
17	VCC					
18		PB0	MTIOC3D/MTIC5W	RSPCKA	TS25	
19	VSS					
20		PA4	MTIOC4C/MTIC5U/MTCLKA/ TMRI0	TXD5/SMOSI5/SSDA5/SSLA0	TS28	IRQ5/CVREFB1
21		PA3	MTIOC0D/MTIOC4D/ MTIC5V/MTCLKD	RXD5/SMISO5/SSCL5	TS29	IRQ6/CMPB1
22		PA1	MTIOC0B/MTIOC3B/ MTCLKC	SCK5/SSLA2	TS31	
23		PE4	MTIOC1A/MTIOC4A/ MTIOC4D		TS33	AN020/CMPA2/ CLKOUT
24		PE3	MTIOC1B/MTIOC4B/POE8#	CTS12#/RTS12#	TS34	AN019/CLKOUT
25		PE2	MTIOC4A	RXD12/SSCL12/RXDX12	TS35	IRQ7/AN018/CVREFB0
26		PE1	MTIOC4C	TXD12/SSDA12/TXDX12/SIOX12		AN017/CMPB0
27		P42*1				AN002
28		P41* ¹				AN001
29		P40*1				AN000
30	AVCC0/VREFH0					
31	AVSS0/VREFL0					
32	VCL					

Note 1. The power source of the I/O buffer for these pins is AVCC0.



2. Electrical Characteristics

2.1 Absolute Maximum Ratings

Table 2.1Absolute Maximum Ratings

Conditions: VSS = AVSS0 = VREFL0 = 0 V

	Item	Symbol	Value	Unit	
Power supply vo	bltage	VCC	-0.3 to +6.5	V V	
Input voltage	Ports for 5 V tolerant: P12, P13, P16, P17	V _{in}	-0.3 to +6.5		
	P03 to P07, P40 to P47, PJ6, PJ7		-0.3 to AVCC0 + 0.3	V	
	Ports other than above		-0.3 to VCC + 0.3		
Reference power supply voltage		VREFH0	-0.3 to AVCC0 + 0.3	V	
Analog power s	upply voltage	AVCC0	-0.3 to +6.5	V	
Analog input	When AN000 to AN007 used	V _{AN}	-0.3 to AVCC0 + 0.3	V	
voltage	When AN016 to AN021, AN024 to AN026 used		-0.3 to VCC + 0.3		
Junction	D-version	Тj	-40 to +105	°C	
temperature	G-version		-40 to +112	7	
Storage temperature		T _{stg}	-55 to +125	°C	

Caution: Permanent damage to the MCU may result if absolute maximum ratings are exceeded.

To preclude any malfunctions due to noise interference, insert capacitors of high frequency characteristics between the VCC and VSS pins, between the AVCC0 and AVSS0 pins, and between the VREFH0 and VREFL0 pins. Place capacitors of about 0.1 µF as close as possible to every power supply pin and use the shortest and heaviest possible traces.

Connect the VCL pin to a VSS pin via a 4.7 µF capacitor. The capacitor must be placed close to the pin, refer to section 2.15.1, Connecting VCL Capacitor and Bypass Capacitors.

Do not input signals or an I/O pull-up power supply to ports other than 5-V tolerant ports while the device is not powered.

The current injection that results from input of such a signal or I/O pull-up may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements.

Even if -0.3 to +6.5 V is input to 5-V tolerant ports, it will not cause problems such as damage to the MCU.



2.2 Recommended Operating Conditions

Item	Symbol	Symbol	Min.	Тур.	Max.	Unit
Power supply voltage	ges	VCC*1, *2	1.8	—	5.5	V
		VSS	_	0	—	
Analog power supp	ly voltages	AVCC0*1	1.8	—	5.5	V
		AVSS0	_	0	—	
		VREFH0	1.8	—	AVCC0	
		VREFL0	_	0	—	
Input voltage	Ports for 5 V tolerant: P12, P13, P16, P17	V _{in}	-0.3	—	5.8	V
	P03 to P07, P40 to P47, PJ6, PJ7		-0.3		AVCC0 + 0.3	
	Ports other than above		-0.3	—	VCC + 0.3	
Operating	D version	T _{opr}	-40	—	85	°C
temperature ^{*3}	G version	1	-40	_	105	

Table 2.2 Recommended Operating Conditions (1)

When powering on the VCC and AVCC0 pins, power them on at the same time or the VCC pin first and then the AVCC0 pin.
 When VCC < 2.4 V, normal operating mode functions of the CTSU are restricted. For details, refer to section 32, Capacitive Touch Sensing Unit (CTSU2SL, CTSU2L) in the User's Manual: Hardware.

Note 3. The upper limit of operating temperature is 85°C or 105°C, depending on the product. For details, refer to section 1.2, List of Products.

Table 2.3	Recommended Operating Conditions (2)
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Item	Symbol	Value
Decoupling capacitance for stabilizing the internal voltage	C _{VCL}	4.7µF ± 30%*1

Note 1. Use a multilayer ceramic capacitor with a nominal capacitance of $4.7 \ \mu$ F, for which the sum of the capacitance tolerance and change in the capacitance under the usage conditions will be no greater than $\pm 30\%$.



2.3 **DC** Characteristics

Table 2.4 DC Characteristics (1)

Conditions: 2.7 V ≤ VCC ≤ 5.5 V, 2.7 V ≤ AVCC0 ≤ 5.5 V, VSS = AVSS0 = 0 V, $T_a = -40$ to +105°C

	ltem	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Schmitt trigger	RIIC input pin (except for SMBus)	V _{IH}	0.7 × VCC	—	—	V	
input voltage		V _{IL}	—	_	0.3 × VCC		
		ΔV _T	0.05 × VCC		—	-	
	IRQ input pin, MTU2 input pin, POE2 input pin, TMR input pin,	V _{IH}	0.8 × VCC		_		
	SCI input pin, RSPI input pin, CAC input pin, CAN input pin,	V _{IL}	—		0.2 × VCC		
	ADTRG0# input pin* ¹ , RES#, NMI, MD	ΔV_T	0.1 × VCC	—	—		
	ADTRG0# input pin*2	V _{IH}	0.8 × AVCC0	_	—		
		V _{IL}	—	_	0.2 × AVCC0		
		ΔV_T	0.1 × AVCC0	_	—		
Input level	EXTAL (external clock input)	V _{IH}	0.8 × VCC	_	—	V	
voltage (except for schmitt		V _{IL}	—	_	0.2 × VCC		
trigger input pins)	RIIC input pin (SMBus) P12 to P17, P20, P21, P26, P27, P30 to P32, P34 to P37, P54, P55, PA0 to PA6, PB0 to PB7, PC2 to PC7, PD0 to PD2, PE0 to PE5, PH0 to PH3, PH6* ³ , PH7* ³ PJ1, PG7	V _{IH}	2.2	_	_		VCC = 3.6 to 5.5 V
			2.0	—	_		VCC = 2.7 to 3.6 V
		V _{IL}	—		0.8		VCC = 3.6 to 5.5 V
			-	_	0.5		VCC = 2.7 to 3.6 V
		V _{IH}	0.8 × VCC	_	_		
		V _{IL}	-	_	0.2 × VCC		
	P03 to P07,	V _{IH}	0.8 × AVCC	_	_		
	P40 to P47, PJ6, PJ7	V _{IL}	—	_	0.2 × AVCC		

Note 1. The ADTRG0# input pin is assigned to P16.

Note 2. The ADTRG0# input pin is assigned to P07. Note 3. This pin function is not provided for products with 64 Kbytes of ROM.



Table 2.5DC Characteristics (2)

Conditions: 1.8 V \leq VCC < 2.7 V, 1.8 V \leq AVCC0 < 2.7 V, VSS = AVSS0 = 0 V, T_a = -40 to +105°C

	Item	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Schmitt trigger input voltage	IRQ input pin, MTU2 input pin, POE2 input pin, TMR input pin,	V _{IH}	0.8 × VCC		—	V	
	SCI input pin, RSPI input pin, CAC input pin, CAN input pin,	V _{IL}	—	_	0.2 × VCC		
	ADTRG0# input pin* ¹ , RES#, NMI, MD	ΔV_T	0.01 × VCC	—	—		
	ADTRG0# input pin*2	V _{IH}	0.8 × AVCC0	_	—		
		V _{IL}	—	_	0.2 × AVCC0		
		ΔV _T	0.01 × AVCC0	_	—		
Input level	EXTAL (external clock input)	V _{IH}	0.8 × VCC	_	—	V	
voltage (except for schmitt		V _{IL}	—	_	0.2 × VCC		
trigger input pins)	P12 to P17, P20, P21, P26, P27, P30 to P32, P34 to P37, P54, P55, PA0 to PA6, PB0 to PB7,	V _{IH}	0.8 × VCC	_	_		
	PE0 to PE7, PC2 to PC7, PD0 to PD2, PE0 to PE5, PH0 to PH3, PH6* ³ , PH7* ³ PJ1, PG7	V _{IL}	_	_	0.2 × VCC		
	P03 to P07,	V _{IH}	0.8 × AVCC	_	_		
	P40 to P47, PJ6, PJ7	V _{IL}	—	_	0.2 × AVCC	1	

Note 1. The ADTRG0# input pin is assigned to P16.

Note 2. The ADTRG0# input pin is assigned to P07.

Note 3. This pin function is not provided for products with 64 Kbytes of ROM.

Table 2.6DC Characteristics (3)

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}, 1.8 \text{ V} \le \text{AVCC0} \le 5.5 \text{ V}, \text{VSS} = \text{AVSS0} = 0 \text{ V}, \text{ T}_{a} = -40 \text{ to } +105^{\circ}\text{C}$

	Symbol	Min.	Тур.	Max.	Unit	Test Conditions	
Input leakage current	RES#, P35, PH6*1, PH7*1	I _{in}		_	1.0	μA	V _{in} = 0 V, VCC
Three-state leakage	Ports for 5-V tolerant	I _{TSI}	—	—	1.0	μA	V _{in} = 0 V, 5.8 V
current (off-state)	PJ6, PJ7		V _{in} = 0 V, VCC				
	Other than ports for 5 V tolerant and PJ6, PJ7		_	_	0.2		V _{in} = 0 V, VCC
Input capacitance	All input pins (except for P35)	C _{in}	—	—	15	pF	V _{in} = 0 mV, f = 1 MHz,
	P35			—	30		T _a = 25°C

Note 1. This pin function is not provided for products with 64 Kbytes of ROM.

Table 2.7 DC Characteristics (4)

Conditions: $1.8 \text{ V} \le \text{VCC} < 5.5 \text{ V}$, $1.8 \text{ V} \le \text{AVCC0} < 5.5 \text{ V}$, VSS = AVSS0 = 0 V, $\text{T}_{a} = -40 \text{ to } +105^{\circ}\text{C}$

	Symbol	Min.	Тур.	Max.	Unit	Test Conditions	
Input pull-up resistor	All ports (except for P35, PH6*1, PH7*1)	R _U	10	20	50	kΩ	V _{in} = 0 V

Note 1. This pin function is not provided for products with 64 Kbytes of ROM.



[Products with 64-Kbyte ROM]

Table 2.8DC Characteristics (5)

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}, 1.8 \text{ V} \le \text{AVCC0} \le 5.5 \text{ V}, \text{VSS} = \text{AVSS0} = 0 \text{ V}, \text{ T}_{a} = -40 \text{ to } +105^{\circ}\text{C}$

	Item					Typ. *4	Max.		Test Conditions
Supply	High-speed	Normal	No peripheral	ICLK = 48 MHz	I _{CC}	2.5	_	mA	
current*1	operating mode	operating mode	operation* ²	ICLK = 32 MHz		1.8	_		
				ICLK = 16 MHz		1.3	_		
				ICLK = 8 MHz		1.0	_		
			All peripheral	ICLK = 48 MHz		9.0	_		
			operation: Normal* ³	ICLK = 32 MHz		7.4	_		
				ICLK = 16 MHz		4.2	_		
				ICLK = 8 MHz		2.5	_		
			All peripheral operation: Max.* ³	ICLK = 48 MHz		_	20.1		
		Sleep mode	No peripheral	ICLK = 48 MHz		1.4	—		
			operation* ²	ICLK = 32 MHz		1.1	—		
				ICLK = 16 MHz		0.8	_		
				ICLK = 8 MHz		0.7	_		
			All peripheral	ICLK = 48 MHz		4.0	_		
			operation: Normal* ³	ICLK = 32 MHz		4.0	_		
				ICLK = 16 MHz		2.3	_		
				ICLK = 8 MHz		1.5	_		
		Deep sleep	No peripheral	ICLK = 48 MHz		1.0	—		
		mode	operation* ²	ICLK = 32 MHz		0.8	—		
				ICLK = 16 MHz		0.7	—		
				ICLK = 8 MHz		0.6	—		
			All peripheral	ICLK = 48 MHz		3.1	—		
			operation: Normal* ³	ICLK = 32 MHz		3.1	—		
				ICLK = 16 MHz		1.9	—		
				ICLK = 8 MHz		1.2	_		
		Increase during f	lash rewrite ^{*5}			2.1	_		
	Middle-speed	Normal	No peripheral	ICLK = 24 MHz		1.6	—		
	operating mode	operating mode	operation* ⁶	ICLK = 8 MHz		0.8	—		
				ICLK = 4 MHz		0.3	—		
				ICLK = 1 MHz		0.2	—		
			All peripheral	ICLK = 24 MHz		5.8	—		
			operation: Normal*7	ICLK = 8 MHz		2.3	—		
				ICLK = 4 MHz		1.5	—		
				ICLK = 1 MHz		0.8	—		
			All peripheral operation: Max.* ⁷	ICLK = 24 MHz		_	13.1		
		Sleep mode	No peripheral	ICLK = 24 MHz		1.1	—		
			operation* ⁶	ICLK = 8 MHz		0.6	—		
				ICLK = 4 MHz		0.2	—		
				ICLK = 1 MHz		0.2	_		



		Item			Symbol	Typ. *4	Max.		Test Conditions
Supply	Middle-speed			ICLK = 24 MHz	I _{CC}	3.3	_	mA	
current*1	current*1 operating mode	de op	operation: Normal* ⁷	ICLK = 8 MHz		1.5	_		
				ICLK = 4 MHz		1.0	_		
				ICLK = 1 MHz		0.7	_		
		Deep sleep	No peripheral	ICLK = 24 MHz		0.8	_		
		mode	operation* ⁶	ICLK = 8 MHz		0.5	_		
				ICLK = 4 MHz		0.1	_		
				ICLK = 1 MHz		0.1	_		
			All peripheral	ICLK = 24 MHz		2.6	_		
			operation: Normal* ⁷	ICLK = 8 MHz		1.3	_		
				ICLK = 4 MHz		0.9	_		
				ICLK = 1 MHz		0.7	_		
		Increase during f	lash rewrite* ⁵			2.1	_		
	Middle-speed operating	Normal operating mode	No peripheral operation* ⁸	ICLK = 1 MHz		0.1			
	mode 2		All peripheral operation: Normal* ⁹	ICLK = 1 MHz		0.8	_	-	
			All peripheral operation: Max.* ⁹	ICLK = 1 MHz			3.0		
		Sleep mode Deep sleep mode	No peripheral operation* ⁸	ICLK = 1 MHz		0.1	—		
			All peripheral operation: Normal* ⁹	ICLK = 1 MHz		0.7	—		
			No peripheral operation* ⁸	ICLK = 1 MHz		0.1		-	
			All peripheral operation: Normal* ⁹	ICLK = 1 MHz		0.7	_		
		Increase during f	lash rewrite*5			1.4	_		
	Low-speed operating mode	Normal operating mode	No peripheral operation* ¹⁰	ICLK = 32.768 kHz		2.4	—	μA	
			All peripheral operation: Normal* ^{11, *12}	ICLK = 32.768 kHz		7.5		-	
			All peripheral operation: Max. *11, *12	ICLK = 32.768 kHz			88.4		
		Sleep mode	No peripheral operation* ¹⁰	ICLK = 32.768 kHz		1.4	_		
			All peripheral operation: Normal* ¹¹	ICLK = 32.768 kHz		3.8	—		
		Deep sleep mode	No peripheral operation* ¹⁰	ICLK = 32.768 kHz		1.0	—		
			All peripheral operation: Normal* ¹¹	ICLK = 32.768 kHz		2.8			

Note 1. Supply current values do not include output charge/discharge current from all pins. The values apply when internal pull-up MOSs are in the off state.

Note 2. Clock supply to the peripheral functions is stopped. This does not include BGO operation. The clock source is PLL. FCLK and PCLK are set to divided by 64.

Note 3. Clocks are supplied to the peripheral functions. This does not include BGO operation. The clock source is PLL. FCLK is set to the same frequency as ICLK and PCLK is set to divided by 2 when ICLK is 48 MHz. FCLK and PCLK are set to the same frequency as ICLK when ICLK is 32 MHz or less.

Note 4. Values when VCC = 3.3 V.

Note 5. This is the increase for programming or erasure of the ROM or E2 DataFlash during program execution.

Note 6. Clock supply to the peripheral function is stopped. The clock source is PLL when ICLK is 24 MHz, HOCO when ICLK is 8 MHz, and LOCO otherwise. FCLK and PCLK are set to divided by 64.

Note 7. Clocks are supplied to the peripheral functions. The clock source is PLL when ICLK is 24 MHz, HOCO when ICLK is (MHz, and LOCO otherwise. FCLK and PCLK are set to the same frequency as ICLK.

Note 8. Clock supply to the peripheral function is stopped. The clock source is LOCO when ICLK is 1 MHz, FCLK and PCLK are set to divided by 64.

Note 9. Clocks are supplied to the peripheral functions. The clock source is LOCO when ICLK is 1 MHz, FCLK and PCLK are set to the same frequency as ICLK.

Note 10. Clock supply to the peripheral functions is stopped. The clock source is the sub-clock oscillator. FCLK and PCLK are set to divided by 64.

Note 11. Clocks are supplied to the peripheral functions. The clock source is the sub-clock oscillator. FCLK and PCLK are set to the same frequency as ICLK.

Note 12. Values when the MSTPCRA.MSTPA17 bit (12-bit A/D converter module stop bit) is set to "transition to the module stop state is made".



RENESAS



Kbyte ROM)





Figure 2.3 Voltage Dependency in Middle-Speed Operating Mode 2 (Reference Data for Products with 64-Kbyte ROM)





Figure 2.4 Voltage Dependency in Low-Speed Operating Mode (Reference Data for Products with 64-Kbyte ROM)



[Products with 128-Kbyte or larger ROM]

Table 2.9DC Characteristics (5)

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $1.8 \text{ V} \le \text{AVCC0} \le 5.5 \text{ V}$, VSS = AVSS0 = 0 V, $\text{T}_{a} = -40 \text{ to } +105^{\circ}\text{C}$

		Item			Symbol	Typ. *4	Max.	Unit	Test Conditions
Supply	High-speed			ICLK = 48 MHz	I _{CC}	2.6		mA	<u> </u>
	operating mode	operating mode	operation*2	ICLK = 32 MHz		1.9	_		
				ICLK = 16 MHz		1.3	_		
				ICLK = 8 MHz		1.0	_		
			All peripheral	ICLK = 48 MHz		10.4	—		
			operation: Normal*3	ICLK = 32 MHz		8.9	_		
				ICLK = 16 MHz		4.9	_		
				ICLK = 8 MHz		2.9	_		
			All peripheral operation: Max.* ³	ICLK = 48 MHz			22.8		
		Sleep mode	No peripheral	ICLK = 48 MHz		1.4	_		
			operation* ²	ICLK = 32 MHz		1.1	_		
				ICLK = 16 MHz		0.8	_		
				ICLK = 8 MHz		0.7	_		
			All peripheral	ICLK = 48 MHz		4.7	—		
			operation: Normal*3	ICLK = 32 MHz		4.9	_		
				ICLK = 16 MHz		2.8	_		
				ICLK = 8 MHz		1.7	_		
		Deep sleep mode	No peripheral operation* ²	ICLK = 48 MHz		1.0	—		
				ICLK = 32 MHz		0.8	—		
				ICLK = 16 MHz		0.7	—		
				ICLK = 8 MHz		0.6	—		
			All peripheral	ICLK = 48 MHz		3.7	—		
		operation: Normal*	operation: Normal*3	ICLK = 32 MHz	-	3.9			
				ICLK = 16 MHz		2.3	—		
				ICLK = 8 MHz		1.4	—		
		Increase during flash rewrite*5					—		
		Increase during encryption function operation					3.9		
	Middle-speed	Normal	No peripheral	ICLK = 24 MHz		1.7	—		
	operating mode	operating mode	operation*6	ICLK = 8 MHz		0.9	—		
				ICLK = 4 MHz		0.3	—		
				ICLK = 1 MHz		0.2	_		
			All peripheral	ICLK = 24 MHz		6.9	—		
			operation: Normal*7	ICLK = 8 MHz		2.8	_		
				ICLK = 4 MHz		1.7	_		
				ICLK = 1 MHz		0.9	—		
			All peripheral operation: Max.* ⁷	ICLK = 24 MHz			15.4		
		Sleep mode	No peripheral	ICLK = 24 MHz		1.1	_		
			operation* ⁶	ICLK = 8 MHz		0.7	—		
				ICLK = 4 MHz		0.2	_		
				ICLK = 1 MHz]	0.2	_		



		Item			Symbol	Typ. *4	Max.	Unit	Test Conditions
Supply		Sleep mode	All peripheral	ICLK = 24 MHz	I _{CC}	4.0	—	mA	
current*1 operatin	operating mode		operation: Normal*7	ICLK = 8 MHz		1.8			
				ICLK = 4 MHz		1.2	_		
				ICLK = 1 MHz		0.8	_		
		Deep sleep	No peripheral	ICLK = 24 MHz		0.8	_		
		mode	operation* ⁶	ICLK = 8 MHz		0.6			
				ICLK = 4 MHz		0.1			
				ICLK = 1 MHz		0.1			
			All peripheral	ICLK = 24 MHz		3.2			
			operation: Normal*7	ICLK = 8 MHz		1.5	_		
				ICLK = 4 MHz		1.0			
				ICLK = 1 MHz		0.7			
		Increase during f	lash rewrite* ⁵			2.1			
	Middle-speed operating	Normal operating mode	No peripheral operation* ⁸	ICLK = 1 MHz		0.1			
	mode 2		All peripheral operation: Normal* ⁹	ICLK = 1 MHz		0.9		-	
			All peripheral operation: Max.* ⁹	ICLK = 1 MHz			3.3		
		Sleep mode Deep sleep mode	No peripheral operation* ⁸	ICLK = 1 MHz		0.1	—		
			All peripheral operation: Normal* ⁹	ICLK = 1 MHz		0.7	_		
			No peripheral operation* ⁸	ICLK = 1 MHz		0.1			
			All peripheral operation: Normal* ⁹	ICLK = 1 MHz		0.7	—		
		Increase during f	lash rewrite*5			1.4			
	Low-speed operating mode	Normal operating mode	No peripheral operation* ¹⁰	ICLK = 32.768 kHz		2.6		μA	
			All peripheral operation: Normal* ^{11, *12}	ICLK = 32.768 kHz		9.4		-	
			All peripheral operation: Max. *11, *12	ICLK = 32.768 kHz	-		175.4		
		Sleep mode	No peripheral operation* ¹⁰	ICLK = 32.768 kHz		1.5	—		
			All peripheral operation: Normal* ¹¹	ICLK = 32.768 kHz		5.1	—		
		Deep sleep mode	No peripheral operation* ¹⁰	ICLK = 32.768 kHz		1.3	—		
			All peripheral operation: Normal* ¹¹	ICLK = 32.768 kHz		4.1	—		

Note 1. Supply current values do not include output charge/discharge current from all pins. The values apply when internal pull-up MOSs are in the off state.

Note 2. Clock supply to the peripheral functions is stopped. This does not include BGO operation. The clock source is PLL. FCLK and PCLK are set to divided by 64.

Note 3. Clocks are supplied to the peripheral functions. This does not include BGO operation. The clock source is PLL. FCLK is set to the same frequency as ICLK and PCLK is set to divided by 2 when ICLK is 48 MHz. FCLK and PCLK are set to the same frequency as ICLK when ICLK is 32 MHz or less.

Note 4. Values when VCC = 3.3 V.
Note 5. This is the increase for programming or erasure of the ROM or E2 DataFlash during program execution.

Note 6. Clock supply to the peripheral function is stopped. The clock source is PLL when ICLK is 24 MHz, HOCO when ICLK is 8 MHz, and LOCO otherwise. FCLK and PCLK are set to divided by 64.

Note 7. Clocks are supplied to the peripheral functions. The clock source is PLL when ICLK is 24 MHz, HOCO when ICLK is (MHz, and LOCO otherwise. FCLK and PCLK are set to the same frequency as ICLK.

Note 8. Clock supply to the peripheral function is stopped. The clock source is LOCO when ICLK is 1 MHz, FCLK and PCLK are set to divided by 64.

Note 9. Clocks are supplied to the peripheral functions. The clock source is LOCO when ICLK is 1 MHz, FCLK and PCLK are set to the same frequency as ICLK.

Note 10. Clock supply to the peripheral functions is stopped. The clock source is the sub-clock oscillator. FCLK and PCLK are set to divided by 64.

Note 11. Clocks are supplied to the peripheral functions. The clock source is the sub-clock oscillator. FCLK and PCLK are set to the same frequency as ICLK.

Note 12. Values when the MSTPCRA.MSTPA17 bit (12-bit A/D converter module stop bit) is set to "transition to the module stop state is made".



or Larger ROM)

RENESAS



Kbyte or Larger ROM)









Figure 2.8 Voltage Dependency in Low-Speed Operating Mode (Reference Data for Products with 128-Kbyte or Larger ROM)



[Products with 64-Kbyte ROM]

Table 2.10DC Characteristics (6)

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $1.8 \text{ V} \le \text{AVCC0} \le 5.5 \text{ V}$, VSS = AVSS0 = 0 V, $\text{T}_{a} = -40 \text{ to } +105^{\circ}\text{C}$

	Item		Symbol	Typ.* ³	Max.	Unit	Test Conditions
Supply	Software standby	T _a = 25°C	I _{CC}	0.25	1.56	μA	
current*1	mode*2	T _a = 55°C		0.54	4.66		
		T _a = 85°C		1.86	18.09		
		T _a = 105°C		4.72	43.74		
	Increment for RTC	operation*4		0.97	_		SOMCR.SODRV[1:0] set to drive capacity for standard CL
	0.52 —			SOMCR.SODRV[1:0] set to high drive capacity for low CL			
				0.27	_		SOMCR.SODRV[1:0] set to middle drive capacity for low CL
				0.17	_		SOMCR.SODRV[1:0] set to low drive capacity for low CL
	Increment for low- operation	power timer		0.28	_		LPTCR1.LPCNTCKSEL set to IWDT- dedicated on-chip oscillator
				15.97	_		LPTCR1.LPCNTCKSEL 2 set to Low-speed on-chip oscillator
	Increment for inde watchdog timer op			0.26	—		

Note 1. Supply current values are with all output pins unloaded and all input pull-up MOSs in the off state.

Note 2. The IWDT, LVD, and CMPB are stopped. Note 3. VCC = 3.3 V. Note 4. Includes the oscillation circuit.





Figure 2.9 Voltage Dependency in Software Standby Mode (Reference Data for Products with 64-Kbyte ROM)



Figure 2.10 Temperature Dependency in Software Standby Mode (Reference Data for Products with 64-Kbyte ROM)

[Products with 128-Kbyte or larger ROM]

Table 2.11DC Characteristics (6)

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}, 1.8 \text{ V} \le \text{AVCC0} \le 5.5 \text{ V}, \text{VSS} = \text{AVSS0} = 0 \text{ V}, \text{ T}_{a} = -40 \text{ to } +105^{\circ}\text{C}$

							-
	Item		Symbol	Typ.* ³	Max.		Test Conditions
Supply	Software standby	T _a = 25°C	I _{CC}	0.43	2.07	μA	
current*1	mode* ²	T _a = 55°C		1.00	8.46		
		T _a = 85°C		3.30	31.14		
		T _a = 105°C		7.76	71.36		
	Increment for RTC	operation*4		0.99	—		SOMCR.SODRV[1:0] set to drive capacity for standard CL
		0.55 —			SOMCR.SODRV[1:0] set to high drive capacity for low CL		
				0.32	—		SOMCR.SODRV[1:0] set to middle drive capacity for low CL
					—		SOMCR.SODRV[1:0] set to low drive capacity for low CL
	Increment for low- operation	power timer		0.33	_		LPTCR1.LPCNTCKSEL set to IWDT- dedicated on-chip oscillator
			15.89	—		LPTCR1.LPCNTCKSEL 2 set to Low-speed on-chip oscillator	
	Increment for inde watchdog timer op			0.32	—		

Note 1. Supply current values are with all output pins unloaded and all input pull-up MOSs in the off state.

Note 2. The IWDT, LVD, and CMPB are stopped. Note 3. VCC = 3.3 V. Note 4. Includes the oscillation circuit.





Figure 2.11 Voltage Dependency in Software Standby Mode (Reference Data for Products with 128-Kbyte or Larger ROM)







Figure 2.12 Temperature Dependency in Software Standby Mode (Reference Data for Products with 128-Kbyte or Larger ROM)



Table 2.12 DC Characteristics (7)

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $1.8 \text{ V} \le \text{AVCC0} \le 5.5 \text{ V}$, VSS = AVSS0 = 0 V, $\text{T}_{a} = -40 \text{ to } +105^{\circ}\text{C}$

	Item	Symbol	Min.	Typ.*4	Max.	Unit	Test Conditions
Analog power	During A/D conversion (at high-speed conversion)	I _{AVCC}	—	0.6	1.3	mA	
supply current	During A/D conversion (at low-speed conversion)		_	0.3	0.7		
	During D/A conversion (per channel)*1		_	_	— 0.5		
	Waiting for A/D and D/A conversion				2.0	μA	
power supply current	During A/D conversion (at high-speed conversion)	I _{REFH0}	—	49.6	120	μA	
	Waiting for A/D conversion		_	_	0.3	nA	
LVD0	—	I _{LVD}		0.04	_	μA	
LVD1, 2	Per channel			0.12	_	μA	
Temperature sensor* ³	_	I _{TEMP}	_	120	—	μA	
Comparator B	Window function enabled	I _{CMP} *2		7.5	12.5	μA	
operating current* ³	Comparator high-speed mode (per channel)	1		5.0	10.0	μA	1
ourion	Comparator low-speed mode (per channel)	1	_	1.5	3.0	μA	1

Note 1. The value of the D/A converter is the value of the power supply current including the reference current.

Note 2. Current consumed only by the comparator B module.

Note 3. ICurrent consumed by the power supply (VCC).

Note 4. When VCC = AVCC0 = 3.3 V.

Table 2.13DC Characteristics (8)

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $1.8 \text{ V} \le \text{AVCC0} \le 5.5 \text{ V}$, VSS = AVSS0 = 0 V, $\text{T}_{a} = -40 \text{ to } +105^{\circ}\text{C}$

Item	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
RAM standby voltage	V _{RAM}	1.8		—	V	

Table 2.14DC Characteristics (9)

Conditions: $0 \text{ V} \le \text{VCC} \le 5.5 \text{ V}, 0 \text{ V} \le \text{AVCC0} \le 5.5 \text{ V}, \text{VSS} = \text{AVSS0} = 0 \text{ V}, \text{ T}_a = -40 \text{ to } +105^{\circ}\text{C}$

	Symbol	Min.	Тур.	Max.	Unit	Test Conditions	
Power-on VCC rising	At normal startup*1	SrVCC	0.02	—	20	ms/V	
gradient	During fast startup time*2		0.02	_	2		
	Voltage monitoring 0 reset enabled at startup* ^{3, *4}		0.02	—	—		

Note 1. When OFS1.(FASTSTUP, LVDAS) = 11b.

Note 2. When OFS1.(FASTSTUP, LVDAS) = 01b.

Note 3. When OFS1.LVDAS = 0.

Note 4. Turn on the power supply voltage according to the normal startup rising gradient because the register settings set by OFS1 are not read in boot mode.



Table 2.15DC Characteristics (10)

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $1.8 \text{ V} \le \text{AVCC0} \le 5.5 \text{ V}$, VSS = AVSS0 = 0 V, $\text{T}_{a} = -40 \text{ to } +105^{\circ}\text{C}$

The ripple voltage must meet the allowable ripple frequency $f_{r (VCC)}$ within the range between the VCC upper limit and lower limit. When VCC change exceeds VCC ±10%, the allowable voltage change rising/falling gradient dt/dVCC must be met.

Item	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Allowable ripple frequency	f _{r (VCC)}	_	_	10	kHz	Figure 2.13 $V_{r (VCC)} \le 0.2 \times VCC$
		_	_	1	MHz	Figure 2.13 V _{r (VCC)} ≤ 0.08 × VCC
		_	_	10	MHz	Figure 2.13 V _{r (VCC)} ≤ 0.06 × VCC
Allowable voltage change rising/falling gradient	dt/dVCC	1.0	_	—	ms/V	When VCC change exceeds VCC ±10%







Table 2.16Permissible Output Currents (1)

Conditions: 1.8 V ≤ VCC ≤ 5.5 V, 1.8 V ≤ AVCC0 ≤ 5.5 V, VSS = AVSS0 = 0 V, T_a = -40 to +85°C

	Item	Symbol	Max.	Unit
Permissible output low current (average value per pin)	P03 to P07, P40 to P47, PJ6, PJ7	I _{OL}	8.0	mA
	Ports other than above		8.0	
Permissible output low current (maximum value per pin)	P03 to P07, P40 to P47, PJ6, PJ7		8.0	
	Ports other than above		8.0	
Permissible output low current	Total of P03 to P07, P40 to P47, PJ6, PJ7	ΣI _{OL}	40	
	Total of P12 to P17, P20, P21, P26 to P27, P30 to P32, P34 to P37, PG7, PH2, PH3, PJ1		40	
	Total of P54, P55, PB0 to PB7, PC2 to PC7, PH0, PH1		40	
	Total of PA0 to PA6, PD0 to PD2, PE0 to PE5		40	
	Total of all output pins		80	
Permissible output high current (average value per pin)	P03 to P07, P40 to P47, PJ6, PJ7	I _{ОН}	-4.0	
	Ports other than above		-4.0	
Permissible output high current (maximum value per pin)	P03 to P07, P40 to P47, PJ6, PJ7		-4.0	
	Ports other than above		-4.0	
Permissible output high current	Total of P03 to P07, P40 to P47, PJ6, PJ7	ΣI _{OH}	-40	
	Total of P12 to P17, P20, P21, P26 to P27, P30 to P32, P34 to P37, PG7, PH2, PH3, PJ1		-40	
	Total of P54, P55, PB0 to PB7, PC2 to PC7, PH0, PH1		-40	
	Total of PA0 to PA6, PD0 to PD2, PE0 to PE5		-40	
	Total of all output pins		-80	1

Note: Do not exceed the permissible total supply current.



Table 2.17 Permissible Output Currents (2)

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $1.8 \text{ V} \le \text{AVCC0} \le 5.5 \text{ V}$, VSS = AVSS0 = 0 V, $\text{T}_{a} = -40 \text{ to } +105^{\circ}\text{C}$

	Item	Symbol	Max.	Unit
Permissible output low current (average value per pin)	P03 to P07, P40 to P47, PJ6, PJ7	I _{OL}	8.0	mA
	Ports other than above		8.0	
Permissible output low current (maximum value per pin)	P03 to P07, P40 to P47, PJ6, PJ7		8.0	
	Ports other than above		8.0	
Permissible output low current	Total of P03 to P07, P40 to P47, PJ6, PJ7	ΣI _{OL}	30	
	Total of P12 to P17, P20, P21, P26 to P27, P30 to P32, P34 to P37, PG7, PH2, PH3, PJ1		30	
	Total of P54, P55, PB0 to PB7, PC2 to PC7, PH0, PH1		30	
	Total of PA0 to PA6, PD0 to PD2, PE0 to PE5		30	
	Total of all output pins		60	
Permissible output high current (average value per pin)	P03 to P07, P40 to P47, PJ6, PJ7	I _{ОН}	-4.0	
	Ports other than above		-4.0	
Permissible output high current (maximum value per pin)	P03 to P07, P40 to P47, PJ6, PJ7		-4.0	
	Ports other than above		-4.0	
Permissible output high current	Total of P03 to P07, P40 to P47, PJ6, PJ7	ΣΙ _{ΟΗ}	-30	
	Total of P12 to P17, P20, P21, P26 to P27, P30 to P32, P34 to P37, PG7, PH2, PH3, PJ1		-30	
	Total of P54, P55, PB0 to PB7, PC2 to PC7, PH0, PH1		-30	
	Total of PA0 to PA6, PD0 to PD2, PE0 to PE5		-30	
	Total of all output pins		-60	1

Note: Do not exceed the permissible total supply current.



Table 2.18 Output Values of Voltage (1)

Conditions: 1.8 V \leq VCC < 2.7 V, 1.8 V \leq AVCC0 < 2.7 V, VSS = AVSS0 = 0 V, T_a = -40 to $+105^{\circ}$ C

Item				Min.	Max.	Unit	Test Conditions
Output low	All output ports (except for RIIC)			—	0.3	V	I _{OL} = 1.0 mA
Output high	All output ports P03 to P07, P40 to P47, PJ6, PJ7 Ports other than above		V _{OH}	AVCC0 - 0.3	_	V	I _{OH} = -0.5 mA
				VCC - 0.3	_	V	

Table 2.19Output Values of Voltage (2)

Conditions: 2.7 V ≤ VCC < 4.0 V, 2.7 V ≤ AVCC0 < 4.0 V, VSS = AVSS0 = 0 V, $T_a = -40$ to +105°C

		Symbol	Min.	Max.	Unit	Test Conditions	
Output low	low All output ports (except for RIIC)			—	0.5 V		I _{OL} = 2.0 mA
RIIC pins				—	0.6		I _{OL} = 6.0 mA
Output high	high All output ports P03 to P07, P40 to P47, PJ6, PJ7		V _{OH}	AVCC0 - 0.5	_	V	I _{OH} = -1.0 mA
Ports other than above				VCC - 0.5			

Table 2.20Output Values of Voltage (3)

Conditions: $4.0 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $4.0 \text{ V} \le \text{AVCC0} \le 5.5 \text{ V}$, VSS = AVSS0 = 0 V, $\text{T}_a = -40 \text{ to } +105^{\circ}\text{C}$

		Symbol	Min.	Max.	Unit	Test Conditions	
Output low	All output ports (except for RIIC)			—	0.8	V	I _{OL} = 4.0 mA
	RIIC pins			—	0.6		I _{OL} = 6.0 mA
Output high	All output ports	P03 to P07, P40 to P47, PJ6, PJ7		AVCC0 - 0.8	— v	I _{OH} = -2.0 mA	
	Ports other than above			VCC - 0.8			

Table 2.21 Thermal Resistance Value (Reference Values)

Item	Package	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Thermal	80-pin LFQFP (PLQP0080KB-B)	θja	_		52.60	°C/W	JESD51-2 and
resistance	64-pin LFQFP (PLQP0064KB-C)				54.70		JESD51-7 compliant
	64-pin LQFP (PLQP0064GA-A)		—		54.30		
	48-pin LFQFP (PLQP0048KB-B)		—		63.50		
	48-pin HWQFN (PWQN0048KC-A)		—	—	21.20* ¹		
	32-pin LQFP (PLQP0032GB-A)				62.20		
	32-pin HWQFN (PWQN0032KE-A)		—	—	23.60*1		
	80-pin LFQFP (PLQP0080KB-B)	Ψjt	—	—	1.54		
	64-pin LFQFP (PLQP0064KB-C)		—	—	2.29		
	64-pin LQFP (PLQP0064GA-A)		_	_	2.29		
	48-pin LFQFP (PLQP0048KB-B)		_	_	2.78		
	48-pin HWQFN (PWQN0048KC-A)				0.21* ¹		
	32-pin LQFP (PLQP0032GB-A)		_	_	2.78		
	32-pin HWQFN (PWQN0032KE-A)			—	0.23*1		

Note: The values are reference values when the 4-layer board is used. Thermal resistance depends on the number of layers or size of the board. For details, refer to the JEDEC standards.

Note 1. This value applies when the exposed die pad for this purpose is connected to VSS.



2.4 Normal I/O Pin Output Characteristics

Table 2.22 Normal I/O Pin VOH Voltage Characteristics (Reference Values)

Conditions: VCC = AVCC0 = 2.0 V, VSS = AVSS0 = 0 V, $T_a = 25^{\circ}C$

	Item	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Output high	All output pins	V _{OH}	_	VCC - 0.05	_	V	I _{OH} = -0.5 mA
level voltage			_	VCC - 0.09	_		I _{OH} = -1.0 mA
			_	VCC - 0.20	_		I _{OH} = -2.0 mA
			_	VCC - 0.49	_		I _{OH} = -4.0 mA

Table 2.23 Normal I/O Pin VOH Voltage Characteristics (Reference Values)

Conditions: VCC = AVCC0 = 3.3 V, VSS = AVSS0 = 0 V, $T_a = 25^{\circ}C$

	Item	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
	All output pins	V _{OH}	_	VCC - 0.02	_	V	I _{OH} = –0.5 mA
level voltage			_	VCC - 0.05	_		I _{OH} = -1.0 mA
			_	VCC - 0.10	_		I _{OH} = -2.0 mA
			_	VCC - 0.22	_		I _{OH} = -4.0 mA

Table 2.24 Normal I/O Pin VOH Voltage Characteristics (Reference Values)

Conditions: VCC = AVCC0 = 5.0 V, VSS = AVSS0 = 0 V, $T_a = 25^{\circ}C$

	Item	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Output high	All output pins	V _{OH}	_	VCC - 0.02	_	V	I _{OH} = -0.5 mA
level voltage			_	VCC - 0.04	_		I _{OH} = -1.0 mA
			_	VCC - 0.08	_		I _{OH} = -2.0 mA
				VCC - 0.15			I _{OH} = -4.0 mA

Table 2.25 Normal I/O Pin VOH Voltage Characteristics (Reference Values)

Conditions: VCC = AVCC0 = 2.0 V, VSS = AVSS0 = 0 V, T_a = 25°C

	Item	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Output low	All output pins	V _{OL}		0.02	_	V	I _{OL} = 0.5 mA
voltage			_	0.04	_		I _{OL} = 1.0 mA
			_	0.08			I _{OL} = 2.0 mA
			_	0.17			I _{OL} = 4.0 mA
			_	0.43			I _{OL} = 8.0 mA

Table 2.26 Normal I/O Pin VOH Voltage Characteristics (Reference Values)

Conditions: VCC = AVCC0 = 3.3 V, VSS = AVSS0 = 0 V, T_a = 25°C

	Item	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Output low	All output pins	V _{OL}	_	0.01	_	V	I _{OL} = 0.5 mA
voltage			_	0.02			I _{OL} = 1.0 mA
			_	0.04			I _{OL} = 2.0 mA
			_	0.08			I _{OL} = 4.0 mA
			_	0.17			I _{OL} = 8.0 mA



Table 2.27Normal I/O Pin VOH Voltage Characteristics (Reference Values)Conditions:VCC = AVCC0 = 5.0 V, VSS = AVSS0 = 0 V, T_a = 25°C

	Item	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Output low				0.01	-	V	I _{OL} = 0.5 mA
voltage			_	0.01	—		I _{OL} = 1.0 mA
			_	0.03	_		I _{OL} = 2.0 mA
			_	0.06	_		I _{OL} = 4.0 mA
			_	0.12	—		I _{OL} = 8.0 mA



2.5 AC Characteristics

2.5.1 Clock Timing

Table 2.28 Operating Frequency Value (High-Speed Operating Mode)

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $1.8 \text{ V} \le \text{AVCC0} \le 5.5 \text{ V}$, VSS = AVSS0 = 0 V, $\text{T}_a = -40 \text{ to } +105^{\circ}\text{C}$

	Item	Symbol	Min.	Тур.	Max.	Unit
Maximum	System clock (ICLK)	f	—	—	48	MHz
operating frequency* ⁴	FlashIF clock (FCLK)*1, *2		_	_	48	
	Peripheral module clock (PCLKB)		_	_	32	
	Peripheral module clock (PCLKD)*3		_	_	48	

Note 1. The lower-limit frequency of FCLK is 1 MHz during programming or erasing of the flash memory. When using FCLK at below 4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.

Note 2. The frequency accuracy of FCLK should be ±3.5%.

Note 3. The lower-limit frequency of PCLKD is 1 MHz when the A/D converter is in use.

Note 4. The maximum operating frequency does not include HOCO error or PLL jitter. See Table 2.35, HOCO Clock Timing (ROM capacity: product with 128 Kbytes or more) or Table 2.36, HOCO Clock Timing (ROM capacity: product with 64 Kbytes).

Table 2.29 Operating Frequency Value (Middle-Speed Operating Mode)

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $1.8 \text{ V} \le \text{AVCCO} \le 5.5 \text{ V}$, VSS = AVSSO = 0 V, $\text{T}_a = -40 \text{ to } +105^{\circ}\text{C}$

	Item	Symbol	Min.	Тур.	Max.	Unit
Maximum	System clock (ICLK)	f	—	—	24	MHz
operating frequency* ⁴	FlashIF clock (FCLK)* ^{1, *2}		_	_	24	
	Peripheral module clock (PCLKB)		_	_	24	
_	Peripheral module clock (PCLKD)* ³		_	_	24	

Note 1. The lower-limit frequency of FCLK is 1 MHz during programming or erasing of the flash memory. When using FCLK at below 4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.

Note 2. The frequency accuracy of FCLK should be ±3.5%.

Note 3. The lower-limit frequency of PCLKD is 1 MHz when the A/D converter is in use.

Note 4. The maximum operating frequency does not include HOCO error or PLL jitter. See Table 2.35, HOCO Clock Timing (ROM capacity: product with 128 Kbytes or more) or Table 2.36, HOCO Clock Timing (ROM capacity: product with 64 Kbytes).

Table 2.30 Operating Frequency Value (Middle-Speed Operating Mode 2)

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $1.8 \text{ V} \le \text{AVCC0} \le 5.5 \text{ V}$, VSS = AVSS0 = 0 V, $\text{T}_a = -40 \text{ to } +105^{\circ}\text{C}$

	Item	Symbol	Min.	Тур.	Max.	Unit
Maximum System clock (ICLK)		f	—	—	1	MHz
operating frequency* ⁴	FlashIF clock (FCLK)* ^{1, *2}		_	_	1	
	Peripheral module clock (PCLKB)		_	_	1	
	Peripheral module clock (PCLKD)*3	1	—	—	1	

Note 1. The lower-limit frequency of FCLK is 1 MHz during programming or erasing of the flash memory.

Note 2. The frequency accuracy of FCLK should be ±3.5%.

Note 3. The lower-limit frequency of PCLKD is 4 MHz when the A/D converter is in use.

Table 2.31 Operating Frequency Value (Low-Speed Operating Mode)

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $1.8 \text{ V} \le \text{AVCCO} \le 5.5 \text{ V}$, VSS = AVSSO = 0 V, $\text{T}_a = -40 \text{ to } +105^{\circ}\text{C}$

	Item	Symbol	Min.	Тур.	Max.	Unit
Maximum	System clock (ICLK)	f	_	_	32.768	kHz
operating frequency	FlashIF clock (FCLK)*1		_	_	32.768	
	Peripheral module clock (PCLKB)		_	_	32.768	
	Peripheral module clock (PCLKD)*2		_	_	32.768	

Note 1. Programming and erasing the flash memory is impossible.

Note 2. The A/D converter cannot be used.



Table 2.32 EXTAL Clock Timing

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}, 1.8 \text{ V} \le \text{AVCC0} \le 5.5 \text{ V}, \text{VSS} = \text{AVSS0} = 0 \text{ V}, \text{ T}_{a} = -40 \text{ to } +105^{\circ}\text{C}$

Item	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
EXTAL external clock input cycle time	t _{Xcyc}	50	—	—	ns	Figure 2.14
EXTAL external clock input high pulse width	t _{XH}	20	—	—	ns	
EXTAL external clock input low pulse width	t _{XL}	20	—	—	ns	
EXTAL external clock rise time	t _{Xr}	—	—	5	ns	
EXTAL external clock fall time	t _{Xf}	—	—	5	ns	
EXTAL external clock input wait time*1	t _{XWT}	0.5	—	—	μs]

Note 1. Time until the clock can be used after the main clock oscillator stop bit (MOSCCR.MOSTP) is set to 0 (operating).



Figure 2.14 EXTAL External Clock Input Timing

Table 2.33Main Clock Timing

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $1.8 \text{ V} \le \text{AVCC0} \le 5.5 \text{ V}$, VSS = AVSS0 = 0 V, $\text{T}_{a} = -40 \text{ to } +105^{\circ}\text{C}$

Item	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Main clock oscillator oscillation frequency	f _{MAIN}	1	—	20	MHz	
Main clock oscillation stabilization time (crystal)*1	t _{MAINOSC}	—	3	_	ms	Figure 2.15
Main clock oscillation stabilization time (ceramic resonator)*1	t _{MAINOSC}	_	50	_	μs	

Note 1. Reference values when an 8-MHz resonator is used.

When specifying the main clock oscillator stabilization time, set the MOSCWTCR register with a stabilization time value that is equal to or greater than the resonator-manufacturer-recommended value.

After changing the setting of the MOSCCR.MOSTP bit so that the main clock oscillator operates, read the OSCOVFSR.MOOVF flag to confirm that is has become 1, and then start using the main clock.







Table 2.34 LOCO and IWDT-Dedicated Low-Speed Clock Timing

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $1.8 \text{ V} \le \text{AVCC0} \le 5.5 \text{ V}$, VSS = AVSS0 = 0 V, $\text{T}_{a} = -40 \text{ to } +105^{\circ}\text{C}$

Item	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
LOCO clock oscillation frequency	f _{LOCO}	3.44	4.0	4.56	MHz	
LOCO clock oscillation frequency error	Δf_{LOCO}	—	—	±14	%	
LOCO clock oscillation stabilization time	t _{LOCO}	—	—	0.5	μs	Figure 2.16
IWDT-dedicated clock oscillation frequency	f _{ILOCO}	12.75	15	17.25	kHz	
IWDT-dedicated clock oscillation frequency error	Δf _{ILOCO}	—	—	±15	%	
IWDT-dedicated clock oscillation stabilization time	t _{ILOCO}	—	—	80	μs	Figure 2.17



Figure 2.16 LOCO Clock Oscillation Start Timing



Figure 2.17 IWDT-Dedicated Clock Oscillation Start Timing



Table 2.35 HOCO Clock Timing (ROM capacity: product with 128 Kbytes or more)

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}, 1.8 \text{ V} \le \text{AVCC0} \le 5.5 \text{ V}, \text{VSS} = \text{AVSS0} = 0 \text{ V}, \text{ T}_{a} = -40 \text{ to } +105^{\circ}\text{C}$

Item	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
HOCO clock oscillation frequency*1	f _{HOCO}	23.76	24	24.24	MHz	T _a = -40 to +105°C
		31.68	32	32.32		
		47.52	48	48.48		
HOCO oscillation frequency error*1	Δf _{HOCO}	_	_	±1.0	%	$T_a = -40 \text{ to } +105^{\circ}\text{C}$
HOCO clock oscillation stabilization time	t _{HOCO}	_		4.95	μs	Figure 2.19

Note 1. Accuracy at production test.

Table 2.36 HOCO Clock Timing (ROM capacity: product with 64 Kbytes)

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $1.8 \text{ V} \le \text{AVCC0} \le 5.5 \text{ V}$, VSS = AVSS0 = 0 V, $\text{T}_{a} = -40 \text{ to } +105^{\circ}\text{C}$

Item	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
HOCO clock oscillation frequency*1	f _{HOCO}	23.64	24	24.36	MHz	$T_a = -40 \text{ to } -20^{\circ}\text{C}$
		23.76		24.24		T _a = -20 to +85°C
		23.52		24.48		T _a = +85 to +105°C
		31.52	32	32.48	MHz	$T_a = -40 \text{ to } -20^{\circ}\text{C}$
		31.68		32.32		$T_a = -20 \text{ to } +85^{\circ}\text{C}$
		31.36		32.64		T _a = +85 to +105°C
		47.28	48	48.72	MHz	$T_a = -40 \text{ to } -20^{\circ}\text{C}$
		47.52		48.48		T _a = –20 to +85°C
		47.04		48.96		T _a = +85 to +105°C
HOCO oscillation frequency error*1	Δf_{HOCO}	—	—	±1.5	%	$T_a = -40 \text{ to } -20^{\circ}\text{C}$
			_	±1.0		T _a = –20 to +85°C
		—	—	±2.0	1	T _a = +85 to +105°C
HOCO clock oscillation stabilization time	t _{HOCO}	—	—	4.95	μs	Figure 2.19

Note 1. Accuracy at production test.







Table 2.37 PLL Clock Timing

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $1.8 \text{ V} \le \text{AVCC0} \le 5.5 \text{ V}$, VSS = AVSS0 = 0 V, $\text{T}_{a} = -40 \text{ to } +105^{\circ}\text{C}$

Item	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
PLL input frequency	f _{PLLIN}	4	_	12	MHz	
PLL circuit oscillation frequency	f _{PLL}	24		48	MHz	
PLL clock oscillation stabilization time	t _{PLL}			81.4	μs	Figure 2.20
PLL free-running oscillation frequency	f _{PLLFR}	_	9	_	MHz	



Figure 2.20 PLL Clock Oscillation Start Timing (PLL is Operated after Main Clock Oscillation Has Settled)



Table 2.38 Sub-Clock Timing

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $1.8 \text{ V} \le \text{AVCC0} \le 5.5 \text{ V}$, VSS = AVSS0 = 0 V, $\text{T}_{a} = -40 \text{ to } +105^{\circ}\text{C}$

Item	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Sub-clock oscillator oscillation frequency*2	f _{SUB}	—	32.768	—	kHz	
Sub-clock oscillation stabilization time*1	t _{SUBOSC}	—	0.5	—	s	Figure 2.21

Note 1. Reference value when a 32.768-kHz resonator is used.

After changing the setting of the SOSCCR.SOSTP bit so that the sub-clock oscillator operates, only start using the sub-clock after the sub-clock oscillation stabilization wait time that is equal to or greater than the oscillator-manufacturer-recommended value has elapsed.

Note 2. Only 32.768-kHz can be used.







Reset Timing 2.5.2

Table 2.39 **Reset Timing**

Conditions: 1.8 V ≤ VCC ≤ 5.5 V, 1.8 V ≤ AVCC0 ≤ 5.5 V, VSS = AVSS0 = 0 V, $T_a = -40$ to +105°C

	Item	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
RES# pulse width	At power-on	t _{RESWP}	10.5	_	—	ms	Figure 2.22
	Other than above	t _{RESW}	30			μs	Figure 2.23
Wait time after RES# cancellation (at power-on)	At normal startup*1	t _{RESWT}	_	8.5		ms	Figure 2.22
	During fast startup time*2	t _{RESWT}		850	_	μs	
Wait time after RES# cancellation (during powered-on state)	LVD0 disabled*3	t _{RESWT}		120	—	μs	Figure 2.23
	LVD0 enabled*4		_	850	_	μs	
Internal reset time	LVD0 disabled*3	t _{RESWT2}	_	190	—	μs	
(independent watchdog timer reset, software reset)	LVD0 enabled*4			890	_	μs	

Note 1. When OFS1.(LVDAS, FASTSTUP) = 11b. Note 2. When OFS1.(LVDAS, FASTSTUP) = a value other than 11b.

Note 3. When OFS1.LVDAS = 1b.

Note 4. When OFS1.LVDAS = 0b.



Figure 2.22 **Reset Input Timing at Power-On**







2.5.3 Timing of Recovery from Low Power Consumption Modes

		Item		Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Oscillation stabilization wait time*1	High-speed operating mode/ Middle- speed operating mode	Main clock oscillator operating	Main clock oscillator operating	t _{SBYOSCWTMC}	_		$t_{LOCO} + (16 + Number of cycles specified in MOSCWTCR)/ f_{LOCO} + 2 / f_{MOSC} + 1 / f_{ICLK}$	μs	
			Main clock oscillator and PLL circuit operating	t _{SBYOSCWTPC}	-		t _{LOCO} + (288 + Number of cycles specified in MOSCWTCR)/ f _{LOCO} + 2 / f _{PLL} + 1 / f _{ICLK}		
		Sub-clock oscillator operating		t _{SBYOSCWTSC}	—	—	3 / f _{SOSC} + 1 / f _{ICLK}		
	• •	High-speed operating	on-chip oscillator	t _{SBYOSCWTHO}	_	_	t _{LOCO} + 16 / f _{LOCO} + 2 / f _{HOCO} + 1 / f _{ICLK}	+2/ +1/	
		Low-speed operating	on-chip oscillator	t _{SBYOSCWTLO}	—	_	t _{LOCO} + 1 / f _{ICLK}		
	ed for operatio re standby mo		uencer before release	t _{SBYSEQ}	_	—	4 / f _{LOCO} + 11 / f _{ICLK} + 3 / f _{PCLKB} + 3n / f _{source clock}		
Recovery time from	High-speed operating	Main clock oscillator	Main clock oscillator operating	t _{SBYMC}	-	_	t _{SBYOSCWTMC} + t _{SBYSEQ}		Figure 2.24
software standby mode* ³	mode/ Middle- speed operating	operating	Main clock oscillator and PLL circuit operating	t _{SBYPC}	—	—	t _{SBYOSCWTPC} + t _{SBYSEQ}		
	mode	Sub-clock of	scillator operating	t _{SBYSC}		—	t _{SBYOSCWTSC} + t _{SBYSEQ}		
		High-speed operating	on-chip oscillator	t _{SBYHO}	—	—	t _{SBYOSCWTHO} + t _{SBYSEQ}		
		Low-speed operating	on-chip oscillator	t _{SBYLO}	_	_	t _{SBYOSCWTLO} +		

Table 2.40 Timing of Recovery from Low Power Consumption Modes (1)

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $1.8 \text{ V} \le \text{AVCC0} \le 5.5 \text{ V}$, VSS = AVSS0 = 0 V, $\text{T}_{a} = -40 \text{ to } +105^{\circ}\text{C}$

Note 1. When multiple oscillators are operating before entry to software standby mode, the oscillation stabilization wait time will be selected as the largest value among those for the operating oscillators.

Note 2. For n, the largest value is selected from among the internal clock division settings.

Note 3. The time for recovery from software standby mode is determined by the value obtained by adding the oscillation stabilization wait time and the time required for operations by the sequencer before release from software standby mode.



Table 2.41 Timing of Recovery from Low Power Consumption Modes (2)

Conditions:	$1.8 V \leq VCC \leq 5.5 V.$	1.8 V ≤ AVCC0 ≤ 5.5 V. VSS	$= AVSS0 = 0 V, T_a = -40 to +105^{\circ}C$
-------------	------------------------------	----------------------------	---

		Item	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Oscillation Middle- stabilization speed wait time*1 operating mode 2		Main clock oscillator and PLL circuit operating	^t sbyoscwtpc	_		t _{LOCO} + (288 + Number of cycles specified in MOSCWTCR)/ f _{LOCO} + 2 / f _{PLL} + 1 / f _{ICLK}	μs	
		Sub-clock oscillator operating	t _{SBYOSCWTSC}	—	—	3 / f _{SOSC} + 1 / f _{ICLK}		
		High-speed on-chip oscillator operating	t _{SBYOSCWTHO}			t _{LOCO} + 16 / f _{LOCO} + 2 / f _{HOCO} + 1 / f _{ICLK}		
		Low-speed on-chip oscillator operating	t _{SBYOSCWTLO}	_	_	t _{LOCO} + 1 / f _{ICLK}		
	ed for operation re standby mo	ons by the sequencer before release ode*2	t _{SBYSEQ}		—	9 / f _{ICLK} + 3 / f _{PCLKB} + 3n / f _{source clock}		
Recovery time from	Middle- speed	Main clock oscillator and PLL circuit operating	t _{SBYPC}	—	_	t _{SBYOSCWTPC} +		Figure 2.24
software standby mode* ³	operating mode 2	Sub-clock oscillator operating	t _{SBYSC}	_		tsbyoscwtsc +		
		High-speed on-chip oscillator operating	^t sbyho	_	_	t _{SBYOSCWTHO} +		
		Low-speed on-chip oscillator operating	t _{SBYLO}	_		t _{SBYOSCWTLO} + t _{SBYSEQ}		

Note 1. When multiple oscillators are operating before entry to software standby mode, the oscillation stabilization wait time will be selected as the largest value among those for the operating oscillators.

Note 2. For n, the largest value is selected from among the internal clock division settings.

Note 3. The time for recovery from software standby mode is determined by the value obtained by adding the oscillation stabilization wait time and the time required for operations by the sequencer before release from software standby mode.



Table 2.42 Timing of Recovery from Low Power Consumption Modes (3)

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $1.8 \text{ V} \le \text{AVCC0} \le 5.5 \text{ V}$, VSS = AVSS0 = 0 V, $\text{T}_{a} = -40 \text{ to } +105^{\circ}\text{C}$

				~				
Item			Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Oscillation stabilization wait time	Low-speed operating mode	Sub-clock oscillator operating	t _{SBYOSCWTSC}	—	—	3 / f _{SOSC} + 1 / f _{ICLK}	μs	
Time required for operations by the sequencer before release from software standby mode*1			t _{SBYSEQ}	—	—	9 / f _{ICLK} + 3 / f _{PCLKB} + 3n / f _{source clock}		
Recovery time from software standby mode* ²	Low-speed operating mode	Sub-clock oscillator operating	t _{SBYSC}	—	—	t _{SBYOSCWTSC} + t _{SBYSEQ}		Figure 2.24

Note 1. For n, the largest value is selected from among the internal clock division settings.

Note 2. The time for recovery from software standby mode is determined by the value obtained by adding the oscillation stabilization wait time and the time required for operations by the sequencer before release from software standby mode.



Figure 2.24 Software Standby Mode Recovery Timing



Table 2.43Timing of Recovery from Low Power Consumption Modes (4)

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $1.8 \text{ V} \le \text{AVCC0} \le 5.5 \text{ V}$, VSS = AVSS0 = 0 V, $\text{T}_{a} = -40 \text{ to } +105^{\circ}\text{C}$

	Item		Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Oscillation stabilization wait time*¹	Main clock oscillator operating	Main clock oscillator operating	t _{SBYOSCWTMC}			$t_{LOCO} + (16 + Number of cycles specified in MOSCWTCR)/ f_{LOCO} + 2 / f_{MOSC} + 1 / f_{ICLK}$	μs	
		Main clock oscillator and PLL circuit operating	^t sbyoscwtpc	_		t _{LOCO} + (288 + Number of cycles specified in MOSCWTCR)/ f _{LOCO} + 2 / f _{PLL} + 1 / f _{ICLK}		
	Sub-clock oscillator operating		t _{SBYOSCWTSC}	_	_	3 / f _{SOSC} + 1 / f _{ICLK}		
	High-speed operating	on-chip oscillator	^t sbyoscwtho	_	_	t _{LOCO} + 16 / f _{LOCO} + 2 / f _{HOCO} + 1 / f _{ICLK}		
	Low-speed of operating	on-chip oscillator	t _{SBYOSCWTLO}	—	—	t _{LOCO} + 1 / f _{ICLK}		
Time required for operatio from software standby mo		uencer before release	t _{SBYSEQ}	_	_	3 / f _{ICLK} + 2n / f _{source clock}		
Time to shift to the snooze mode from the	Main clock oscillator	Main clock oscillator operating	t _{SNZMC}		_	t _{SBYOSCWTMC} +		Figure 2.25
software standby mode*3	operating	Main clock oscillator and PLL circuit operating	t _{SNZPC}	_	—	t _{SBYOSCWTPC} + t _{SBYSEQ}		
	Sub-clock os	scillator operating	t _{SNZSC}	—	—	t _{SBYOSCWTSC} +		
	High-speed operating	on-chip oscillator	t _{SNZHO}	_	_	t _{SBYOSCWTHO} +		
	Low-speed of operating	on-chip oscillator	t _{SNZLO}	_	_	^t SBYOSCWTLO + ^t SBYSEQ		

Note 1. When multiple oscillators are operating before entry to software standby mode, the oscillation stabilization wait time will be selected as the largest value among those for the operating oscillators.

Note 2. For n, the largest value is selected from among the internal clock division settings.

Note 3. The time to shift to the snooze mode from the software standby mode is determined by the value obtained by adding the oscillation stabilization wait time and the time required for operations by the sequencer before release from software standby mode.





Figure 2.25 Timing to shift to the Snooze Mode from the Software Standby Mode

Table 2.44 Timing of Recovery from Low Power Consumption Modes (5)

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $1.8 \text{ V} \le \text{AVCC0} \le 5.5 \text{ V}$, VSS = AVSS0 = 0 V, $\text{T}_{a} = -40 \text{ to } +105^{\circ}\text{C}$

	Item	Symbol	Min.	Тур.	Max.*2	Unit	Test Conditions
Recovery time from deep sleep mode*1	om deep High-speed operating mode t _{DSLP} –		_	—	4 / f _{LOCO} + 8 / f _{ICLK} + 2 / f _{PCLKB} + 3n / f _{source} clock	μs	Figure 2.26
	Middle-speed operating mode				4 / f _{LOCO} + 8 / f _{ICLK} + 2 / fPCLKB + 3n / f _{source} clock		
	Middle-speed operating mode 2				6 / f _{ICLK} + 2 / f _{PCLKB} + 3n / f _{source} clock		
	Low-speed operating mode				6 / f _{ICLK} + 2 / f _{PCLKB} + 3n / f _{source clock}		

Note 1. Oscillators continue oscillating in deep sleep mode.

Note 2. For n, the largest value is selected from among the internal clock division settings.







Table 2.45Operating Mode Transition TimeConditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $1.8 \text{ V} \le \text{AVCC0} \le 5.5 \text{ V}$, VSS = AVSS0 = 0 V, $\text{T}_a = -40 \text{ to } +105^{\circ}\text{C}$

Mode before Transition	Mode after Transition	ICLK Frequency		Unit		
Mode before transmon			Min.	Тур.	Max.	Unit
High-speed operating mode	Middle-speed operating mode	24 MHz		5 / f _{ICLK} + 3 / f _{FCLK}	_	μs
	Middle-speed operating mode 2	1 MHz	—	5 / f _{ICLK} + 3 / f _{FCLK}	_	
	Low-speed operating mode	32.768 kHz	—	3 / f _{ICLK} + 2 / f _{FCLK}	—	
Middle-speed operating mode	High-speed operating mode	24 MHz	—	5 / f _{ICLK} + 3 / f _{FCLK}		
	Middle-speed operating mode 2	1 MHz	_	5 / f _{ICLK} + 3 / f _{FCLK}		
	Low-speed operating mode	32.768 kHz	—	3 / f _{ICLK} + 2 / f _{FCLK}		
Middle-speed operating mode 2	High-speed operating mode	1 MHz	—	5 / f _{ICLK} + 3 / f _{FCLK}	_	
	Middle-speed operating mode	1 MHz	—	5 / f _{ICLK} + 3 / f _{FCLK}		
	Low-speed operating mode	32.768 kHz	—	3 / f _{ICLK} + 2 / f _{FCLK}	_	
Low-speed operating mode	Middle-speed operating mode, high-speed operating mode	32.768 kHz	—	5 / f _{ICLK} + 3 / f _{FCLK}	_	
	Middle-speed operating mode	32.768 kHz	_	3 / f _{ICLK} + 3 / f _{FCLK}		
	Middle-speed operating mode 2	32.768 kHz	_	3 / f _{ICLK} + 3 / f _{FCLK}		



Control Signal Timing 2.5.4

Table 2.46 **Control Signal Timing**

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $1.8 \text{ V} \le \text{AVCC0} \le 5.5 \text{ V}$, VSS = AVSS0 = 0 V, $\text{T}_{a} = -40 \text{ to } +105^{\circ}\text{C}$

Item	Symbol	Min.	Тур.	Max.	Unit	Test Conditions				
NMI pulse width	t _{NMIW}	200	—	—	ns	NMI digital filter disabled	t _{Pcyc} × 2 ≤ 200 ns			
		t _{Pcyc} × 2*1	—	_		(NMIFLTE.NFLTEN = 0)	t _{Pcyc} × 2 > 200 ns			
		200	—	—		NMI digital filter enabled	t _{NMICK} × 3 ≤ 200 ns			
		t _{NMICK} × 3.5* ²	—	_		(NMIFLTE.NFLTEN = 1)	t _{NMICK} × 3 > 200 ns			
IRQ pulse width	t _{IRQW}	200	—	_	ns	IRQ digital filter disabled	t _{Pcyc} × 2 ≤ 200 ns			
		t _{Pcyc} × 2*1	—	_		(IRQFLTE0.FLTENi = 0)	t _{Pcyc} × 2 > 200 ns			
		200	—	_		IRQ digital filter enabled	t _{IRQCK} × 3 ≤ 200 ns			
		t _{IRQCK} × 3.5* ³	—	_		(IRQFLTE0.FLTENi = 1)	t _{IRQCK} × 3 > 200 ns			

200 ns minimum in software standby mode. Note:

Note 1. t_{Pcyc} indicates the cycle of PCLKB. Note 2. t_{NMICK} indicates the cycle of the NMI digital filter sampling clock. Note 3. t_{IRQCK} indicates the cycle of the IRQi digital filter sampling clock (i = 0 to 7).



Figure 2.27 **NMI Interrupt Input Timing**







2.5.5 Timing of On-Chip Peripheral Modules

2.5.5.1 I/O Port Input Timing

Table 2.47I/O Port Input Timing

Conditions: 1.8 V ≤ VCC ≤ 5.5 V, 1.8 V ≤ AVCC0 ≤ 5.5 V, VSS = AVSS0 = 0 V, $T_a = -40$ to +105°C Output load conditions: $V_{OH} = 0.7 \times VCC$, $V_{OL} = 0.3 \times VCC$, C = 30 pF

Item			Min.	Max.	Unit *1	Test Conditions
I/O ports	Input data pulse width	t _{PRW}	1.5		t _{Pcyc}	Figure 2.29

Note 1. t_{Pcyc}: PCLK cycle





2.5.5.2 MTU2

Table 2.48 MTU2 Timing

Conditions: 1.8 V ≤ VCC ≤ 5.5 V, 1.8 V ≤ AVCC0 ≤ 5.5 V, VSS = AVSS0 = 0 V, T_a = -40 to +105°C Output load conditions: V_{OH} = 0.7 × VCC, V_{OL} = 0.3 × VCC, C = 30 pF

ltem			Symbol	Min.	Max.	Unit *1	Test Conditions
MTU2	Input capture input pulse width	Single-edge setting	t _{TICW}	1.5 2.5		t _{Pcyc}	Figure 2.30
		Both-edge setting					
	Input capture input rise/fall time	Input capture input rise/fall time			0.1	µs/V	
	Timer clock pulse width	Single-edge setting	t _{TCKWH} ,	1.5	—	t _{Pcyc}	Figure 2.31
		Both-edge setting	t _{TCKWL}	2.5	—		
		Phase counting mode			—		
	Timer clock rise/fall time	Timer clock rise/fall time			0.1	µs/V	1





Figure 2.30 MTU2 Input/Output Timing



Figure 2.31 MTU2 Clock Input Timing

2.5.5.3 POE2

Table 2.49 POE2 Timing

Conditions: 1.8 V ≤ VCC ≤ 5.5 V, 1.8 V ≤ AVCC0 ≤ 5.5 V, VSS = AVSS0 = 0 V, T_a = -40 to +105°C Output load conditions: V_{OH} = 0.7 × VCC, V_{OL} = 0.3 × VCC, C = 30 pF

	Item		Symbol	Min.	Max.	Unit *1	Test Conditions
POE2	POE# input pulse wid	POE# input pulse width POE# input rise/fall time			—	t _{Pcyc}	Figure 2.32
	POE# input rise/fall ti				0.1	µs/V	
	Output disable time	Transition of the POEn# signal level	^t poedi	_	5t _{Pcyc} + 0.24	μs	Figure 2.33 When detecting falling edges (ICSRm.PO EnM[3:0] = 0000 (m =1, 2; n = 0, 1, 2,3,8))
		Simultaneous conduction of output pins	t _{POEDO}	_	3t _{Pcyc} + 0.2	Figure 2.34	
		Register setting	t _{POEDS}	_	1t _{Pcyc} + 0.2		Figure 2.35 Time for access to the register is not included.
		Oscillation stop detection	t _{POEDOS}	—	21		Figure 2.36





Figure 2.32 POE# Input Timing









Figure 2.34 Output Disable Time for POE in Response to the Simultaneous Conduction of Output Pins



Figure 2.35 Output Disable Time for POE in Response to the Register Setting



Figure 2.36 Output Disable Time for POE in Response to the Oscillation Stop Detection

2.5.5.4 TMR

Table 2.50 TMR Timing

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $1.8 \text{ V} \le \text{AVCCO} \le 5.5 \text{ V}$, VSS = AVSSO = 0 V, $\text{T}_{a} = -40 \text{ to } +105^{\circ}\text{C}$ Output load conditions: $\text{V}_{OH} = 0.7 \times \text{VCC}$, $\text{V}_{OL} = 0.3 \times \text{VCC}$, C = 30 pF

Item			Symbol	Min.	Max.	Unit *1	Test Conditions
TMR	MR Timer clock pulse width Single-edge settin Both-edge setting		t _{TMCWH} ,	1.5	—	t _{Pcyc}	Figure 2.37
			t _{TMCWL}	2.5	—		
Timer clock rise/fall time			t _{TMCr} ,	_	0.1	µs/V	
			t _{TMCf}				

Note 1. t_{Pcyc}: PCLK cycle



Figure 2.37 TMR Clock Input Timing



2.5.5.5 SCI

Table 2.51 SCI Timing

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $1.8 \text{ V} \le \text{AVCC0} \le 5.5 \text{ V}$, VSS = AVSS0 = 0 V, $\text{T}_{a} = -40 \text{ to } +105^{\circ}\text{C}$ Output load conditions: $\text{V}_{OH} = 0.5 \times \text{VCC}$, $\text{V}_{OL} = 0.5 \times \text{VCC}$, C = 30 pF

			ltere		Cumphel	Min	Max	Unit	Test
	1		Item		Symbol	Min.	Max.	*1	Conditions
SCI	Input clock cyc	cle time		Asynchronous	t _{Scyc}	4	—	t _{Pcyc}	Figure 2.38
(channel 1, 5)				Clock synchronous		6	-		
	Input clock pu	lse width			t _{SCKW}	0.4	0.6	t _{Scyc}	
	Input clock rise	e time			t _{SCKr}	—	20	ns	_
	Input clock fall time					—	20	ns	
	Output clock cycle time	Asynchronou			t _{Scyc}	6	—	t _{Pcyc}	Figure 2.39
	cycle unie	Clock synchronous	2.4 V ≤ VCC ≤ 5.5 V			4	—		
		synchronous	1.8 V ≤ VCC < 2.4 V	24 MHz < PCLKB ≤ 32 MHz	-	8	—	-	
				PCLKB ≤ 24 MHz		4	—		_
	Output clock p	oulse width			t _{SCKW}	0.4	0.6	t _{Scyc}	_
	Output clock r				t _{SCKr}	—	20	ns	
	Output clock fa	all time	-		t _{SCKf}	_	20	ns	_
	Transmit data (master)	delay time	Clock synchronous		t _{TXD}	—	40	ns	
	Transmit data	delay time	Clock synchronous	2.7 V or above	_		55	ns	-
	(slave)			2.4 V or above			60	ns	
				1.8 V or above		_	100	ns	
	Receive data setup time (master)		Clock synchronous	2.7 V or above	t _{RXS}	45	-	ns	1
				2.4 V or above	55		-	ns	1
				1.8 V or above		90	—	ns	1
	Receive data setup time Clock synchronous (slave)			•		40	-	ns	
	Receive data l		t _{RXH}	40	- 1	ns			
SCI	Input clock cyc	cle time		Asynchronous	t _{Scyc}	4	—	t _{Pcyc}	Figure 2.38
(channel				Clock synchronous	-	6	—		
6,8,9,12)	Input clock put	lse width			t _{SCKW}	0.4	0.6	t _{Scyc}	
	Input clock rise time					—	20	ns	
	Input clock fall time					_	20	ns	
	Output clock Asynchronous				t _{Scyc}	8	-	t _{Pcyc}	Figure 2.39
	cycle time	Clock	2.4 V ≤ VCC ≤ 5.5 V		-	4	—		
		synchronous	1.8 V ≤ VCC < 2.4 V	24 MHz < PCLKB ≤ 32 MHz		8	—		
				PCLKB ≤ 24 MHz		4	—		
	Output clock p	ulse width			t _{SCKW}	0.4	0.6	t _{Scyc}	
	Output clock r	ise time			t _{SCKr}	_	20	ns	
	Output clock fa	all time			t _{SCKf}	_	20	ns	-
	Transmit data (master)	delay time	Clock synchronous		t _{TXD}	_	40	ns	
	Transmit data	Transmit data delay time Clo		2.7 V or above		_	65	ns	-
	(slave)	-		1.8 V or above		_	100	ns	-
	Receive data	setup time	Clock synchronous	2.7 V or above	t _{RXS}	65	-	ns	-
	(master)	·		1.8 V or above	100	90	-	ns	1
	Receive data s (slave)	setup time	Clock synchronous	1		40	-	ns	
	Receive data l	hold time	Clock synchronous		t _{RXH}	40	_	ns	-
						I	1		L

Note 1. t_{Pcyc} : PCLK cycle





Figure 2.38 SCK Clock Input Timing



Figure 2.39 SCI Input/Output Timing: Clock Synchronous Mode


Table 2.52 Simple I²C Timing

Conditions: 2.7 V ≤ VCC ≤ 5.5 V, 2.7 V ≤ AVCC0 ≤ 5.5 V, VSS = AVSS0 = 0 V, $T_a = -40$ to +105°C Output load conditions: V_{OH} = 0.7 × VCC, V_{OL} = 0.3 × VCC, C = 30 pF

	ltem	Symbol	Min.	Max.	Unit	Test Conditions
Simple I ² C	SDA rise time	t _{Sr}	—	1000	ns	Figure 2.40
(standard mode)	SDA fall time	t _{Sf}	—	300	ns	
	SDA spike pulse removal time	t _{SP}	0	4 × t _{Pcyc}	ns	
	Data setup time	t _{SDAS}	250	—	ns	
	Data hold time	t _{SDAH}	0	—	ns	
	SCL, SDA capacitive load	C _b *1	—	400	pF	
Simple I ² C	SDA rise time	t _{Sr}	—	300	ns	Figure 2.40
(fast mode)	SDA fall time	t _{Sf}	—	300	ns	
	SDA spike pulse removal time	t _{SP}	0	4 × t _{Pcyc}	ns	
	Data setup time	t _{SDAS}	100	—	ns	
	Data hold time	t _{SDAH}	0	—	ns	
	SCL, SDA capacitive load	C _b *1	—	400	pF	

Note: t_{Pcyc} : PCLK cycle Note 1. C_b is the total capacitance of the bus lines.



Output Timing and Simple I²C Bus Interface Input/Output Timing Figure 2.40



Table 2.53Simple SPI Timing

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $1.8 \text{ V} \le \text{AVCC0} \le 5.5 \text{ V}$, VSS = AVSS0 = 0 V, $\text{T}_{a} = -40 \text{ to } +105^{\circ}\text{C}$ Output load conditions: $\text{V}_{OH} = 0.7 \times \text{VCC}$, $\text{V}_{OL} = 0.3 \times \text{VCC}$, C = 30 pF

		Item		Symbol	Min.	Max.	Unit*1	Test Conditions
Simple SPI		2.4 V ≤ VCC ≤ 5.5 V		t _{SPcyc}	4	65536	t _{Pcyc}	Figure 2.41
	cycle output (master)	1.8 V ≤ VCC < 2.4 V	24 MHz < PCLKB ≤ 32 MHz		8	65536		
	(master)		PCLKB ≤ 24 MHz		4	65536		
	SCK clock cy	cle input (slave)			6	—	t _{Pcyc}	
	SCK clock high pulse width			t _{SPCKWH}	0.4	0.6	t _{SPcyc}	
	SCK clock low pulse width			t _{SPCKWL}	0.4	0.6	t _{SPcyc}	
	SCK clock ris	e/fall time		t _{SPCKr} , t _{SPCKf}	_	20	ns	
	Data input setup time (master) 2.7 V or above		2.7 V or above	t _{SU}	45	—	ns	Figure 2.42,
			2.4 V or above		55	_		Figure 2.43
			1.8 V or above		80	_		
	Data input se	tup time (slave)	L		40	—		
	Data input ho	ld time		t _H	40	—	ns	
	SSL input set	up time		t _{LEAD}	1	—	t _{SPcyc}	
	SSL input hol	d time		t _{LAG}	1	—	t _{SPcyc}	
	Data output d	lelay time (master)		t _{OD}	_	40	ns	
	Data output o	lelay time (slave)	2.7 V or above		_	65		
			1.8 V or above		_	100		
	Data output h	old time (master)	2.7 V or above	t _{он}	-10	—	ns	
			1.8 V or above		-20	—		
	Data output h	old time (slave)			-10	—		
	Data rise/fall	time		t _{Dr} , t _{Df}		20	ns	
	SSL input rise	e/fall time		t _{SSLr} , t _{SSLf}		20	ns	
	Slave $2.4 \text{ V} \leq \text{VCC} \leq 5.5 \text{ V}$			t _{SA}		6	t _{Pcyc}	Figure 2.44,
	access time	1.8 V ≤ VCC < 2.4 V	24 MHz < PCLKB ≤ 32 MHz			7		Figure 2.45
			PCLKB ≤ 24 MHz		_	6		
	Slave output 2.4 V ≤ VCC ≤ 5.5 V		t _{REL}	_	6	t _{Pcyc}	1	
	release time	1.8 V ≤ VCC < 2.4 V	24 MHz < PCLKB ≤ 32 MHz		_	7	-	
			PCLKB ≤ 24 MHz		_	6		

Note 1. t_{Pcyc}: PCLK cycle













Figure 2.43 Simple SPI Clock Timing (Master, CKPH = 0)



Figure 2.44 Simple SPI Clock Timing (Slave, CKPH = 1)

RENESAS



Figure 2.45 Simple SPI Clock Timing (Slave, CKPH = 0)



2.5.5.6 RIIC

Table 2.54 **RIIC** Timing

Conditions: $2.7 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $2.7 \text{ V} \le \text{AVCC0} \le 5.5 \text{ V}$, VSS = AVSS0 = 0 V, $\text{T}_{a} = -40 \text{ to } +105^{\circ}\text{C}$ Output load conditions: V_{OH} = 0.7 × VCC, V_{OL} = 0.3 × VCC, C = 30 pF

	Item	Symbol	Min.*1	Max.	Unit	Test Conditions
RIIC	SCL cycle time	t _{SCL}	6 (12) × t _{IICcyc} + 1300		ns	Figure 2.46
(standard mode, SMBus)	SCL high pulse width	t _{SCLH}	3 (6) × t _{IICcyc} + 300		ns	
	SCL low pulse width	t _{SCLL}	3 (6) × t _{IICcyc} + 300	_	ns	
	SCL, SDA rise time	t _{Sr}	—	1000	ns	
	SCL, SDA fall time	t _{Sf}	—	300	ns	
	SCL, SDA spike pulse removal time	t _{SP}	0	1 (4) × t _{IICcyc}	ns	
	SDA bus free time	t _{BUF}	3 (6) × t _{IICcyc} + 300	_	ns	
	START condition input hold time	t _{STAH}	t _{IICcyc} + 300		ns	
	Repeated START condition input setup time	t _{STAS}	1000	_	ns	
	STOP condition input setup time	t _{STOS}	1000	_	ns	
	Data setup time	t _{SDAS}	t _{IICcyc} + 50		ns	
	Data hold time	t _{SDAH}	0	_	ns	
	SCL, SDA capacitive load	C _b *2	—	400	pF	
RIIC	SCL cycle time	t _{SCL}	6 (12) × t _{IICcyc} + 600	_	ns	Figure 2.46
(fast mode)	SCL high pulse width	t _{SCLH}	3 (6) × t _{IICcyc} + 300	_	ns	
	SCL low pulse width	t _{SCLL}	3 (6) × t _{IICcyc} + 300	_	ns	
	SCL, SDA rise time	t _{Sr}	—	300	ns	
	SCL, SDA fall time	t _{Sf}	—	300	ns	
	SCL, SDA spike pulse removal time	t _{SP}	0	1 (4) × t _{IICcyc}	ns	
	SDA bus free time	t _{BUF}	3 (6) × t _{IICcyc} + 300	_	ns	
	START condition input hold time	t _{STAH}	t _{IICcyc} + 300	_	ns	
	Repeated START condition input setup time	t _{STAS}	300	_	ns	-
	STOP condition input setup time	t _{STOS}	300	_	ns	1
	Data setup time	t _{SDAS}	t _{IICcyc} + 50		ns	1
	Data hold time	t _{SDAH}	0		ns	1
	SCL, SDA capacitive load	C _b *2	_	400	pF	1

Note: t_{IICcyc} : RIIC internal reference count clock (IIC ϕ) cycle Note 1. The value in parentheses is used when the ICMR3.NF[1:0] bits are set to 11b while a digital filter is enabled with the ICFER.NFE bit = 1.

Note 2. C_b is the total capacitance of the bus lines.





Figure 2.46 RIIC Bus Interface Input/Output Timing



2.5.5.7 RSPI

Table 2.55 RSPI Timing (1/2)

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $1.8 \text{ V} \le \text{AVCC0} \le 5.5 \text{ V}$, VSS = AVSS0 = 0 V, $\text{T}_a = -40 \text{ to } +105^{\circ}\text{C}$, C = 30 pFOutput load conditions: $\text{V}_{OH} = 0.7 \times \text{VCC}$, $\text{V}_{OL} = 0.3 \times \text{VCC}$, C = 30 pF

			Item	Symbol	Min.	Max.	Unit	Test Condition
	RSPCK	Master		t _{SPcyc}	2	4096	t _{Pcyc} *1	Figure 2.47
	clock cycle	Slave			4			
	RSPCK clock high	Master		t _{SPCKWH}	${t_{SPCyc} - t_{SPCKr} - t_{SPCKr} - t_{SPCKf}} / 2 - 3$	_	ns	
	pulse width	Slave			${t_{SPCyc} - t_{SPCKr} - t_{SPCKr} - t_{SPCKf}} / 2$	_		
	RSPCK clock low	Master		t _{SPCKWL}	$(t_{SPcyc} - t_{SPCKr} - t_{SPCKf}) / 2 - 3$	_	ns	
	pulse width	Slave	lave		(t _{SPcyc} – t _{SPCKr} – t _{SPCKf}) / 2			
	RSPCK	Output	2.7 V or above	t _{SPCKr} ,	—	10	ns	
	clock rise/ fall time		2.4 V or above	t _{SPCKf}	_	15		
			1.8 V or above		_	20		
		Input	1		_	0.1	μs/V	
	Data input	Master	2.7 V or above	t _{SU}	10	_	ns	Figure 2.4
	setup time		1.8 V or above		30	_		to Figure 2.5
		Slave	2.7 V or above		10	_		Figure 2.5
			1.8 V or above		15	_		
	Data input hold time	Master	RSPCK set to a division ratio other than PCLKB divided by 2	t _H	t _{Pcyc}	_	ns	-
			RSPCK set to PCLKB divided by 2	t _{HF}	0			
		Slave	1	t _H	20			
Ī	SSL setup	Master		t _{LEAD}	–30 + N* ² × t _{SPcyc}		ns	
	time	Slave			6	_	t _{Pcyc}	
Ī	SSL hold	Master		t _{LAG}	$-30 + N^{*3} \times t_{SPcyc}$	_	ns	
	time	Slave			6	_	t _{Pcyc}	
	Data output	Master	2.7 V or above	t _{OD}	_	14	ns	
	delay time		2.4 V or above		_	20		
			1.8 V or above		_	25		
		Slave	2.7 V or above			50		
			2.4 V or above			60		
			1.8 V or above			85		
	Data output	Master	•	t _{OH}	0	_	ns	
	hold time	Slave		1	0	—	1	
	Successive transmissio	Master		t _{TD}	t_{SPcyc} + 2 × t_{Pcyc}	8 × t _{SPcyc} + 2 × t _{Pcyc}	ns	1
	n delay time	Slave		1	6 × t _{Pcyc}	—		
	MOSI and	Output	2.7 V or above	t _{Dr} , t _{Df}	—	10	ns	1
	MISO rise/		2.4 V or above	1		15		
	fall time		1.8 V or above	1		20		
		Input	1	1		1	μs	1



Table 2.55 RSPI Timing (2/2)

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $1.8 \text{ V} \le \text{AVCC0} \le 5.5 \text{ V}$, VSS = AVSS0 = 0 V, $\text{T}_{a} = -40 \text{ to } +105^{\circ}\text{C}$, C = 30 pFOutput load conditions: $\text{V}_{OH} = 0.7 \times \text{VCC}$, $\text{V}_{OL} = 0.3 \times \text{VCC}$, C = 30 pF

			Item	Symbol	Min.	Max.	Unit	Test Conditions
RSPI	SSL rise/fall	Output	2.7 V or above	t _{SSLr} ,	_	10	ns	Figure 2.48
	time		2.4 V or above	t _{SSLf}	_	15	ns	to Figure 2.51
			1.8 V or above		—	20	ns	
		Input	·		_	1	μs	
	Slave access	s time	2.4 V or above	t _{SA}	_	2 × t _{Pcyc} + 100	ns	Figure 2.50,
			1.8 V or above		_	2 × t _{Pcyc} + 140	ns	Figure 2.51
	Slave output	release	2.4 V or above	t _{REL}	_	2 × t _{Pcyc} + 100	ns	
	time		1.8 V or above		_	2 × t _{Pcyc} + 140	ns	

Note 1. t_{Pcyc}: PCLK cycle

Note 2. N: An integer from 1 to 8 that can be set by the RSPI clock delay register (SPCKD)

Note 3. N: An integer from 1 to 8 that can be set by the RSPI slave select negation delay register (SSLND)



Figure 2.47 RSPI Clock Timing





Figure 2.48 RSPI Timing (Master, CPHA = 0)



Figure 2.49 RSPI Timing (Master, CPHA = 1)







RENESAS

2.5.5.8 A/D Converter Trigger

Table 2.56 A/D Converter Trigger Timing

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $1.8 \text{ V} \le \text{AVCCO} \le 5.5 \text{ V}$, VSS = AVSSO = 0 V, $\text{T}_{a} = -40 \text{ to } +105^{\circ}\text{C}$

Output load conditions: V_{OH} = 0.7 × VCC, V_{OL} = 0.3 × VCC, C = 30 pF

Item	Symbol	Min.	Max.	Unit *1	Test Conditions
A/D converter Trigger input pulse width	t _{TRGW}	1.5	_	t _{Pcyc}	Figure 2.52

Note 1. t_{Pcyc} : PCLK cycle



Figure 2.52 A/D Converter External Trigger Input Timing

2.5.5.9 CAC

Table 2.57 **CAC** Timing

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $1.8 \text{ V} \le \text{AVCC0} \le 5.5 \text{ V}$, VSS = AVSS0 = 0 V, $\text{T}_{a} = -40 \text{ to } +105^{\circ}\text{C}$ Output load conditions: V_{OH} = 0.7 × VCC, V_{OL} = 0.3 × VCC, C = 30 pF

	Item		Symbol	Min.	Max.	Unit *1	Test Conditions
CAC	CACREF input pulse width	$t_{Pcyc} \le t_{cac}^{*2}$ $t_{Pcyc} > t_{cac}^{*2}$	t _{CACREF}	$4.5 t_{cac} + 3 t_{Pcyc}$ $5 t_{cac} + 6.5 t_{Pcyc}$	_	ns	
	CACREF input rise/fall time		t _{CACREFr} , t _{CACREFf}	—	0.1	µs/V	

Note 1. t_{Pcyc} : PCLK cycle Note 2. t_{cac} : CAC count clock source cycle



2.5.5.10 CLKOUT

Table 2.58 CLKOUT Timing

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $1.8 \text{ V} \le \text{AVCC0} \le 5.5 \text{ V}$, VSS = AVSS0 = 0 V, $\text{T}_{a} = -40 \text{ to } +105^{\circ}\text{C}$ Output load conditions: $\text{V}_{OH} = 0.7 \times \text{VCC}$, $\text{V}_{OL} = 0.3 \times \text{VCC}$, C = 30 pF

	Item			Min.	Max.	Unit	Test Conditions
CLKOUT	CLKOUT pin output cycle*2	VCC = 2.7 V or above	t _{Ccyc}	62.5	—	ns	Figure 2.53
		VCC = 1.8 V or above		125			
	CLKOUT pin high pulse width*1	VCC = 2.7 V or above	t _{CH}	15	—	ns	
		VCC = 1.8 V or above		30			
	CLKOUT pin low pulse width*1	VCC = 2.7 V or above	t _{CL}	15	—	ns	-
		VCC = 1.8 V or above		30			
	CLKOUT pin output rise time	VCC = 2.7 V or above	t _{Cr}	—	12	ns	-
		VCC = 1.8 V or above			25		
	CLKOUT pin output fall time	VCC = 2.7 V or above	t _{Cf}	—	12	ns	
		VCC = 1.8 V or above			25	1	

Note 1. When the LOCO is selected as the clock output source (CKOCR.CKOSEL[3:0] bits = 0000b), set the clock output division ratio selection to divided by 2 (CKOCR.CKODIV[2:0] bits = 001b).

Note 2. When the XTAL external clock input or an oscillator is used with divided by 1 (CKOCR.CKOSEL[3:0] bits = 010b and CKOCR.CKODIV[2:0] bits = 000b) to output from CLKOUT, the above should be satisfied with an input duty cycle of 45 to 55%.



Figure 2.53 CLKOUT Output Timing



2.6 A/D Conversion Characteristics

Table 2.59A/D Conversion Characteristics (1)

Conditions: $2.7 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $2.7 \text{ V} \le \text{VREFH0} = \text{AVCC0} \le 5.5 \text{ V}^{*1}$, VSS = AVSS0 = VREFL0 = 0 V, $\text{T}_{a} = -40 \text{ to } +105^{\circ}\text{C}$, signal source impedance = $0.3 \text{ k}\Omega$ Reference voltage = VREFH0

Item	1	Min.	Тур.	Max.	Unit	Test Conditions
Frequency		1	_	48	MHz	
Resolution		—	_	12	Bit	
Conversion time* ² (operation at PCLKD = 48 MHz)		0.67 (0.208)* ³	_	—	μs	High-precision channel ADCSR.ADHSC bit = 0 ADSSTRn = 0Ah ADCCR.CCS = 1
		1.29 (0.833)* ³	_	—	μs	Normal-precision channel ADCSR.ADHSC bit = 0 ADSSTRn = 28h ADCCR.CCS = 1
Analog input capacitance	Cs	—	_	9*4	pF	High-precision channel
		—	_	10* ⁴		Normal-precision channel
Analog input resistance	Rs	—	_	1.9* ⁴	kΩ	High-precision channel
		—	_	6.0*4		Normal-precision channel
Analog input effective rang	je	0	_	VREFH0	V	
Offset error		—	±1.0	±4.5	LSB	High-precision channel
				±6.0	LSB	Other than above
Full-scale error		—	±1.0	±4.5	LSB	High-precision channel
				±6.0	LSB	Other than above
Quantization error		—	± 0.5	—	LSB	
Absolute accuracy		—	±2.5	±5.5	LSB	High-precision channel
				±8.5	LSB	Other than above
DNL differential nonlinearit	ty error	—	±1.0	—	LSB	
INL integral nonlinearity er	ror	—	±1.5	±3.0	LSB	

Note: The characteristics apply when no pin functions other than A/D converter input are used. Absolute accuracy includes quantization errors. Offset error, full-scale error, DNL differential nonlinearity error, and INL integral nonlinearity error do not include quantization errors.

Note 1. For 32-pin products, VREFH0 = AVCC0.

Note 2. The conversion time is the sum of the sampling time and the comparison time. As the test conditions, the number of sampling states is indicated.

Note 3. The values in () show the sampling times.



Table 2.60 A/D Conversion Characteristics (2)

Conditions: $2.4 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $2.4 \text{ V} \le \text{VREFH0} = \text{AVCC0} \le 5.5 \text{ V}^{*1}$, VSS = AVSS0 = VREFL0 = 0 V, $\text{T}_a = -40 \text{ to } +105^{\circ}\text{C}$, signal source impedance = $1.3 \text{ k}\Omega$ Reference voltage = VREFH0

I	tem	Min.	Тур.	Max.	Unit	Test Conditions
Frequency		1	_	32	MHz	
Resolution		—	_	12	Bit	
Conversion time*2 (Operation at PCLKD = 32 MHz)		1.00 (0.313)* ³	_	—	μs	High-precision channel ADCSR.ADHSC bit = 0 ADSSTRn = 0Ah ADCCR.CCS = 1
		1.94 (1.250)* ³	_	—	μs	Normal-precision channel ADCSR.ADHSC bit = 0 ADSSTRn = 28h ADCCR.CCS = 1
Analog input	Cs	—	_	9*4	pF	High-precision channel
capacitance		—	_	10*4		Normal-precision channel
Analog input	Rs	—	_	2.2*4	kΩ	High-precision channel
resistance		—	_	7.0*4		Normal-precision channel
Analog input effective r	ange	0	_	VREFH0	V	
Offset error		—	±1.0	±4.5	LSB	High-precision channel
				±6.0	LSB	Other than above
Full-scale error		—	±1.0	±4.5	LSB	High-precision channel
				±6.0	LSB	Other than above
Quantization error		—	±0.5	—	LSB	
Absolute accuracy		—	±2.5	±5.5	LSB	High-precision channel
				±8.5	LSB	Other than above
DNL differential nonline	earity error	—	±1.0	—	LSB	
INL integral nonlinearity	y error	—	±1.5	±3.0	LSB	

Note: The characteristics apply when no pin functions other than A/D converter input are used. Absolute accuracy includes quantization errors. Offset error, full-scale error, DNL differential nonlinearity error, and INL integral nonlinearity error do not include quantization errors.

Note 1. For 32-pin products, VREFH0 = AVCC0.

Note 2. The conversion time is the sum of the sampling time and the comparison time. As the test conditions, the number of sampling states is indicated.

Note 3. The values in () show the sampling times.



Table 2.61 A/D Conversion Characteristics (3)

Conditions: $2.7 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $2.7 \text{ V} \le \text{VREFH0} = \text{AVCC0} \le 5.5 \text{ V}^{*1}$, VSS = AVSS0 = VREFL0 = 0 V, $\text{T}_a = -40 \text{ to } +105^{\circ}\text{C}$, signal source impedance = $1.1 \text{ k}\Omega$ Reference voltage = VREFH0

	Item	Min.	Тур.	Max.	Unit	Test Conditions
Frequency		1	_	24	MHz	
Resolution		_	_	12	Bit	
Conversion time*2 (operation at PCLKD = 24 MHz)		1.58 (0.417)* ³	_	—	μs	High-precision channel ADCSR.ADHSC bit = 1 ADSSTRn = 0Ah ADCCR.CCS = 1
		2.00 (0.833)* ³	_	_		Normal-precision channel ADCSR.ADHSC bit = 1 ADSSTRn = 14h ADCCR.CCS = 1
Analog input	Cs	—	_	9*4	pF	High-precision channel
capacitance		—	_	10*4		Normal-precision channel
Analog input	Rs	—	_	1.9* ⁴	kΩ	High-precision channel
resistance		—	_	6*4		Normal-precision channel
Analog input effective	e range	0	_	VREFH0	V	
Offset error		—	±1.25	±4.5	LSB	High-precision channel
				±6.0	LSB	Other than above
Full-scale error		—	±1.0	±4.5	LSB	High-precision channel
				±6.0	LSB	Other than above
Quantization error		—	±0.5	—	LSB	
Absolute accuracy		—	±2.5	±5.5	LSB	High-precision channel
				±8.5	LSB	Other than above
DNL differential nonli	inearity error	—	±1.0	—	LSB	
INL integral nonlinea	rity error	—	±1.5	±3.0	LSB	

Note: The characteristics apply when no pin functions other than A/D converter input are used. Absolute accuracy includes quantization errors. Offset error, full-scale error, DNL differential nonlinearity error, and INL integral nonlinearity error do not include quantization errors.

Note 1. For 32-pin products, VREFH0 = AVCC0.

Note 2. The conversion time is the sum of the sampling time and the comparison time. As the test conditions, the number of sampling states is indicated.

Note 3. The values in () show the sampling times.



Table 2.62 A/D Conversion Characteristics (4)

Conditions: $2.4 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $2.4 \text{ V} \le \text{VREFH0} = \text{AVCC0} \le 5.5 \text{ V}^{*1}$, VSS = AVSS0 = 0 V, $\text{T}_a = -40 \text{ to } +105^{\circ}\text{C}$, signal source impedance = $2.2 \text{ k}\Omega$ Reference voltage = VREFH0

It	em	Min.	Тур.	Max.	Unit	Test Conditions
Frequency		1	—	16	MHz	
Resolution		—	_	12	Bit	
Conversion time ^{*2} (operation at PCLKD = 16 MHz)		2.38 (0.625)* ³	_	—	μs	High-precision channel ADCSR.ADHSC bit = 1 ADSSTRn = 0Ah ADCCR.CCS = 1
		3.00 (1.250)* ³	_	—		Normal-precision channel ADCSR.ADHSC bit = 1 ADSSTRn = 14h ADCCR.CCS = 1
Analog input	Cs	—	—	9*4	pF	High-precision channel
capacitance		—	—	10* ⁴		Normal-precision channel
Analog input	Rs	—	—	2.2*4	kΩ	High-precision channel
resistance		—	—	7* ⁴		Normal-precision channel
Analog input effective ra	ange	0	_	VREFH0	V	
Offset error		—	±1.25	±4.5	LSB	High-precision channel
				±6.0	LSB	Other than above
Full-scale error		—	±1.0	±4.5	LSB	High-precision channel
				±6.0	LSB	Other than above
Quantization error		—	±0.5	—	LSB	
Absolute accuracy		—	±2.5	±5.5	LSB	High-precision channel
				±8.5	LSB	Other than above
DNL differential nonline	arity error	—	±1.0	—	LSB	
INL integral nonlinearity	error	_	±1.5	±3.0	LSB	

Note: The characteristics apply when no pin functions other than A/D converter input are used. Absolute accuracy includes quantization errors. Offset error, full-scale error, DNL differential nonlinearity error, and INL integral nonlinearity error do not include quantization errors.

Note 1. or 32-pin products, VREFH0 = AVCC0.

Note 2. The conversion time is the sum of the sampling time and the comparison time. As the test conditions, the number of sampling states is indicated.

Note 3. The values in () show the sampling times.



Table 2.63 A/D Conversion Characteristics (5)

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $1.8 \text{ V} \le \text{VREFH0} = \text{AVCC0} \le 5.5 \text{ V}^{*1}$, VSS = AVSS0 = VREFL0 = 0 V, $\text{T}_a = -40 \text{ to } +105^{\circ}\text{C}$, signal source impedance = $5 \text{ k}\Omega$ Reference voltage = VREFH0

	Item	Min.	Тур.	Max.	Unit	Test Conditions
Frequency		1		8	MHz	
Resolution		_		12	Bit	
Conversion time ^{*2} (operation at PCLKD = 8 MHz)	operation at			—	μs	High-precision channel ADCSR.ADHSC bit = 1 ADSSTRn = 0Ah ADCCR.CCS = 1
		6.00 (2.500)* ³	_	_		Normal-precision channel ADCSR.ADHSC bit = 1 ADSSTRn = 14h ADCCR.CCS = 1
Analog input capacitance	Cs	—	_	9*4	pF	High-precision channel
		—	_	10* ⁴		Normal-precision channel
Analog input	Rs	_		6*4	kΩ	High-precision channel
resistance		_		14* ⁴		Normal-precision channel
Analog input effective	range	0	_	VREFH0	V	
Offset error		_	±1.25	±7.5	LSB	High-precision channel
				±10.0	LSB	Other than above
Full-scale error		—	±1.5	±7.5	LSB	High-precision channel
				±10.0	LSB	Other than above
Quantization error		—	±0.5	—	LSB	
Absolute accuracy		—	±3.0	±8.0	LSB	High-precision channel
				±11.0	LSB	Other than above
DNL differential nonlin	earity error	—	±1.25	—	LSB	
INL integral nonlineari	ty error	_	±1.5	±3.5	LSB	

Note: The characteristics apply when no pin functions other than A/D converter input are used. Absolute accuracy includes quantization errors. Offset error, full-scale error, DNL differential nonlinearity error, and INL integral nonlinearity error do not include quantization errors.

Note 1. For 32-pin products, VREFH0 = AVCC0.

Note 2. The conversion time is the sum of the sampling time and the comparison time. As the test conditions, the number of sampling states is indicated.

Note 3. The values in () show the sampling times.



Classification	Channel	Conditions	Remarks				
High-precision channel	AN000 to AN007	AVCC0 = 1.8 to 5.5 V	Pins AN000 to AN007 cannot be used as digi				
Normal-precision channel	AN016 to AN021, AN024 to AN026		outputs when the A/D converter is in use.				
Internal reference voltage input channel	Internal reference voltage	AVCC0 = 1.8 to 5.5 V					
Temperature sensor input channel	Temperature sensor output	AVCC0 = 1.8 to 5.5 V					
CTSU input channels	AN008	AVCC0 = 1.8 to 5.5V					

Table 2.64 A/D Converter Channel Classification

Table 2.65 A/D Internal Reference Voltage Characteristics

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}, 1.8 \text{ V} \le \text{VREFH0} = \text{AVCC0} \le 5.5 \text{ V}, \text{VSS} = \text{AVSS0} = \text{VREFL0} = 0 \text{ V}, \text{ T}_{a} = -40 \text{ to } +105^{\circ}\text{C}$

Item	Min.	Тур.	Max.	Unit	Test Conditions
Internal reference voltage input channel*1	1.42	1.48	1.54	V	

Note 1. The A/D internal reference voltage indicates the voltage when the internal reference voltage is input to the A/D converter.









Figure 2.55 Illustration of A/D Converter Characteristic Terms

Absolute accuracy

Absolute accuracy is the difference between output code based on the theoretical A/D conversion characteristics, and the actual A/D conversion result. When measuring absolute accuracy, the voltage at the midpoint of the width of analog input voltage (1-LSB width), that can meet the expectation of outputting an equal code based on the theoretical A/D conversion characteristics, is used as an analog input voltage. For example, if 12-bit resolution is used and if reference voltage (VREFH0 = 3.072 V), then 1-LSB width becomes 0.75 mV, and 0 mV, 0.75 mV, 1.5 mV, ... are used as analog input voltages.

If analog input voltage is 6 mV, absolute accuracy = ± 5 LSB means that the actual A/D conversion result is in the range of 003h to 00Dh though an output code, 008h, can be expected from the theoretical A/D conversion characteristics.

Integral nonlinearity error (INL)

Integral nonlinearity error is the maximum deviation between the ideal line when the measured offset and full-scale errors are zeroed, and the actual output code.

Differential nonlinearity error (DNL)

Differential nonlinearity error is the difference between 1-LSB width based on the ideal A/D conversion characteristics and the width of the actual output code.

Offset error

Offset error is the difference between a transition point of the ideal first output code and the actual first output code.

Full-scale error

Full-scale error is the difference between a transition point of the ideal last output code and the actual last output code.



2.7 D/A Conversion Characteristics

Table 2.66D/A Conversion Characteristics (1)Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $1.8 \text{ V} \le \text{AVCC0} \le 5.5 \text{ V}$, VSS = AVSS0 = 0 V, $\text{T}_a = -40 \text{ to } +105^{\circ}\text{C}$

	Item		Min.	Тур.	Max.	Unit	Test Conditions	
Resolution		—	_	—	8	Bit		
Conversion time	VCC = 1.8 to 5.5 V	t _{DCONV}	_	—	3.0	μs	35-pF capacitive load	
Absolute VCC = 2.4	VCC = 2.4 to 5.5 V	—	_	—	±3.0	LSB	2-M Ω resistive load	
accuracy	VCC = 1.8 to 2.4 V	—	_	—	±3.5			
	VCC = 2.4 to 5.5 V	—		—	±2.0	LSB	4-M Ω resistive load	
	VCC = 1.8 to 2.4 V	—		—	±2.5			
RO output resistance		—	_	9.0	_	kΩ		



2.8 Temperature Sensor Characteristics

Table 2.67 Temperature Sensor Characteristics

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $1.8 \text{ V} \le \text{AVCC0} \le 5.5 \text{ V}$, VSS = AVSS0 = 0 V, $\text{T}_{a} = -40 \text{ to } +105^{\circ}\text{C}$

Item	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Relative accuracy	_	—	±1.5	—	°C	2.4 V or above
		—	±2.0	—		Below 2.4 V
Temperature slope	_	—	-3.3	—	mV/°C	
Output voltage (25°C)	—	—	1.05	—	V	VCC = 3.3 V
Temperature sensor start time	t _{START}	—	—	5	μs	
Sampling time*1	—	5	—	—	μs	

Note 1. Set the S12AD.ADSSTRT register so that the sampling time of the 12-bit A/D converter meets this specification.

2.9 Comparator Characteristics

Table 2.68 Comparator Characteristics

Conditions: 1.8 V ≤ VCC ≤ 5.5 V, 1.8 V ≤ AVCC0 ≤ 5.5 V, VSS = AVSS0 = 0 V, $T_a = -40$ to +105°C

	Item	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
CVREFB0 to CVR voltage	EFB1 input reference	VREF	0	—	VCC - 1.4	V	
CMPB0 to CMPB2	l input voltage	VI	0	—	VCC	V	
Internal reference	Internal reference voltage		1.34	1.44	1.54	V	
Offset	Comparator high-speed mode	—	—	—	50	mV	
	Comparator high-speed mode Window function enabled	—	_	_	60	mV	
	Comparator low-speed mode	—	—	—	40	mV	
Comparator output delay time	Comparator high-speed mode	Td	—	—	1.2	μs	VCC = 3 V, input slew rate ≥ 50 mV/µs
. ,	Comparator high-speed mode Window function enabled	Tdw	—	—	2.0	μs	
	Comparator low-speed mode	Td	_	—	9.0	μs	
High-side reference voltage (comparator high-speed mode, window function enabled)		VRFH	_	0.76 × VCC	_	V	
	Low-side reference voltage (comparator high-speed mode, window function enabled)		_	0.24 × VCC	_	V	
Operation stabilization	ation wait time	Tcmp	100	—	—	μs	











Comparator Output Delay Time in High-Speed Mode with Window Function Enabled

2.10 CTSU Characteristics

Table 2.69 CTSU Characteristics

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $1.8 \text{ V} \le \text{AVCC0} \le 5.5 \text{ V}$, VSS = AVSS0 = 0 V, $\text{T}_{a} = -40 \text{ to } +105^{\circ}\text{C}$

	Item	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
External capacitance connected to TSCAP pin		C _{tscap}	9	10	11	nF	
Permissible output high/low current	P12 to P17, P20, P21, P26, P27, P30 to P32, P34, P35, P54, P55, PB1 to PB7, PC2 to PC7, PH0 to PH3	ΣΙ _{ΟΗ} + ΣΙ _{ΟL}	_	_	24	mA	When VXSEL = 0
	PA0, PA1, PA3, PA4, PA6, PB0, PE0 to PE5		_	_	16	mA	[Products with 64 Kbytes of flash memory or less] When VXSEL = 0
	PA0 to PA6, PB0, PD0 to PD2, PE0 to PE5		_	_	16	mA	[Products with at least 128 Kbytes of flash memory] When VXSEL = 0

2.11 Power-On Reset Circuit and Voltage Detection Circuit Characteristics

Table 2.70 Power-On Reset Circuit and Voltage Detection Circuit Characteristics (1)

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $1.8 \text{ V} \le \text{AVCC0} \le 5.5 \text{ V}$, VSS = AVSS0 = 0 V, $\text{T}_{a} = -40 \text{ to } +105^{\circ}\text{C}$

	Item	Symbol	Min.	Тур.	Max.	Unit	Test Conditions		
Voltage detection	Power-on reset (POR)	V _{POR}	1.35	1.50	1.65	V	Figure 2.58, Figure 2.59		
level	Voltage detection circuit	V _{det0_0}	3.67	3.85	3.97	V	Figure 2.60		
	(LVD0)*1	V _{det0_1}	2.70	2.85	3.00		At falling edge VCC		
		V _{det0_2}	2.37	2.53	2.67				
		V _{det0_3}	1.80	1.90	1.99				
	Voltage detection circuit	V _{det1_0}	4.12	4.29	4.42	V	Figure 2.61		
	(LVD1)* ²	V _{det1_1}	3.98	4.16	4.28		At falling edge VCC		
		V _{det1_2}	3.86	4.03	4.16				
		V _{det1_3}	3.68	3.86	3.98				
		V _{det1_4}	2.99	3.10	3.29				
		V _{det1_5}	2.89	3.00	3.19				
		V _{det1_6}	2.79	2.90	3.09				
		V _{det1_7}	2.68	2.80	2.98				
		V _{det1_8}	2.57	2.68	2.87				
		V _{det1_9}	2.47	2.59	2.67				
		V _{det1_A}	2.37	2.48	2.57				
		V _{det1_B}	2.10	2.20	2.30				
		V _{det1_C}	1.86	1.96	2.06				
		V _{det1_D}	1.80	1.86	1.96				
Voltage detection	Voltage detection circuit	V _{det2_0} *4	4.08	4.32	4.48	V	Figure 2.62		
level	(LVD2)*3	V _{det2_1}	3.95	4.17	4.35		At falling edge VCC		
		V _{det2_2}	3.82	4.03	4.22				
		V _{det2_3}	3.62	3.84	4.02				

Note: These characteristics apply when noise is not superimposed on the power supply. When a setting is made so that the voltage detection level overlaps with that of the voltage detection circuit (LVD2), it cannot be specified which of LVD1 and LVD2 is used for voltage detection.

- Note 1. n in the symbol Vdet0_n denotes the value of the LDSEL1[1:0] bits.
- Note 2. n in the symbol Vdet1_n denotes the value of the LVDLVLR.LVD1LVL[3:0] bits.
- Note 3. n in the symbol Vdet2_n denotes the value of the LVDLVLR.LVD2LVL[1:0] bits.
- Note 4. Vdet2_0 selection can be used only when the CMPA2 pin input voltage is selected, and cannot be used when the power supply voltage (VCC) is selected.

Table 2.71 Power-On Reset Circuit and Voltage Detection Circuit Characteristics (2)

Conditions: $1.8 \text{ V} \le \text{AVCC0} \le 5.5 \text{ V}$, VSS = AVSS0 = 0 V, $\text{T}_a = -40 \text{ to } +105^{\circ}\text{C}$

	Item	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Wait time after	At normal startup*1	t _{POR}	_	12.5	_	ms	Figure 2.59
power-on reset cancellation	During fast startup time* ²	t _{POR}		5.0	—		
Wait time after voltage cancellation	e monitoring 0 reset	t _{LVD0}		860	—	μs	Figure 2.60
Wait time after	LVD0 disabled*4	t _{LVD1}	—	160	—	μs	Figure 2.61
voltage monitoring 1 reset cancellation	LVD0 enabled*5		—	860	—	μs	_
Wait time after	-		—	160	—	μs	Figure 2.62
voltage monitoring 2 reset cancellation	LVD0 enabled*5		—	860	—	μs	_
PDR response delay time		t _{det}			500	μs	Figure 2.58
LVD0 response delay			_	500	μs	Figure 2.58	
LVD1 response delay				360	μs	Figure 2.58	
LVD2 response delay time			_	—	600	μs	Figure 2.58
POR/LVD0 minimum VCC down time*3		t _{VOFF}	500	—	—	μs	Figure 2.58, VCC = 1.0 V or above
LVD1 minimum VCC down time*3			300		—	μs	Figure 2.58, VCC = 1.0 V or above
LVD2 minimum VCC	down time* ³		600		—	μs	Figure 2.58, VCC = 1.0 V or above
Power-on reset enable	e time	t _{W(POR)}	1		—	ms	Figure 2.59, VCC = below 1.0 V
LVD1 operation stabili enabled)	ization time (after LVD is	t _{d(E-A)}	_		300	μs	Figure 2.61
LVD2 operation stabili enabled)	ization time (after LVD is	t _{d(E-A)}			1200	μs	Figure 2.62
Hysteresis width (pow	ver-on rest (POR))	V _{PORH}	—	110	_	mV	
Hysteresis width (LVD	00, LVD1, and LVD2)	V _{LVH}	—	60	—	mV	Vdet0_0 to Vdet0_3 selected
			—	110	—		Vdet1_0 to Vdet1_2 selected
			—	70	—	1	Vdet1_3 to 9 selected
				60	—		Vdet1_A to B selected
			_	50	—		Vdet1_C to D selected
				90	_		LVD2 selected

Note: These characteristics apply when noise is not superimposed on the power supply. When a setting is made so that the voltage detection level overlaps with that of the voltage detection circuit (LVD1), it cannot be specified which of LVD1 and LVD2 is used for voltage detection.

Note 1. When OFS1.(LVDAS, FASTSTUP) = 11b.

Note 2. When OFS1.(LVDAS, FASTSTUP) ≠ 11b.

Note 3. The minimum VCC down time indicates the time when VCC is below the minimum value of voltage detection levels V_{POR} , V_{det0} , V_{det1} , and V_{det2} for the POR/LVD.

Note 4. When OFS1.LVDAS = 1b.

Note 5. When OFS1.LVDAS = 0b.













Figure 2.60 Voltage Detection Circuit Timing (V_{det0})



Figure 2.61 Voltage Detection Circuit Timing (V_{det1})



Figure 2.62 Voltage Detection Circuit Timing (V_{det2})



2.12 Oscillation Stop Detection Timing

Table 2.72 Oscillation Stop Detection Timing

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $1.8 \text{ V} \le \text{AVCC0} \le 5.5 \text{ V}$, VSS = AVSS0 = 0 V, $\text{T}_{a} = -40 \text{ to } +105^{\circ}\text{C}$

Item	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Detection time	t _{dr}	_	_	1	ms	Figure 2.63



Figure 2.63 Oscillation Stop Detection Timing



2.13 ROM (Flash Memory for Code Storage) Characteristics

Item	Symbol	Min.	Тур.	Max.	Unit	Conditions
Program/erase cycles*1	N _{PEC}	1K	_	—	Times	
Data retention* ^{2, *3} After 1K times of N _{PEC}	t _{DRP}	20		_	Year	T _a = +105°C

Table 2.73 ROM (Flash Memory for Code Storage) Characteristics (1)

Note 1. Definition of program/erase cycle:

The program/erase cycle is the number of erasing for each block. When the number of program/erase cycles is n, each block can be erased n times. For instance, when 8-byte program is performed 256 times for different addresses in a 2-Kbyte block and then the block is erased, the program/erase cycle is counted as one. However, the same address cannot be programmed more than once before the next erase cycle (overwriting is prohibited).

Note 2. Characteristic when using the flash memory programmer and the self-programming library provided from Renesas Electronics. Note 3. This result is obtained from reliability testing.

Table 2.74 ROM (Flash Memory for Code Storage) Characteristics (2) High-Speed Operating Mode

Conditions: 1.8 V ≤ VCC ≤ 5.5 V, 1.8 V ≤ AVCC0 ≤ 5.5 V, VSS = AVSS0 = 0 V Temperature range for the programming/erasure operation: $T_a = -40$ to +105°C

Item		Symbol	FC	LK = 1 N	lHz	FCI	LK = 32 I	MHz	FCI	_K = 48 M	ИНz	Unit
item		Symbol	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.	Onic
Programming time	8-byte	t _{P8}	_	94.0	843.5	_	45.4	448.7	—	45.1	446.0	μs
Erasure time	2-Kbyte	t _{E2K}	_	8.3	282.0	_	5.4	220.4	_	5.4	220.1	ms
	64-Kbyte	t _{E64K}	_	105	2331	_	12.7	375.4	_	12.4	368.0	ms
Blank check time	8-byte	t _{BC8}	_	_	45.0	_	_	8.9	_	—	8.7	μs
	2-Kbyte	t _{BC2K}	_	_	1573	_	_	120	_	—	115	μs
Erase operation forc time	ible stop	t _{SED}	—	_	22.8	_	—	11.1	_	—	11.0	μs
Start-up area switchi time	ng setting	t _{SAS}	—	8.2	503.3		5.6	438.0	_	5.6	437.7	ms
Access window setting	ng time	t _{AWS}	—	8.2	503.3	—	5.6	438.0	—	5.6	437.7	ms
ROM mode transition	n wait time	t _{MS}	15	_	_	15	_	_	15	—	_	μs

Note: Does not include the time until each operation of the flash memory is started after instructions are executed by software. Note: The lower-limit frequency of FCLK is 1 MHz during programming or erasing of the flash memory. When using FCLK at below 4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.

Note: The frequency accuracy of FCLK should be ±3.5%.



Table 2.75ROM (Flash Memory for Code Storage) Characteristics (3) Middle-Speed Operating ModeConditions: $1.8 \ V \le VCC \le 5.5 \ V$, $1.8 \ V \le AVCC0 \le 5.5 \ V$, $VSS = AVSS0 = 0 \ V$ Temperature range for the programming/erasure operation: $T_a = -40 \ to +105^{\circ}C$

Item		Symbol	F	CLK = 1 MF	lz	F	Unit		
		Symbol	Min.	Тур.	Max.	Min.	Тур.	Max.	Unit
Programming time	8-byte	t _{P8}		94.0	843.5	_	45.7	450.7	μs
Erasure time	2-Kbyte	t _{E2K}	—	8.3	282.0	—	5.4	220.2	ms
	64-Kbyte	t _{E64K}	—	105	2331	—	17.0	500.5	ms
Blank check time	8-byte	t _{BC8}	—	—	45	—	—	9	μs
	2-Kbyte	t _{BC2K}	—	—	1573	—	—	115	μs
Erase operation forcible stop time		t _{SED}	—	—	22.8	—	—	11.2	μs
Start-up area switching setting time		t _{SAS}	—	8.2	503.3	—	5.6	437.7	ms
Access window setting time		t _{AWS}	—	8.2	503.3	—	5.6	437.7	ms
ROM mode transition wait time		t _{MS}	15	—	—	15	—	—	μs

 Note:
 Does not include the time until each operation of the flash memory is started after instructions are executed by software.

 Note:
 The lower-limit frequency of FCLK is 1 MHz during programming or erasing of the flash memory. When using FCLK at below 4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.

 Note:
 The frequency accuracy of FCLK should be ±3.5%.

Table 2.76 ROM (Flash Memory for Code Storage) Characteristics (4) Middle-Speed Operating Mode 2

Conditions: 1.8 V \leq VCC \leq 5.5 V, 1.8 V \leq AVCC0 \leq 5.5 V, VSS = AVSS0 = 0 V Temperature range for the programming/erasure operation: T_a = -40 to +105°C

lten	Item		FCLK = 1 MHz					
nem		Symbol	Min.	Тур.	Max.	— Unit		
Programming time	8-byte	t _{P8}	—	94.0	843.5	μs		
Erasure time	2-Kbyte	t _{E2K}	_	8.3	282.0	ms		
	64-Kbyte	t _{E64K}	_	105	2331	ms		
Blank check time	8-byte	t _{BC8}	_	—	45	μs		
	2-Kbyte	t _{BC2K}	_	—	1573	μs		
Erase operation forcible stop time		t _{SED}	—	—	22.8	μs		
Start-up area switching setting time		t _{SAS}	_	8.2	503.3	ms		
Access window setting time		t _{AWS}	_	8.2	503.3	ms		
ROM mode transition wait time		t _{MS}	15	—	—	μs		

Note: Does not include the time until each operation of the flash memory is started after instructions are executed by software.

Note: The lower-limit frequency of FCLK is 1 MHz during programming or erasing of the flash memory.

Note: The frequency accuracy of FCLK should be ±3.5%.



2.14 E2 DataFlash Characteristics (Flash Memory for Data Storage)

Item		Symbol	Min.	Тур.	Max.	Unit	Conditions
Program/erase cycles*1		N _{DPEC}	100K	1000K	—	Times	
Data retention	After 10K times of N _{DPEC}	t _{DDRP}	20* ^{2, *3}	—	—	Year	T _a = +105°C
	After 100K times of N _{DPEC}		5* ^{2, *3}	—	—	Year	
	After 1000K times of N _{DPEC}		—	1* ^{2, *3}	—	Year	T _a = +25°C

Table 2.77 E2 DataFlash Characteristics (1)

Note 1. Definition of program/erase cycle:

The program/erase cycle is the number of erasing for each block. When the number of program/erase cycle is n, each block can be erased n times. For instance, when 1-byte program is performed 256 times for different addresses in a 256-byte block and then the block is erased, the program/erase cycle is counted as one. However, the same address cannot be programmed more than once before the next erase cycle (overwriting is prohibited).

Note 2. Characteristic when using the flash memory programmer and the self-programming library provided from Renesas Electronics.

Note 3. These results are obtained from reliability testing.

Table 2.78 E2 DataFlash Characteristics (2) High-speed operating mode

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $1.8 \text{ V} \le \text{AVCCO} \le 5.5 \text{ V}$, VSS = AVSSO = 0 V

Temperature range for the programming/erasure operation: $T_a = -40$ to +105°C

ltem		Symbol	FCLK = 1 MHz			FCLK = 32 MHz			FCLK = 48 MHz			Unit
		Symbol	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.	Unit
Programming time	1-byte	t _{DP1}		83.0	729.5	_	35.1	341.2		34.8	338.8	μs
Erasure time	256-byte	t _{DE256}		8.3	282.0		5.4	220.4	-	5.4	220.1	ms
	4-Kbyte	t _{DE4K}	_	55.0	1273.7		9.0	295.4	_	8.8	291.7	ms
Blank check time	1-byte	t _{DBC1}	_	_	44.6		_	8.9	_	_	8.2	μs
	256-byte	t _{DBC256}	_	_	1573		_	120	_	_	115	μs
Erase operation forcible stop time		t _{DSED}	_	_	22.8		_	11.1	_		11.0	μs
DataFlash STOP recovery time		t _{DSTOP}	250	—	_	250	—	_	250		—	ns

Note:Does not include the time until each operation of the flash memory is started after instructions are executed by software.Note:The lower-limit frequency of FCLK is 1 MHz during programming or erasing of the flash memory. When using FCLK at below
4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.

Note: The frequency accuracy of FCLK should be ±3.5%.

Table 2.79E2 DataFlash Characteristics (3) Middle-speed operating modeConditions: $1.8 V \le VCC \le 5.5 V$, $1.8 V \le AVCC0 \le 5.5 V$, VSS = AVSS0 = 0 V

Temperature range for the programming/erasure operation: $T_a = -40$ to $+105^{\circ}C$

Item		Symbol	F	CLK = 1 M⊦	z	FCLK = 8 MHz			Unit
		Symbol	Min.	Тур.	Max.	Min.	Тур.	Max.	Onic
Programming time	1-byte	t _{DP1}	—	83.0	729.5	—	35.3	343.2	μs
Erasure time	256-byte	t _{DE256}	—	8.3	282.0	—	5.4	220.2	ms
	4-Kbyte	t _{DE4K}	—	55.0	1273.7	—	8.8	291.8	ms
Blank check time	1-byte	t _{DBC1}	—	—	44.6	—	—	9.0	μs
	256-byte	t _{DBC256}	—	—	1573	—	—	115	ms
Erase operation forcible stop time		t _{DSED}	—	—	22.8	—	—	11.2	μs
DataFlash STOP recovery time		t _{DSTOP}	250	—	_	250	—	—	ns

 Note:
 Does not include the time until each operation of the flash memory is started after instructions are executed by software.

 Note:
 The lower-limit frequency of FCLK is 1 MHz during programming or erasing of the flash memory. When using FCLK at below 4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.

 Note:
 The frequency accuracy of FCLK should be ±3.5%.

Table 2.80 E2 DataFlash Characteristics (4) Middle-speed operating mode 2

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, $1.8 \text{ V} \le \text{AVCC0} \le 5.5 \text{ V}$, VSS = AVSS0 = 0 VTemperature range for the programming/erasure operation: $T_a = -40 \text{ to } +105^{\circ}\text{C}$

Item		Symbol		Unit		
		Symbol	Min.	Тур.	Max.	Unit
Programming time	1-byte	t _{DP1}	—	83.0	729.5	μs
Erasure time	256-byte	t _{DE256}	—	8.3	282.0	ms
	4-Kbyte	t _{DE4K}	—	55.0	1273.7	ms
Blank check time	1-byte	t _{DBC1}	—	—	44.6	μs
	256-byte	t _{DBC256}	—	—	1573	ms
Erase operation forcible stop time		t _{DSED}	—	—	22.8	μs
DataFlash STOP recovery time		t _{DSTOP}	250	—	_	ns

Note: Does not include the time until each operation of the flash memory is started after instructions are executed by software.

Note: The lower-limit frequency of FCLK is 1 MHz during programming or erasing of the flash memory.

Note: The frequency accuracy of FCLK should be ±3.5%.



2.15 Usage Notes

2.15.1 Connecting VCL Capacitor and Bypass Capacitors

This MCU integrates an internal voltage-down circuit, which is used for lowering the power supply voltage in the internal MCU to adjust automatically to the optimum level. A 4.7- μ F capacitor needs to be connected between this internal voltage-down power supply (VCL pin) and VSS pin. Figure 2.64 to Figure 2.66 shows how to connect external capacitors. Place an external capacitor close to the pins. Do not apply the power supply voltage to the VCL pin. Insert a multilayer ceramic capacitor as a bypass capacitor between each pair of the power supply pins. Implement a bypass capacitor to the MCU power supply pins as close as possible. Use a recommended value of 0.1 μ F as the capacitance of the capacitors. For the capacitors related to crystal oscillation, see section 9, Clock Generation Circuit in the User's Manual: Hardware. For the capacitors related to analog modules, also see section 35, 12-Bit A/D Converter (S12ADE) in the User's Manual: Hardware.

For notes on designing the printed circuit board, see the descriptions of the application note "Hardware Design Guide" (R01AN1411EJ). The latest version can be downloaded from Renesas Electronics Website.









Connecting Capacitors (64 Pins) Figure 2.65








Figure 2.67 **Connecting Capacitors (32 Pins)**



Appendix 1. Package Dimensions

Information on the latest version of the package dimensions or mountings has been displayed in "Packages" on Renesas Electronics Corporation website.







Figure B 64-Pin LQFP (PLQP0064GA-A)





Figure C 64-Pin LFQFP (PLQP0064KB-C)





Figure D 48-Pin HWQFN (PWQN0048KC-A)





Figure E 48-Pin LFQFP (PLQP0048KB-B)











Figure G 32-Pin HWQFN (PWQN0032KE-A)



REVISION HISTORY

RX140 Group Datasheet

Classifications

- Items with Technical Update document number: Changes according to the corresponding issued Technical Update

- Items without Technical Update document number: Minor changes that do not require Technical Update to be issued

Rev.	Date	Description		Classification
		Page	Summary	Classification
1.00	Aug 05, 2021	_	First edition, issued	
1.10	Apr 20, 2022	Features		
		1	Low power design and architecture, changed	TN-RX*-A0258A/E
		1. Overview		
		3	Table 1.1 Outline of Specifications (2/4), changed	
		7, 8	Table 1.3 List of Products, changed	
		9	Figure 1.1 How to Read the Product Part Number, changed	
		13	Table 1.4 Pin Functions (3/3), changed	
		14	Figure 1.3 Pin Assignments of the 80-Pin LFQFP, changed	
		15	Figure 1.4 Pin Assignments of the 64-Pin LFQFP, 64-Pin LQFP, changed	
		16	Figure 1.5 Pin Assignments of the 48-Pin LQFP, changed	
		16	Figure 1.6 Pin Assignments of the 48-Pin HWQFN, changed	
		18	Table 1.5 List of Pins and Pin Functions (80-Pin LFQFP) (1/2), changed	
		20	Table 1.6 List of Pins and Pin Functions (64-Pin LFQFP, 64-Pin LQFP) (1/2), changed	
		24	Table 1.8 List of Pins and Pin Functions (32-Pin LQFP, 32-Pin HWQFN), changed	
		2. Electrical	Characteristics	
		All	Characteristics of PH7 and PH6, added	
		All	Characteristics of products with ROM capacity of 128 Kbytes or more, added	
		46	Table 2.14 DC Characteristics (9), changed	TN-RX*-A0258A/E
		49	Table 2.17 Permissible Output Currents (2), changed	
		50	Table 2.21 Thermal Resistance Value (Reference Values), Note 1, added	
		56	Table 2.36 HOCO Clock Timing (ROM capacity: product with 64 Kbytes) Note 1, added	TN-RX*-A0258A/E
		85	Table 2.59 A/D Conversion Characteristics (2), changed	
		88	Table 2.62 A/D Conversion Characteristics (5), changed	TN-RX*-A0258A/E
		102	Table 2.77 E2 DataFlash Characteristics (2): high-speed operating mode, changed	
		Appendix 1	Package Dimensions	
		114	Figure F 32-Pin LQFP (PLQP0032GB-A), added	
1.20	Nov 22, 2024		Characteristics	
1.20	1100 22, 2024	2. Electrical 4	Table 2.3 Recommended Operating Conditions (2), changed	TN-RX*-A0269A/E
		60	Table 2.40 Timing of Recovery from Low Power Consumption Modes (1),	
			changed	TN-RX*-A0285A/E
		61	Table 2.41 Timing of Recovery from Low Power Consumption Modes (2), changed	
		62	Table 2.42 Timing of Recovery from Low Power Consumption Modes (3), added	
		63	Table 2.43 Timing of Recovery from Low Power Consumption Modes (4), changed	
		64	Table 2.44 Timing of Recovery from Low Power Consumption Modes (5), changed	
		71	Table 2.51 SCI Timing, changed	
		95	Table 2.67 Temperature Sensor Characteristics, Note 1 added	
		102	Table 2.73 ROM (Flash Memory for Code Storage) Characteristics (1), changed	
		102	Table 2.74 ROM (Flash Memory for Code Storage) Characteristics (2) High- Speed Operating Mode, changed	TN-RX*-A0285A/E
		103	Table 2.75 ROM (Flash Memory for Code Storage) Characteristics (3) Middle-Speed Operating Mode, changed	



Rev.	Date	Description		Classification
		Page	Summary	Classification
1.20	Nov 22, 2024	103	Table 2.76 ROM (Flash Memory for Code Storage) Characteristics (4) Middle-Speed Operating Mode 2, changed	
		104	Table 2.77 E2 DataFlash Characteristics (1), changed	



General Precautions in the Handling of Microprocessing Unit and Microcontroller Unit Products

The following usage notes are applicable to all Microprocessing unit and Microcontroller unit products from Renesas. For detailed usage notes on the products covered by this document, refer to the relevant sections of the document as well as any technical updates that have been issued for the products.

1. Precaution against Electrostatic Discharge (ESD)

A strong electrical field, when exposed to a CMOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop the generation of static electricity as much as possible, and quickly dissipate it when it occurs. Environmental control must be adequate. When it is dry, a humidifier should be used. This is recommended to avoid using insulators that can easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors must be grounded. The operator must also be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions must be taken for printed circuit boards with mounted semiconductor devices.

2. Processing at power-on

The state of the product is undefined at the time when power is supplied. The states of internal circuits in the LSI are indeterminate and the states of register settings and pins are undefined at the time when power is supplied. In a finished product where the reset signal is applied to the external reset pin, the states of pins are not guaranteed from the time when power is supplied until the reset process is completed. In a similar way, the states of pins in a product that is reset by an on-chip power-on reset function are not guaranteed from the time when power is supplied until the power is supplied until the power is supplied until the reset ping is specified.

3. Input of signal during power-off state

Do not input signals or an I/O pull-up power supply while the device is powered off. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Follow the guideline for input signal during power-off state as described in your product documentation.

4. Handling of unused pins

Handle unused pins in accordance with the directions given under handling of unused pins in the manual. The input pins of CMOS products are generally in the high-impedance state. In operation with an unused pin in the open-circuit state, extra electromagnetic noise is induced in the vicinity of the LSI, an associated shoot-through current flows internally, and malfunctions occur due to the false recognition of the pin state as an input signal become possible.

5. Clock signals

After applying a reset, only release the reset line after the operating clock signal becomes stable. When switching the clock signal during program execution, wait until the target clock signal is stabilized. When the clock signal is generated with an external resonator or from an external oscillator during a reset, ensure that the reset line is only released after full stabilization of the clock signal. Additionally, when switching to a clock signal produced with an external resonator or by an external oscillator while program execution is in progress, wait until the target clock signal is stable.

6. Voltage application waveform at input pin

Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between V_{IL} (Max.) and V_{IH} (Min.) due to noise, for example, the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between V_{IL} (Max.) and V_{IH} (Min.).

7. Prohibition of access to reserved addresses

Access to reserved addresses is prohibited. The reserved addresses are provided for possible future expansion of functions. Do not access these addresses as the correct operation of the LSI is not guaranteed.

8. Differences between products

Before changing from one product to another, for example to a product with a different part number, confirm that the change will not lead to problems. The characteristics of a microprocessing unit or microcontroller unit products in the same group but having a different part number might differ in terms of internal memory capacity, layout pattern, and other factors, which can affect the ranges of electrical characteristics, such as characteristic values, operating margins, immunity to noise, and amount of radiated noise. When changing to a product with a different part number, implement a system-evaluation test for the given product.

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(Rev.5.0-1 October 2020)

Corporate Headquarters

TOYOSU FORESIA, 3-2-24 Toyosu, Koto-ku, Tokyo 135-0061, Japan www.renesas.com

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